DRV8343-Q1 独立のハーフブリッジ制御と 3 つの内蔵電流センス・アンプを搭載した 12V/24V 車載用ゲート・ドライバ・ユニット (GDU)

1 特長

- **車載アプリケーション用に AEC-Q100 認定済み**
  - 温度グレード 1: -40°C ≤ T_A ≤ +125°C
- **3 つの独立したハーフブリッジ・ゲート・ドライバ**
  - 専用のソース (SHx) およびドレイン (DLx) ピンにより、独立の MOSFET 制御をサポート
  - 3 つのハイサイドと 3 つのローサイドの N チャネル MOSFET (NMOS) を駆動
- **スマート・ゲート・ドライブ・アーキテクチャ**
  - 調整可能なスルーレート制御
  - 1.5mA～1A のピーク・ソース電流
  - 3mA～2A のピーク・シンク電流
- **ゲート・ドライバのチャージ・ポンプによる 100% デューティ・サイクル**
- **3 つの電流センス・アンプ (CSA) を内蔵**
  - 可変ゲイン (5、10、20、40V/V)
  - 双方向または単方向のサポート
- **SPI (S) およびハードウェア (H) インターフェイスを使用可能**
- **6x、3x、1x、および独立 PWM モード**
- **3.3V と 5 Vのロジック入力電圧をサポート**
- **チャージ・ポンプ出力を使用して、逆電圧保護 MOSFET を駆動可能**
- **リニア電圧レギュレータ、3.3V、30mA**
- **保護機能内蔵**
  - VM 低電圧誤動作防止 (UVLO)
  - チャージ・ポンプ低電圧 (CPUV)
  - バッテリへの短絡 (SHT_BAT)
  - グランドへの短絡 (SHT_GND)
  - MOSFET 過電流保護 (OCP)
  - ゲート・ドライバのフォルト (GDF)
  - 熱警告およびシャットダウン (OTW/OTSD)
  - 障害状況インジケータ (nFAULT)

2 アプリケーション

- **12Vおよび24Vの車載用モータ制御アプリケーション**
  - BLDC および BDC モータ・モジュール
  - ファンと送風機
  - 燃料および水ポンプ
  - ソレノイド駆動

3 概要

DRV8343-Q1デバイスは、3相アプリケーション用の統合ゲート・ドライバです。このデバイスには、3つのハーフ・ブリッジ・ゲート・ドライバがあり、それぞれがハイサイドとローサイドのNチャネル・パワーMOSFETを駆動できます。専用のソースおよびドレイン・ピンにより、ソレノイド・アプリケーションで独立のMOSFET制御が可能です。DRV8343-Q1 は、内蔵のチャージ・ポンプを使用してハイサイド MOSFET 用の、リニア・レギュレータを使用してローサイド MOSFET 用の、適切なゲート駆動電圧を生成します。スマート・ゲート・ドライブのアーキテクチャは、最大でソース1A、シンク2Aのピーク・ゲート駆動電流をサポートします。DRV8343-Q1は単一電源で動作でき、ゲート・ドライバ用に5.5～60Vの広い入力電源電圧範囲をサポートします。

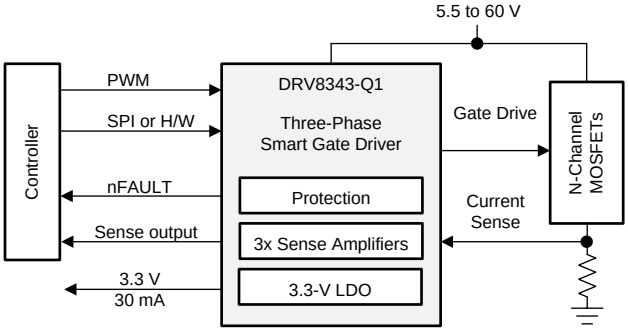
6x、3x、1x、および独立入力のPWMモードにより、コントローラの回路と簡単に接続できます。ゲート・ドライバとデバイスの構成設定は、SPIまたはハードウェア（H/W）インターフェイスにより細かく変更可能です。 DRV8343-Q1 デバイスには3つのローサイド電流センス・アンプが内蔵されており、駆動段の3相すべてについて、双方向の電流センシングが可能です。

製品情報(1)

型番	パッケージ	本体サイズ（公称）
DRV8343-Q1	HTQFP（48）	7.00mm×7.00mm

(1) 提供されているすべてのパッケージについては、巻末の注文情報を参照してください。

概略回路図



目次

4 改訂履歴

資料番号末尾の英字は改訂を表しています。その改訂履歴は英語版に準じています。

2018年3月発行のものから更新 **Page**

- デバイスのステータスを量産データに 変更 ... 1

5 概要（続き）

低消費電力のスリープ・モードがあり、静止電流を低減できます。低電圧誤動作防止、チャージ・ポンプのフォルト、MOSFET過電流、MOSFET短絡、位相ノードの電源およびグランドへの短絡、ゲート・ドライバのフォルト、過熱への保護機能が内蔵されています。フォルト状況はnFAULTピンにより通知され、SPIデバイスのバリエーションではデバイスのレジスタにより詳細が通知されます。

PP

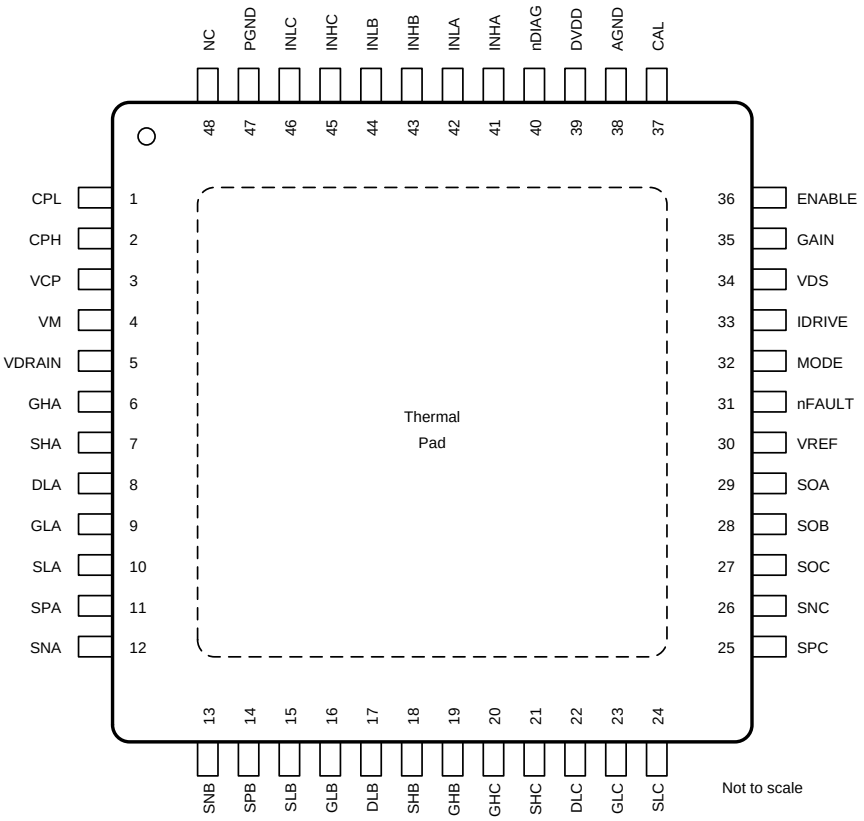
6 Device Comparison Table

DEVICE	VARIANT(1)	INTERFACE(1)
DRV8343-Q1	DRV8343H	Hardware
	DRV8343S	SPI

(1) For more information on the device name and device options, see the *デバイスの項目表記* section.

7 Pin Configuration and Functions

DRV8343H PHP PowerPAD™ Package
48-Pin HTQFP With Exposed Thermal Pad
Top View



Pin Functions—DRV8343H

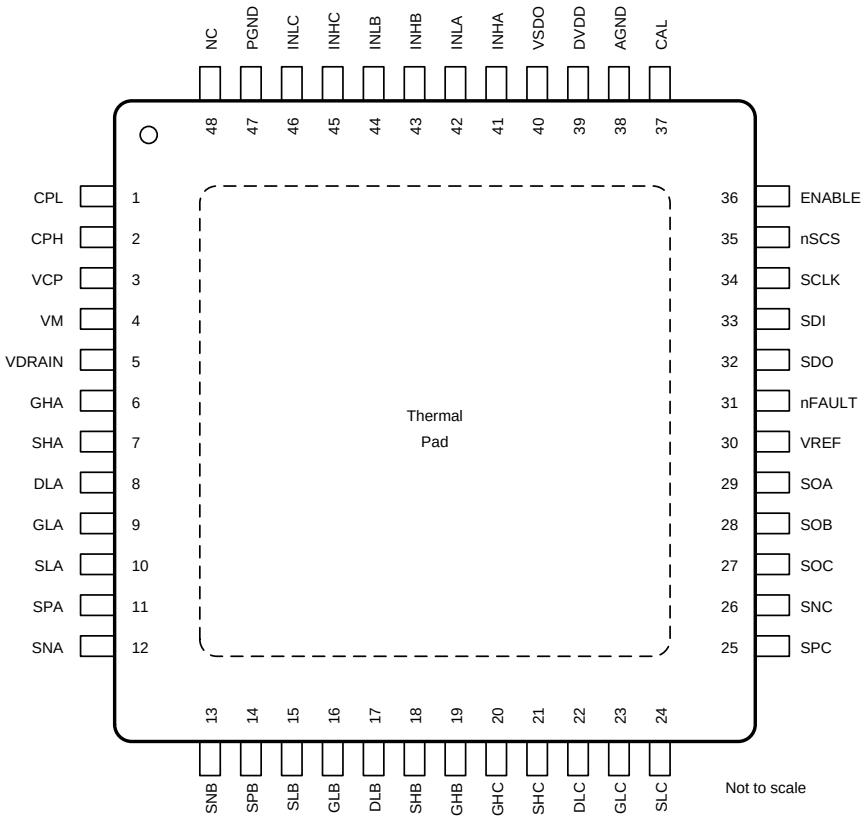
PIN		TYPE(1)	DESCRIPTION
NO.	NAME		
1	CPL	PWR	Charge pump switching node. Connect a flying capacitor between the CPH and CPL pins
2	CPH	PWR	Charge pump switching node. Connect a flying capacitor between the CPH and CPL pins
3	VCP	PWR	Charge pump output. Connect a bypass capacitor between the VCP and VM pins
4	VM	PWR	Gate driver power supply input. Connect to the bridge power supply. Connect bypass capacitors VM and PGND pins
5	VDRAIN	I	High-side MOSFET drain sense input. Connect to the common point of the MOSFET drains
6	GHA	O	High-side gate driver output. Connect to the gate of the high-side power MOSFET
7	SHA	I	High-side source sense input. Connect to the high-side power MOSFET source. If high-side power MOSFET is not used, connect to GND
8	DLA	I	Low-side MOSFET drain sense input. Connect to the low-side MOSFET drain

(1) PWR = power, I = input, O = output, NC = no connection, OD = open-drain output

Pin Functions—DRV8343H (continued)

PIN		TYPE[1]	DESCRIPTION
NO.	NAME		
9	GLA	O	Low-side gate driver output. Connect to the gate of the low-side power MOSFET
10	SLA	I	Low-side source sense input. Connect to the low-side power MOSFET source
11	SPA	I	Low-side current shunt amplifier input. Connect to the low-side power MOSFET source and high-side of the current shunt resistor
12	SNA	I	Current sense amplifier input. Connect to the low-side of the current shunt resistor
13	SNB	I	Low-side source sense input. Connect to the low-side power MOSFET source
14	SPB	I	Low-side current shunt amplifier input. Connect to the low-side power MOSFET source and high-side of the current shunt resistor
15	SLB	I	Low-side source sense input. Connect to the low-side power MOSFET source
16	GLB	O	Low-side gate driver output. Connect to the gate of the low-side power MOSFET
17	DLB	I	Low-side MOSFET drain sense input. Connect to the low-side MOSFET drain
18	SHB	I	High-side source sense input. Connect to the high-side power MOSFET source. If high-side power MOSFET is not used, connect to GND
19	GHB	O	High-side gate driver output. Connect to the gate of the high-side power MOSFET
20	GHC	O	High-side gate driver output. Connect to the gate of the high-side power MOSFET
21	SHC	I	High-side source sense input. Connect to the high-side power MOSFET source. If high-side power MOSFET is not used, connect to GND
22	DLC	I	Low-side MOSFET drain sense input. Connect to the low-side MOSFET drain
23	GLC	O	Low-side gate driver output. Connect to the gate of the low-side power MOSFET
24	SLC	I	Low-side source sense input. Connect to the low-side power MOSFET source
25	SPC	I	Low-side current shunt amplifier input. Connect to the low-side power MOSFET source and high-side of the current shunt resistor
26	SNC	I	Current sense amplifier input. Connect to the low-side of the current shunt resistor
27	SOC	O	Current sense amplifier output
28	SOB	O	Current sense amplifier output
29	SOA	O	Current sense amplifier output
30	VREF	PWR	Current sense amplifier power supply input and reference. Connect a bypass capacitor between VREF and AGND
31	nFAULT	OD	Fault indicator output. This pin is pulled logic low during a fault condition and requires an external pullup resistor
32	MODE	I	PWM input mode setting. This pin is a 7-level input pin set by an external resistor
33	IDRIVE	I	Gate drive output current setting. This pin is a 7-level input pin set by an external resistor
34	VDS	I	VDS monitor trip point setting. This pin is a 7-level input pin set by an external resistor
35	GAIN	I	Amplifier gain setting. The pin is a 4-level input pin set by an external resistor
36	ENABLE	I	Gate driver enable. When this pin is logic low the device goes to a low-power sleep mode. An 20-µs (typ) low pulse can be used to reset fault conditions
37	CAL	I	Amplifier calibration input. Set logic high to internally short amplifier inputs
38	AGND	PWR	Device analog ground. Connect to system ground
39	DVDD	PWR	3.3-V internal regulator output. Connect a bypass capacitor between the DVDD and AGND pins. This regulator can externally source up to 30 mA.
40	nDIAG	I	Control pin for open load diagnostic and offline short-to-battery and short-to-ground diagnostic. To enable the diagnostics at device power-up, do not connect this pin (or tie it to ground). To disable the diagnostics, connect this pin to the DVDD pin.
41	INHA	I	High-side gate driver control input. This pin controls the output of the high-side gate driver
42	INLA	I	Low-side gate driver control input. This pin controls the output of the low-side gate driver
43	INHB	I	High-side gate driver control input. This pin controls the output of the high-side gate driver
44	INLB	I	Low-side gate driver control input. This pin controls the output of the low-side gate driver
45	INHC	I	High-side gate driver control input. This pin controls the output of the high-side gate driver
46	INLC	I	Low-side gate driver control input. This pin controls the output of the low-side gate driver
47	PGND	PWR	Device power ground. Connect to system ground
48	NC	NC	No connect. Do not connect anything to this pin
—	Thermal Pad	PWR	Must be connected to ground

DRV8343S PHP PowerPAD™ Package
48-Pin HTQFP With Exposed Thermal Pad
Top View



Pin Functions—DRV8343S

PIN		TYPE[1]	DESCRIPTION
NO.	NAME		
1	CPL	PWR	Charge pump switching node. Connect a flying capacitor between the CPH and CPL pins
2	CPH	PWR	Charge pump switching node. Connect a flying capacitor between the CPH and CPL pins
3	VCP	PWR	Charge pump output. Connect a bypass capacitor between the VCP and VM pins
4	VM	PWR	Gate driver power supply input. Connect to the bridge power supply. Connect bypass capacitors between the VM and PGND pins
5	VDRAIN	I	High-side MOSFET drain sense input. Connect to the common point of the MOSFET drains
6	GHA	O	High-side gate driver output. Connect to the gate of the high-side power MOSFET
7	SHA	I	High-side source sense input. Connect to the high-side power MOSFET source. If high-side power MOSFET is not used, connect to GND
8	DLA	I	Low-side MOSFET drain sense input. Connect to the low-side MOSFET drain
9	GLA	O	Low-side gate driver output. Connect to the gate of the low-side power MOSFET
10	SLA	I	Low-side source sense input. Connect to the low-side power MOSFET source
11	SPA	I	Low-side current shunt amplifier input. Connect to the low-side power MOSFET source and high-side of the current shunt resistor
12	SNA	I	Current sense amplifier input. Connect to the low-side of the current shunt resistor
13	SNB	I	Low-side source sense input. Connect to the low-side power MOSFET source
14	SPB	I	Low-side current shunt amplifier input. Connect to the low-side power MOSFET source and high-side of the current shunt resistor
15	SLB	I	Low-side source sense input. Connect to the low-side power MOSFET source
16	GLB	O	Low-side gate driver output. Connect to the gate of the low-side power MOSFET
17	DLB	I	Low-side MOSFET drain sense input. Connect to the low-side MOSFET drain

(1) PWR = power, I = input, O = output, NC = no connection, OD = open-drain output, PP = push-pull

Pin Functions—DRV8343S (continued)

PIN		TYPE[1]	DESCRIPTION
NO.	NAME		
18	SHB	I	High-side source sense input. Connect to the high-side power MOSFET source. If high-side power MOSFET is not used, connect to GND
19	GHB	O	High-side gate driver output. Connect to the gate of the high-side power MOSFET
20	GHC	O	High-side gate driver output. Connect to the gate of the high-side power MOSFET
21	SHC	I	High-side source sense input. Connect to the high-side power MOSFET source. If high-side power MOSFET is not used, connect to GND
22	DLC	I	Low-side MOSFET drain sense input. Connect to the low-side MOSFET drain
23	GLC	O	Low-side gate driver output. Connect to the gate of the low-side power MOSFET
24	SLC	I	Low-side source sense input. Connect to the low-side power MOSFET source
25	SPC	I	Low-side current shunt amplifier input. Connect to the low-side power MOSFET source and high-side of the current shunt resistor
26	SNC	I	Current sense amplifier input. Connect to the low-side of the current shunt resistor
27	SOC	O	Current sense amplifier output
28	SOB	O	Current sense amplifier output
29	SOA	O	Current sense amplifier output
30	VREF	PWR	Current sense amplifier power supply input and reference. Connect a bypass capacitors between VREF and AGND
31	nFAULT	OD	Fault indicator output. This pin is pulled logic low during a fault condition and requires an external pullup resistor
32	SDO	PP	Serial data output. Data is shifted out on the rising edge of the SCLK pin. VSDO determines logic level on the output
33	SDI	I	Serial data input. Data is captured on the falling edge of the SCLK pin
34	SCLK	I	Serial clock input. Serial data is shifted out and captured on the corresponding rising and falling edge on this pin
35	nSCS	I	Serial chip select. A logic low on this pin enables serial interface communication
36	ENABLE	I	Gate driver enable. When this pin is logic low the device goes to a low-power sleep mode. An 20-µs (typ) low pulse can be used to reset fault conditions
37	CAL	I	Amplifier calibration input. Set logic high to internally short amplifier inputs
38	AGND	PWR	Device analog ground. Connect to system ground
39	DVDD	PWR	3.3-V internal regulator output. Connect a bypass capacitor between the DVDD and AGND pins. This regulator can externally source up to 30 mA.
40	VSDO	PWR	Supply pin for SDO output. Connect to 5-V or 3.3-V depending on the desired logic level. Connect a bypass capacitors between VSDO and AGND
41	INHA	I	High-side gate driver control input. This pin controls the output of the high-side gate driver
42	INLA	I	Low-side gate driver control input. This pin controls the output of the low-side gate driver
43	INHB	I	High-side gate driver control input. This pin controls the output of the high-side gate driver
44	INLB	I	Low-side gate driver control input. This pin controls the output of the low-side gate driver
45	INHC	I	High-side gate driver control input. This pin controls the output of the high-side gate driver
46	INLC	I	Low-side gate driver control input. This pin controls the output of the low-side gate driver
47	PGND	PWR	Device power ground. Connect to system ground
48	NC	NC	No connect. Do not connect anything to this pin
—	Thermal Pad	PWR	Must be connected to ground

8 Specifications

8.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

	MIN	MAX	UNIT
GATE DRIVER			
Power supply pin voltage (VM)	–0.3	65	V
Voltage differential between ground pins (AGND, BGND, DGND, PGND)	–0.3	0.3	V
MOSFET drain sense pin voltage (VDRAIN)	–0.3	65	V
Charge pump pin voltage (CPH, VCP)	–0.3	V_{VM} + 13.5	V
Charge-pump negative-switching pin voltage (CPL)	–0.3	V_{VM}	V
Internal logic regulator pin voltage (DVDD)	–0.3	3.8	V
Voltage difference between VM and VDRAIN	–10	10	V
Digital pin voltage (CAL, ENABLE, GAIN, IDRIVE, INHx, INLx, MODE, nFAULT, nSCS, SCLK, SDI, SDO, VDS, nDIAG)	–0.3	5.75	V
Continuous high-side gate drive pin voltage (GHx)	–5(2)	V_{VCP} + 0.5	V
Transient 200-ns high-side gate drive pin voltage (GHx)	–7	V_{VCP} + 0.5	V
High-side gate drive pin voltage with respect to SHx (GHx)	–0.3	13.5	V
Continuous high-side source sense pin voltage (SHx, DLx)	–5(2)	V_{VM} + 5	V
Transient 200-ns high-side source sense pin voltage (SHx, DLx)	–7	V_{VM} + 7	V
Continuous high-side source sense pin voltage (SHx, DLx)	–5(2)	V_{DRAIN} + 5	V
Transient 200-ns high-side source sense pin voltage (SHx, DLx)	–7	V_{DRAIN} + 7	V
Continuous low-side gate drive pin voltage (GLx)	–0.5	15	V
Gate drive pin source current (GHx, GLx)	Internally limited		A
Gate drive pin sink current (GHx, GLx)	Internally limited		A
Continuous low-side source sense pin voltage (SLx)	–1	1	V
Transient 200-ns low-side source sense pin voltage (SLx)	–3	3	V
Continuous shunt amplifier input pin voltage (SNx, SPx)	–1	1	V
Transient 200-ns shunt amplifier input pin voltage (SNx, SPx)	–3	3	V
Reference input pin voltage (VREF)	–0.3	5.75	V
Shunt amplifier output pin voltage (SOx)	–0.3	V_{VREF} + 0.3	V
Shunt amplifier output current (SOx)	0	8	mA
Push-pull output buffer reference voltage (VSDO)	–0.3	5.75	V
Push-pull output current (SDO)	0	10	mA
Open drain pullup voltage (nFAULT)	–0.3	5.75	V
Open drain output current (nFAULT)	0	10	mA
Operating junction temperature, T_J	–40	150	°C
Storage temperature, T_{stg}	–65	150	°C

(1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) Continuous high-side gate pin (GHx) and phase node pin voltage (SHx) should be limited to –2 V minimum for an absolute maximum of 65 V on VM. At 60 V and below, the full specification of –5 V continuous on GHx and SHx is allowable.

8.2 ESD Ratings

				VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human-body model (HBM), per AEC Q100-002(1)		±2000	V
		Charged-device model (CDM), per AEC Q100-011	All pins	±500	
			Corner pins (1, 10, 11, 20, 21, 30, 31, and 40)	±750	V

(1) AEC Q100-002 indicates that HBM stressing shall be in accordance with the ANSI/ESDA/JEDEC JS-001 specification.

8.3 Recommended Operating Conditions

		MIN	MAX	UNIT
GATE DRIVER				
V_{VM}	Power supply voltage (VM) Continuous (1)	5.5	50	V
	Power supply voltage (VM) Transient over voltage (2)	5.5	60	V
V_I	Input voltage (CAL, ENABLE, GAIN, IDRIVE, INHx, INLx, MODE, nSCS, SCLK, SDI, VDS, VSDO, nDIAG)	0	5.5	V
f_{PWM}	Applied PWM signal (INHx, INLx)	0	200(3)	kHz
I_{GATE_HS}	High-side average gate-drive current (GHx)	0	25(3)	mA
I_{GATE_LS}	Low-side average gate-drive current (GLx)	0	25(3)	mA
I_{DVDD}	External load current (DVDD)	0	30(3)	mA
V_{VREF}	Reference voltage input (VREF)	3	5.5	V
V_{SDO}	Push-pull voltage (SDO)	3	5.5	V
V_{OD}	Open drain pullup voltage (nFAULT)	0	5.5	V
T_A	Operating ambient temperature	–40	125	°C

(1) Operation at VM = 5.5V only when coming from higher VM. The minimum VM voltage for startup is greater than V_{UVLO} (rising) voltage.
(2) VM recommended operating condition for electrical characteristic table. Product life time depends on VM voltage. The device is intended for 12–V and 24–V battery automotive system with life-time nominal voltage of 5.5 V - 50 V. The device can be operated during additional overvoltage events as specified in ISO16750-2:2012
(3) Power dissipation and thermal limits must be observed

8.4 Thermal Information

THERMAL METRIC(1)		DRV8343-Q1 PHP (HTQFP) 48 PINS	UNIT
$R_{\theta JA}$	Junction-to-ambient thermal resistance	26.5	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	16.3	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	6.7	°C/W
ψ_{JT}	Junction-to-top characterization parameter	0.2	°C/W
ψ_{JB}	Junction-to-board characterization parameter	6.8	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	1.0	°C/W

(1) For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

8.5 Electrical Characteristics

Over recommended operating conditions 5.5 ≤ V_{VM} ≤ 60 V (unless otherwise noted). Typical limits apply for V_{VM} = 24 V

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
POWER SUPPLIES (DVDD, VCP, VM)						
I_{VM}	VM operating supply current	V_{VM} = 24 V, ENABLE = 3.3 V, INHx/INLx = 0 V, SHx = 0 V		12	16	mA
I_{VMQ}	VM sleep mode supply current	ENABLE = 0 V, V_{VM} = 24 V, T_A = 25°C		12	20	µA
		ENABLE = 0 V, V_{VM} = 24 V, T_A = 125°C			50	
t_{RST}	Reset pulse time	ENABLE = 0 V period to reset faults	4.4		43	µs
t_{WAKE} (1)	Turnon time	ENABLE = 3.3 V to outputs ready, V_{VM} > V_{UVLO}			1	ms
t_{SLEEP}	Turnoff time	ENABLE = 0 V to device sleep mode			1	ms
V_{DVDD}	DVDD regulator voltage	V_{VM} > 6 V, I_{DVDD} = 0 to 30 mA	3	3.3	3.6	V
		V_{VM} = 5.5 to 6 V, I_{DVDD} = 0 to 20 mA	3	3.3	3.6	V
V_{VCP}	VCP operating voltage with respect to VM	V_{VM} = 13 V, I_{VCP} = 0 to 25 mA	8.4	11	12.5	V
		V_{VM} = 10 V, I_{VCP} = 0 to 20 mA	6.3	9	10	
		V_{VM} = 8 V, I_{VCP} = 0 to 15 mA	5.4	7	8	
		V_{VM} = 5.5 V, I_{VCP} = 0 to 5 mA	4	5	6	
LOGIC-LEVEL INPUTS (CAL, ENABLE, INHx, INLx, SCLK, SDI)						
V_{IL}	Input logic low voltage		0		0.7	V
V_{IH}	Input logic high voltage		1.6		5.5	V
V_{HYS}	Input logic hysteresis			182		mV
I_{IL}	Input logic low current	V_{VIN} = 0 V; INHx, INLx, SDI(IDRIVE), SCLK(VDS), ENABLE	–5		5	µA
I_{IH}	Input logic high current	V_{VIN} = 5 V; INHx, INLx, SDI(IDRIVE), SCLK(VDS)		50	90	µA
I_{IH}	Input logic high current	V_{VIN} = 5 V; ENABLE		80	110	µA
R_{PD}	Pulldown resistance	To AGND; INHx, INLx, SDI(IDRIVE), SCLK(VDS)	50	100	200	kΩ
R_{PD}	Pulldown resistance	To AGND; ENABLE	30	60	110	kΩ
t_{PD}	Propagation delay	INHx/INLx input buffer and digital core propagation delay. Dead time is excluded.		105		ns
LOGIC LEVEL INPUT (nSCS)						
$V_{IL,nSCS}$	Input logic low voltage		0		0.7	V
$V_{IH,nSCS}$	Input logic high voltage		1.6		5.5	V
$R_{PU,nSCS}$	Pullup resistance	To DVDD	25	50	90	kΩ
FOUR-LEVEL H/W INPUT (GAIN)						
V_{I1}	Input mode 1 voltage	Tied to AGND		0		V
V_{I2}	Input mode 2 voltage	47 kΩ ± 5% to tied AGND		1.2		V
V_{I3}	Input mode 3 voltage	Hi-Z (> 500 kΩ to AGND)		2		V
V_{I4}	Input mode 4 voltage	Tied to DVDD		3.3		V
R_{PU}	Pullup resistance	Internal pullup to DVDD	25	50	80	kΩ
R_{PD}	Pulldown resistance	Internal pulldown to AGND	40	84	130	kΩ
SEVEN-LEVEL H/W INPUTS (MODE, IDRIVE, VDS)						
V_{I1}	Input mode 1 voltage	Tied to AGND		0		V
V_{I2}	Input mode 2 voltage	18 kΩ ± 5% tied to AGND		0.5		V
V_{I3}	Input mode 3 voltage	75 kΩ ± 5% tied to AGND		1.1		V
V_{I4}	Input mode 4 voltage	Hi-Z (> 1.5 MΩ)		1.65		V
V_{I5}	Input mode 5 voltage	75 kΩ ± 5% tied to DVDD		2.2		V
V_{I6}	Input mode 6 voltage	18 kΩ ± 5% tied to DVDD		2.8		V
V_{I7}	Input mode 7 voltage	MODE : 0.47 kΩ ± 5% tied to DVDD VDS, IDRIVE : Tied to DVDD		3.3		V
R_{PU}	Pullup resistance	Internal pullup to DVDD	35	73	125	kΩ
R_{PD}	Pulldown resistance	Internal pulldown to AGND	35	73	125	kΩ
PUSH-PULL OUTPUT (SDO)						

(1) Does not include OLP/Shorts diagnostic delay time in the H/W device

Electrical Characteristics (continued)

Over recommended operating conditions 5.5 ≤ V_{VM} ≤ 60 V (unless otherwise noted). Typical limits apply for V_{VM} = 24 V

PARAMETER			TEST CONDITIONS	MIN	TYP	MAX	UNIT
$R_{PU,SDO}$	Internal pullup		To VSDO = 5 V		40	90	Ω
			To VSDO = 3.3 V		60	120	
$R_{PD,SDO}$	Internal pulldown		To GND		30	50	Ω
OPEN DRAIN OUTPUT (nFAULT)							
V_{OL}	Output logic low voltage		I_O = 5 mA			0.15	V
I_{OZ}	Output high impedance leakage		V_O = 5 V	–1		9	µA
GATE DRIVERS (GHx, GLx)							
V_{GSH}	High-side gate drive voltage with respect to SHx		V_{VM} = 13 V, I_{VCP} = 0 to 25 mA, GHx no output load	8.4	11	12.5	V
			V_{VM} = 10 , I_{VCP} = 0 to 20 mA, GHx no output load	6.3	9	10	
			V_{VM} = 8 V, I_{VCP} = 0 to 15 mA, GHx no output load	5.4	7	8	
			V_{VM} = 5.5 V, I_{VCP} = 0 to 5 mA, GHx no output load	4	5	6	
V_{GSL}	Low-side gate drive voltage with respect to PGND		V_{VM} = 12 V, I_{VCP} = 0 to 25 mA, GLx no output load	9	11	12	V
			V_{VM} = 10 V, I_{VCP} = 0 to 20 mA, GLx no output load	9.9	10.0	10.1	
			V_{VM} = 8 V, I_{VCP} = 0 to 15 mA, GLx no output load	7.9	8.0	8.1	
			V_{VM} = 5.5 V, I_{VCP} = 0 to 5 mA, GLx no output load	5.4	5.5	5.6	
t_{DEAD}	Gate drive dead time	SPI Device	DEAD_TIME = 00b		500		ns
			DEAD_TIME = 01b		1000		
			DEAD_TIME = 10b		2000		
			DEAD_TIME = 11b		4000		
		H/W Device			1000		
t_{DRIVE}	Peak current gate drive time	SPI Device	TDRIVE = 00b		500		ns
			TDRIVE = 01b		1000		
			TDRIVE = 10b		2000		
			TDRIVE = 11b		3000		
		H/W Device			3000		
t_{DRIVE_MAX}	Peak current gate drive max time		IDRIVEP_Hx = 0000b, 0001b, 0010b, 0011b		20		µs

Electrical Characteristics (continued)

Over recommended operating conditions 5.5 ≤ V_{VM} ≤ 60 V (unless otherwise noted). Typical limits apply for V_{VM} = 24 V

PARAMETER			TEST CONDITIONS	MIN	TYP	MAX	UNIT
I_{DRIVEP}	Peak source gate current	SPI Device	IDRIVEP_Hx = 0000b (GHx), V_{VM} = 24 V	0.45	1.5	3.0	mA
			IDRIVEP_Lx = 0000b (GLx), V_{VM} = 24 V	0.81	2.7	5.4	
			IDRIVEP_Hx = 0001b (GHx), V_{VM} = 24 V	1.05	3.5	7	
			IDRIVEP_Lx = 0001b (GLx), V_{VM} = 24 V	1.17	3.9	7.8	
			IDRIVEP_Hx = 0010b (GHx), V_{VM} = 24 V	1.5	5	10	
			IDRIVEP_Lx = 0010b (GLx), V_{VM} = 24 V	1.95	6.5	13	
			IDRIVEP_Hx or IDRIVEP_Lx = 0011b (GHx/GLx), V_{VM} = 24 V	3	10	20	
			IDRIVEP_Hx or IDRIVEP_Lx = 0100b (GHx/GLx), V_{VM} = 24 V	4.5	15	30	
			IDRIVEP_Hx or IDRIVEP_Lx = 0101b (GHx/GLx), V_{VM} = 24 V	15	50	100	
			IDRIVEP_Hx or IDRIVEP_Lx = 0110b (GHx/GLx), V_{VM} = 24 V	18	60	120	
			IDRIVEP_Hx or IDRIVEP_Lx = 0111b (GHx/GLx), V_{VM} = 24 V	19.5	65	130	
			IDRIVEP_Hx or IDRIVEP_Lx = 1000b (GHx/GLx), V_{VM} = 24 V	76	200	400	
			IDRIVEP_Hx or IDRIVEP_Lx = 1001b (GHx/GLx), V_{VM} = 24 V	79.8	210	420	
			IDRIVEP_Hx or IDRIVEP_Lx = 1010b (GHx/GLx), V_{VM} = 24 V	98.8	260	520	
			IDRIVEP_Hx or IDRIVEP_Lx = 1011b (GHx/GLx), V_{VM} = 24 V	100.7	265	530	
			IDRIVEP_Hx or IDRIVEP_Lx = 1100b (GHx/GLx), V_{VM} = 24 V	279.3	735	1470	
			IDRIVEP_Hx or IDRIVEP_Lx = 1101b (GHx/GLx), V_{VM} = 24 V	304	800	1600	
			IDRIVEP_Hx or IDRIVEP_Lx = 1110b (GHx/GLx), V_{VM} = 24 V	355.3	935	1870	
			IDRIVEP_Hx or IDRIVEP_Lx = 1111b (GHx/GLx), V_{VM} = 24 V	380	1000	2000	
		H/W Device	IDRIVE = Tied to AGND (GHx), V_{VM} = 24 V	0.45	1.5	3.0	
			IDRIVE = Tied to AGND (GLx), V_{VM} = 24 V	0.81	2.7	5.4	
			IDRIVE = 18 kΩ ± 5% tied to AGND (GHx), V_{VM} = 24 V	1.5	5	10	
			IDRIVE = 18 kΩ ± 5% tied to AGND (GLx), V_{VM} = 24 V	1.95	6.5	13	
			IDRIVE = 75 kΩ ± 5% tied to AGND (GHx/GLx), V_{VM} = 24 V	3	10	20	
			IDRIVE = Hi-Z (GHx/GLx), V_{VM} = 24 V	18	60	120	
			IDRIVE = 75 kΩ ± 5% tied to DVDD (GHx/GLx), V_{VM} = 24 V	76	200	400	
			IDRIVE = 18 kΩ ± 5% tied to DVDD (GHx/GLx), V_{VM} = 24 V	98.8	260	520	
			IDRIVE = Tied to DVDD (GHx/GLx), V_{VM} = 24 V	380	1000	2000	

Electrical Characteristics (continued)

Over recommended operating conditions 5.5 ≤ V_{VM} ≤ 60 V (unless otherwise noted). Typical limits apply for V_{VM} = 24 V

PARAMETER			TEST CONDITIONS	MIN	TYP	MAX	UNIT
I_{DRIVEN}	Peak sink gate current	SPI Device	IDRIVEN_Hx or IDRIVEN_Lx = 0000b, V_{VM} = 24 V	0.9	3	5.4	mA
			IDRIVEN_Hx or IDRIVEN_Lx = 0001b, V_{VM} = 24 V	2.09	7	12.6	
			IDRIVEN_Hx or IDRIVEN_Lx = 0010b, V_{VM} = 24 V	3	10	18	
			IDRIVEN_Hx or IDRIVEN_Lx = 0011b, V_{VM} = 24 V	6	20	36	
			IDRIVEN_Hx or IDRIVEN_Lx= 0100b, V_{VM} = 24 V	9	30	54	
			IDRIVEN_Hx or IDRIVEN_Lx = 0101b, V_{VM} = 24 V	30	100	180	
			IDRIVEN_Hx or IDRIVEN_Lx = 0110b, V_{VM} = 24 V	36	120	216	
			IDRIVEN_Hx or IDRIVEN_Lx = 0111b, V_{VM} = 24 V	39	130	234	
			IDRIVEN_Hx or IDRIVEN_Lx = 1000b, V_{VM} = 24 V	120	400	720	
			IDRIVEN_Hx or IDRIVEN_Lx = 1001b, V_{VM} = 24 V	126	420	756	
			IDRIVEN_Hx or IDRIVEN_Lx = 1010b, V_{VM} = 24 V	156	520	936	
			IDRIVEN_Hx or IDRIVEN_Lx = 1011b, V_{VM} = 24 V	159	530	954	
			IDRIVEN_Hx or IDRIVEN_Lx = 1100b, V_{VM} = 24 V	441	1470	2646	
			IDRIVEN_Hx or IDRIVEN_Lx = 1101b, V_{VM} = 24 V	480	1600	2880	
			IDRIVEN_Hx or IDRIVEN_Lx = 1110b, V_{VM} = 24 V	561	1870	3366	
			IDRIVEN_Hx or IDRIVEN_Lx = 1111b, V_{VM} = 24 V	600	2000	3600	
		H/W Device	IDRIVE = Tied to AGND, V_{VM} = 24 V	0.9	3	5.4	
			IDRIVE = 18 kΩ ± 5% tied to AGND, V_{VM} = 24 V	3	10	18	
			IDRIVE = 75 kΩ ± 5% tied to AGND, V_{VM} = 24 V	6	20	36	
			IDRIVE = Hi-Z, V_{VM} = 24 V	36	120	216	
			IDRIVE = 75 kΩ ± 5% tied to DVDD, V_{VM} = 24 V	120	400	720	
			IDRIVE = 18 kΩ ± 5% tied to DVDD, V_{VM} = 24 V	156	520	936	
			IDRIVE = Tied to DVDD, V_{VM} = 24 V	600	2000	3600	
I_{HOLDP}	Gate holding source current after t_{DRIVE}	SPI Device	IDRIVEP_Hx = 0000b, V_{VM} = 24 V	0.45	1.5	3.8	mA
			IDRIVEP_Hx = 0001b, V_{VM} = 24 V	1.05	3.5	7	
			IDRIVEP_Hx = 0010b, V_{VM} = 24 V	1.5	5	10	
			IDRIVEP_Hx = 0011b, V_{VM} = 24 V	3	10	20	
			All other IDRIVE settings, V_{VM} = 24 V	4.5	15	30	
		H/W Device	IDRIVE tied to AGND, V_{VM} = 24 V	0.45	1.5	3.8	
			IDRIVE = 18 kΩ ± 5% tied to AGND, V_{VM} = 24 V	1.5	5	10	
			IDRIVE = 75 kΩ ± 5% tied to AGND, V_{VM} = 24 V	3	10	20	
			All other IDRIVE settings, V_{VM} = 24 V	4.5	15	30	
I_{HOLDN}	Gate holding sink current after t_{DRIVE}	SPI Device	IDRIVEP_Hx = 0000b, V_{VM} = 24 V	0.9	3	5.4	mA
			IDRIVEP_Hx = 0001b, V_{VM} = 24 V	2	7	12.6	
			IDRIVEP_Hx = 0010b, V_{VM} = 24 V	3	10	18	
			IDRIVEP_Hx = 0011b, V_{VM} = 24 V	6	20	36	
			All other IDRIVE settings, V_{VM} = 24 V	9	30	54	
		H/W Device	IDRIVE tied to AGND, V_{VM} = 24 V	0.9	3	5.4	
			IDRIVE = 18 kΩ ± 5% tied to AGND, V_{VM} = 24 V	3	10	18	
			IDRIVE = 75 kΩ ± 5% tied to AGND, V_{VM} = 24 V	6	20	36	
			All other IDRIVE settings, V_{VM} = 24 V	9	30	54	
I_{STRONG}	Gate strong pulldown current (GHx to SHx and GLx to PGND)		IDRIVEP_Hx = 0000b, 0001b, 0010b, 0011b, V_{VM} = 24 V	9	30	54	mA
			All other IDRIVE settings, V_{VM} = 24 V	0.6	2	3.6	A
R_{OFF}	Gate hold off resistor		GHx to SHx		150	280	kΩ
R_{OFF}	Gate hold off resistor		GLx to PGND		150	280	kΩ
CURRENT SHUNT AMPLIFIER (SNx, SOx, SPx, VREF)							

Electrical Characteristics (continued)

Over recommended operating conditions 5.5 ≤ V_{VM} ≤ 60 V (unless otherwise noted). Typical limits apply for V_{VM} = 24 V

PARAMETER			TEST CONDITIONS	MIN	TYP	MAX	UNIT
G_{CSA}	Amplifier gain	SPI Device	CSA_GAIN = 00b, CSA_FET = 0b	4.9	5	5.1	V/V
			CSA_GAIN = 01b, CSA_FET = 0b	9.8	10	10.2	
			CSA_GAIN = 10b, CSA_FET = 0b	19.6	20	20.4	
			CSA_GAIN = 11b, CSA_FET = 0b	39.2	40	40.8	
		SPI Device	CSA_GAIN = 00b, CSA_FET = 1b	4.85	5	5.15	
			CSA_GAIN = 01b, CSA_FET = 1b	9.7	10	10.3	
			CSA_GAIN = 10b, CSA_FET = 1b	19.4	20	20.6	
			CSA_GAIN = 11b, CSA_FET = 1b	38.8	40	41.2	
		H/W Device	GAIN = Tied to AGND	4.9	5	5.1	
			GAIN = 47 kΩ ± 5% tied to AGND	9.8	10	10.2	
			GAIN = Hi-Z	19.6	20	20.4	
			GAIN = Tied to DVDD	39.2	40	40.8	
t_{SET}	Settling time to ±1%		V_{O_STEP} = 0.5 V, G_{CSA} = 5 V/V		150		ns
			V_{O_STEP} = 0.5 V, G_{CSA} = 10 V/V		300		
			V_{O_STEP} = 0.5 V, G_{VSA} = 20 V/V		600		
			V_{O_STEP} = 0.5 V, G_{CSA} = 40 V/V		1200		
V_{COM}	Common mode input range			–0.15		0.15	V
V_{DIFF}	Differential mode input range			–0.3		0.3	V
V_{OFF}	Input offset error		V_{SP} = V_{SN} = 0 V, VREF = 3.3 V, G_{CSA} = 10, 20, 40 V/V	–4		4	mV
V_{OFF}	Input offset error		V_{SP} = V_{SN} = 0 V, VREF = 3.3 V, G_{CSA} = 5 V/V	–5		5	mV
V_{DRIFT}	Drift offset		V_{SP} = V_{SN} = 0 V	-45	10	45	µV/°C
V_{LINEAR}	SOx output voltage linear range			0.25		V_{VREF} – 0.25	V
V_{BIAS}	SOx output voltage bias	SPI Device	V_{SP} = V_{SN} = 0 V, CAL = 3.3 V, VREF_DIV = 0b		V_{VREF} – 0.3		V
			V_{SP} = V_{SN} = 0 V, CAL = 3.3 V, VREF_DIV = 1b		V_{VREF} / 2		
		H/W Device	V_{SP} = V_{SN} = 0 V, CAL = 3.3 V		V_{VREF} / 2		
I_{BIAS}	SPx/SNx input bias current					100	µA
V_{SLEW}	SOx output slew rate		60-pF load		10		V/µs
I_{VREF}	VREF input current		V_{VREF} = 5 V		2	3	mA
UGB	Unity gain bandwidth		60-pF load		8		MHz
PROTECTION CIRCUITS							
V_{UVLO}	VM undervoltage lockout		VM falling, UVLO report		5.2	5.4	V
			VM rising, UVLO recovery		5.4	5.9	
$V_{UVLO,DVDD}$	DVDD undervoltage lockout					2.9	V
V_{UVLO_HYS}	VM undervoltage hysteresis		Rising to falling threshold		200		mV
t_{UVLO_DEG}	VM undervoltage deglitch time		VM falling, UVLO report		11.5		µs
V_{CPUV}	Charge pump undervoltage lockout		VCP falling, CPUV report	V_{VM} + 1.4	V_{VM} + 2.5	V_{VM} + 3.1	V
V_{GS_CLAMP}	High-side gate clamp		Positive clamping voltage	15	16.5	19	V
			Negative clamping voltage		–0.7		
V_{OLA}	Open load active mode detection threshold		DLx – VDRAIN	150	300	430	mV
			SLx – SHx, –1 < SLx < 0	150	300	500	
I_{OL}	Open load current				2.5		mA
t_{OLP}	Open load passive diagnostic delay	SPI Device	OLP_SHRT_DLY = 00b		0.25		ms
			OLP_SHRT_DLY = 01b		1.25		
			OLP_SHRT_DLY = 10b		5		
			OLP_SHRT_DLY = 11b		11.5		
		H/W Device	After t_{WAKE} and t_{SHORTS} elapse		5		

Electrical Characteristics (continued)

Over recommended operating conditions 5.5 ≤ V_{VM} ≤ 60 V (unless otherwise noted). Typical limits apply for V_{VM} = 24 V

PARAMETER			TEST CONDITIONS	MIN	TYP	MAX	UNIT
t_{SHORTS}	Offline short-to-battery and short-to-GND diagnostic delay	SPI Device	OLP_SHRT_DLY = 00b		0.1		ms
			OLP_SHRT_DLY = 01b		0.5		
			OLP_SHRT_DLY = 10b		2		
			OLP_SHRT_DLY = 11b		4.4		
		H/W Device	After t_{WAKE} elapses		2		
V_{VDS_OCP}	V_{DS} overcurrent trip voltage	SPI Device	VDS_LVL = 0000b	0.01	0.06	0.11	V
			VDS_LVL = 0001b	0.08	0.13	0.18	
			VDS_LVL = 0010b	0.15	0.2	0.25	
			VDS_LVL = 0011b	0.2	0.26	0.32	
			VDS_LVL = 0100b	0.24	0.31	0.38	
			VDS_LVL = 0101b	0.38	0.45	0.52	
			VDS_LVL = 0110b	0.45	0.53	0.61	
			VDS_LVL = 0111b	0.51	0.6	0.69	
			VDS_LVL = 1000b	0.59	0.68	0.77	
			VDS_LVL = 1001b	0.64	0.75	0.86	
			VDS_LVL = 1010b	0.81	0.94	1.07	
			VDS_LVL = 1011b	0.97	1.13	1.29	
			VDS_LVL = 1100b	1.14	1.3	1.46	
			VDS_LVL = 1101b	1.34	1.5	1.66	
			VDS_LVL = 1110b	1.52	1.7	1.88	
			VDS_LVL = 1111b	1.69	1.88	2.07	
		H/W Device	VDS = Tied to AGND	0.01	0.06	0.11	
			VDS = 18 kΩ ± 5% tied to AGND	0.08	0.13	0.18	
			VDS = 75 kΩ ± 5% tied to AGND	0.2	0.26	0.32	
			VDS = Hi-Z	0.51	0.6	0.69	
			VDS = 75 kΩ ± 5% tied to DVDD	0.97	1.13	1.29	
			VDS = 18 kΩ ± 5% tied to DVDD	1.69	1.88	2.07	
			VDS = Tied to DVDD		Disabled		
t_{OCP_DEG}	V_{DS} and V_{SENSE} overcurrent deglitch time	SPI Device	OCP_DEG=000b		2.5		µs
			OCP_DEG = 001b		4.75		
			OCP_DEG = 010b		6.75		
			OCP_DEG = 011b		8.75		
			OCP_DEG = 100b		10.25		
			OCP_DEG = 101b		11.5		
			OCP_DEG = 110b		16.5		
			OCP_DEG = 111b		20.5		
		H/W Device			4.75		
V_{SEN_OCP}	V_{SENSE} overcurrent trip voltage	SPI Device	SEN_LVL = 00b		0.25		V
			SEN_LVL = 01b		0.5		
			SEN_LVL = 10b		0.75		
			SEN_LVL = 11b		1		
		H/W Device			1		
t_{RETRY}	Overcurrent fault retry time	SPI Device	TRETRY = 00b		2		ms
			TRERTY = 01b		4		
			TRETRY = 10b		6		
			TRETRY = 11b		8		
T_{HYS}	Thermal hysteresis		Die temperature, T_J		20		°C
T_{OTSD}	Thermal shutdown temperature		Die temperature, T_J	150	170	188	°C
T_{OTW}	Thermal warning temperature		Die temperature, T_J	130	150	169	°C

8.6 SPI Timing Requirements

Over recommended operating conditions unless otherwise noted. Typical limits apply for V_{VM} = 24 V

			MIN	NOM	MAX	UNIT
t_{READY}	SPI ready after enable	VM > UVLO, ENABLE = 3.3 V			1	ms
t_{CLK}	SCLK minimum period		100			ns
t_{CLKH}	SCLK minimum high time		50			ns
t_{CLKL}	SCLK minimum low time		50			ns
t_{SU_SDI}	SDI input data setup time		20			ns
t_{H_SDI}	SDI input data hold time		30			ns
t_{D_SDO}	SDO output data delay time	SCLK high to SDO valid, C_L = 20 pF			30	ns
t_{SU_nSCS}	nSCS input setup time		50			ns
t_{H_nSCS}	nSCS input hold time		50			ns
t_{HI_nSCS}	nSCS minimum high time before active low		500			ns
t_{DIS_nSCS}	nSCS disable time	nSCS high to SDO high impedance		10		ns

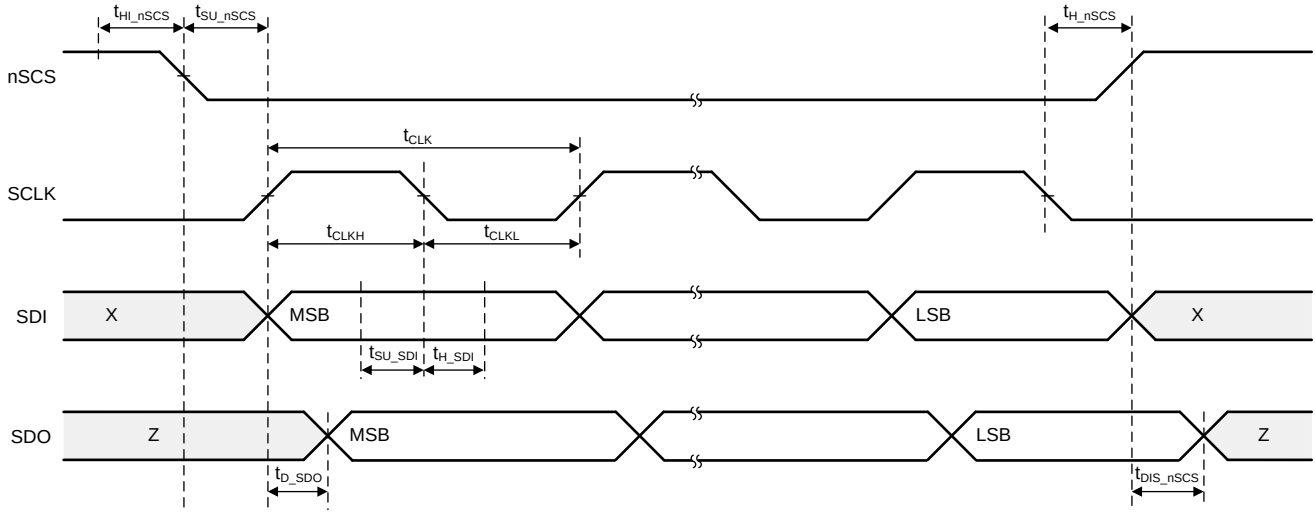
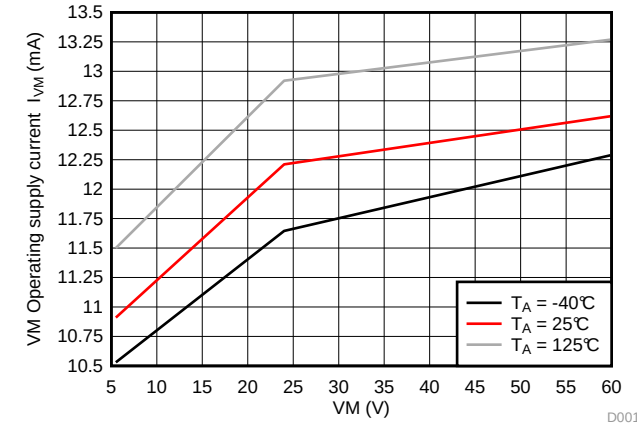


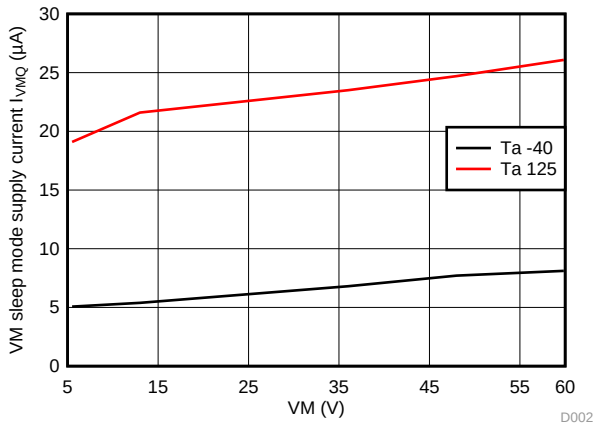
図 1. SPI Slave Mode Timing Diagram

8.7 Typical Characteristics



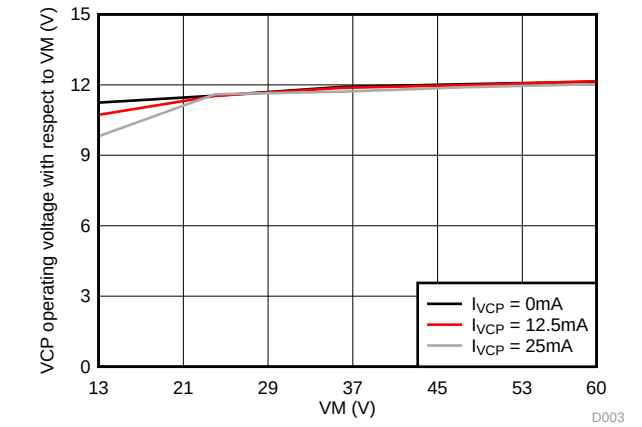
No PWM Switching

図 2. VM Operating Supply Current



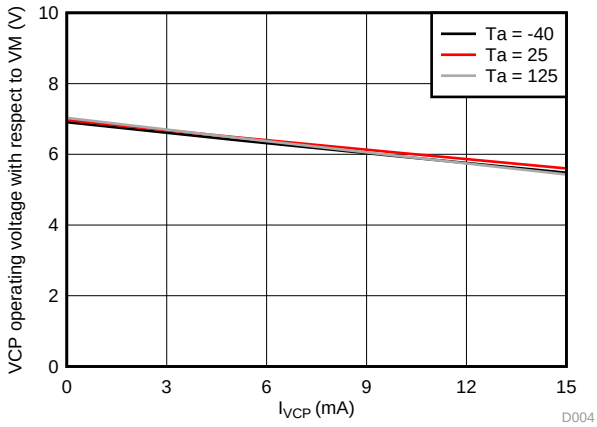
ENABLE = 0V

図 3. VM Sleep Mode Supply Current



T_A = 25°C

図 4. VCP w.r.t VM over VM voltage > 13V



VM = 8V

図 5. VCP w.r.t VM over output load I_{VCP}

9 Detailed Description

9.1 Overview

The DRV8343-Q1 device is an integrated gate driver for three-phase motor driver automotive applications. These devices decrease system complexity by integrating three independent half-bridge gate drivers, charge pump, and linear regulator for the supply voltages of the high-side and low-side gate drivers.The device also integrates three current shunt (or current sense) amplifiers. A standard serial peripheral interface (SPI) provides a simple method for configuring the various device settings and reading fault diagnostic information through an external controller. Alternatively, a hardware interface (H/W) option allows for configuring the most common settings through fixed external resistors.

The gate drivers support external N-channel high-side and low-side power MOSFETs and can drive up to 1-A source, 2-A sink peak currents. A doubler charge pump generates the supply voltage of the high-side gate drive. This charge pump architecture regulates the VCP output voltage for driving high-side power MOSFET. The supply voltage of the low-side gate driver is generated using a linear regulator from the VM power supply that regulates for driving low-side power MOSFET. A Smart Gate Drive architecture provides the ability to dynamically adjust the strength of the gate drive output current which lets the gate driver control the V_{DS} switching speed of the power MOSFET. This feature lets the user remove the external gate drive resistors and diodes, reducing the component count in the bill of materials (BOM), cost, and area of the printed circuit board (PCB). The architecture also uses an internal state machine to protect against short-circuit events in the gate driver, control the half-bridge dead time, and protect against dV/dt parasitic turnon of the external power MOSFET.

The DRV8343-Q1 device integrates three bidirectional current sense amplifiers for monitoring the current level through each of the external half-bridges using a low-side shunt resistor. The gain setting of the current sense amplifiers can be adjusted through the SPI or hardware interface. The SPI method providing additional flexibility to adjust the output bias point.

In addition to the high level of device integration, the DRV8343-Q1 device provides a wide range of integrated protection features. These features include power supply undervoltage lockout (UVLO), charge pump undervoltage lockout (CPUV), short to supply (SHT_BAT), short-to-ground (SHT_GND), open-load detection (OLD), V_{DS} overcurrent monitoring (OCP), gate driver short-circuit detection (GDF), and overtemperature shutdown (OTW and OTSD). Fault events are indicated by the nFAULT pin with detailed information available in the SPI registers on the SPI device version.

The DRV8343-Q1 device is available in a 0.5-mm pin pitch, 7 × 7 mm, HTQFP surface-mount package.

9.2 Functional Block Diagram

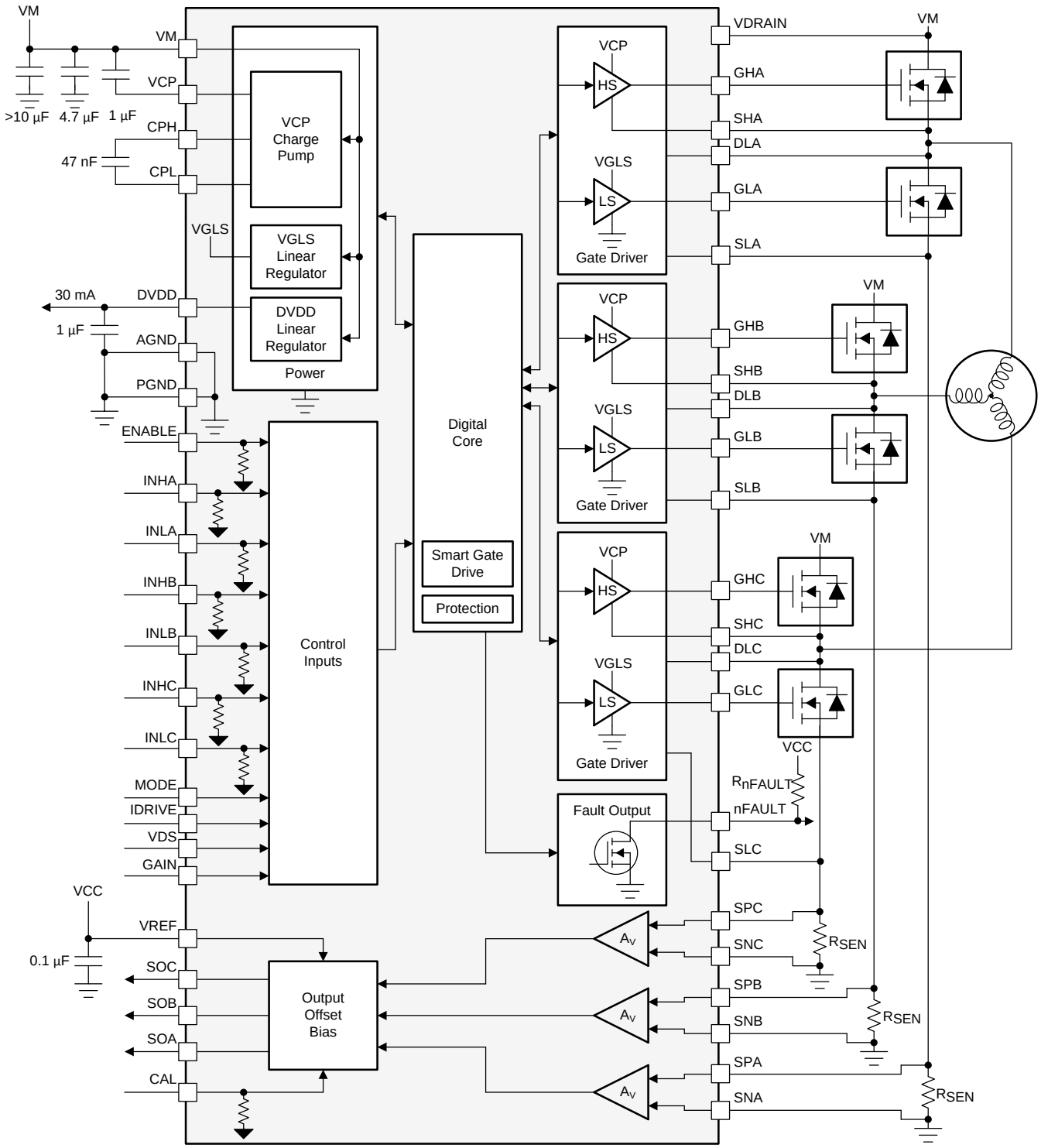


図 6. Block Diagram for DRV8343H

Functional Block Diagram (continued)

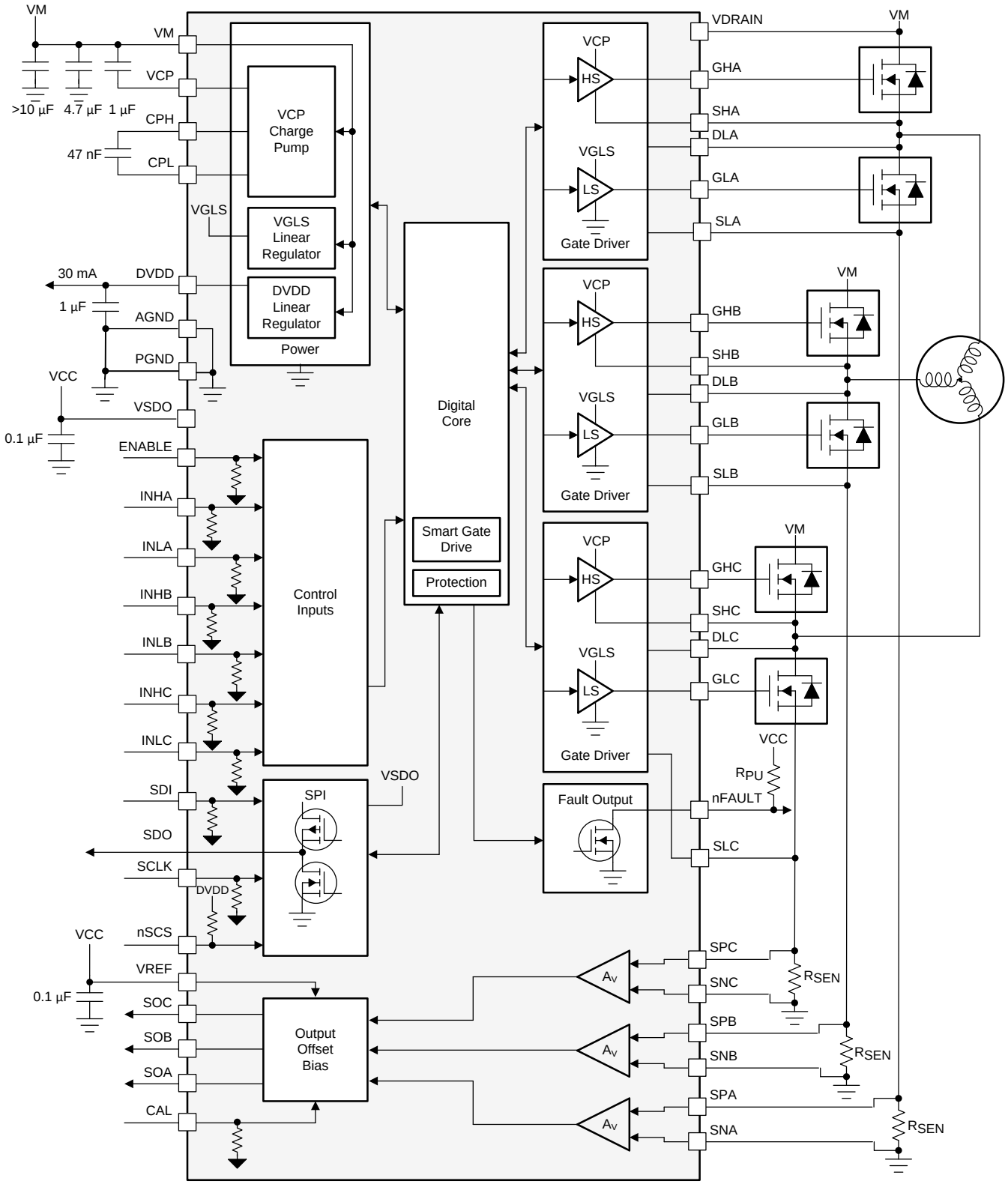


図 7. Block Diagram for DRV8343S

9.3 Feature Description

9.3.1 Three Phase Smart Gate Drivers

The DRV8343-Q1 device integrates three, half-bridge gate drivers, each capable of driving high-side and low-side N-channel power MOSFETs. A doubler charge pump provides the correct gate bias voltage to the high-side MOSFET across a wide operating voltage range in addition to providing 100% support of the duty cycle. An internal linear regulator provides the gate bias voltage for the low-side MOSFETs. The half-bridge gate drivers can be used in combination to drive a three-phase motor or separately to drive other types of loads.

The DRV8343-Q1 device implements a Smart Gate Drive architecture which allows the user to dynamically adjust the gate drive current without requiring external resistors to limit the gate current. Additionally, this architecture provides a variety of protection features for the external MOSFETs including automatic dead time insertion, prevent of parasitic dV/dt gate turnon, and gate fault detection.

9.3.1.1 PWM Control Modes

The DRV8343-Q1 device provides eight different PWM control modes in the SPI device and seven different modes in the H/W device to support various commutation and control methods. Texas Instruments does not recommend changing the MODE pin or PWM_MODE register during operation of the power MOSFETs. Set all INHx and INLx pins to logic low before making a MODE pin or PWM_MODE register change. 表 1 shows the different mode settings for the SPI device. The MODE bit setting of 100b is not available in the H/W device.

表 1. 6x PWM Mode Truth Table

H/W DEVICE	SPI DEVICE	MODE SETTINGS
Tied to AGND	000b	6x PWM
18 kΩ to AGND	001b	3x PWM
75 kΩ to AGND	010b	1x PWM
Hi-Z	011b	Independent half-bridge (for all three half-bridges)
Not Available	100b	Phases A and B are independent half-bridges, Phase C is independent FET
75 kΩ to DVDD	101b	Phases B and C are independent half-bridges, Phase A is independent FET
18 kΩ to DVDD	110b	Phases A is independent half-bridge, Phase B and C are independent FET
0.47 kΩ to DVDD	111b	Independent MOSFET (for all three half-bridges)

9.3.1.1.1 6x PWM Mode (PWM_MODE = 000b or MODE Pin Tied to AGND)

In 6x PWM mode, each half-bridge supports three output states: low, high, or high-impedance (Hi-Z). The corresponding INHx and INLx signals control the output state as listed in 表 2.

表 2. 6x PWM Mode Truth Table

INLx	INHx	GLx	GHx	SHx + DLx
0	0	L	L	Hi-Z
0	1	L	H	H
1	0	H	L	L
1	1	L	L	Hi-Z

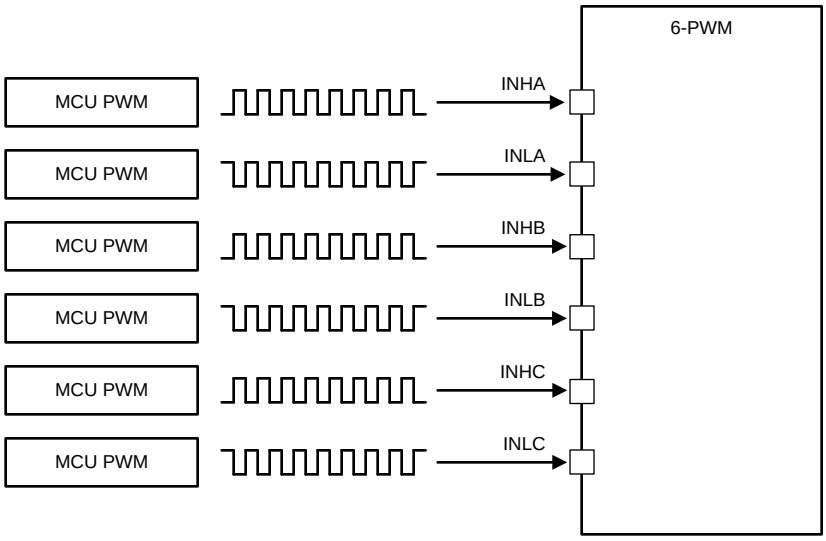


図 8. 6-PWM Mode

9.3.1.1.2 3x PWM Mode (PWM_MODE = 001b or MODE Pin = 18 kΩ to AGND)

In 3x PWM mode, the INHx pin controls each half-bridge and supports two output states: low or high. The INLx pin is used to put the half bridge in the Hi-Z state. If the Hi-Z state is not required, tie all INLx pins to logic high. The corresponding INHx and INLx signals control the output state as listed in 表 3.

表 3. 3x PWM Mode Truth Table

INLx	INHx	GLx	GHx	SHx + DLx
0	X	L	L	Hi-Z
1	0	H	L	L
1	1	L	H	H

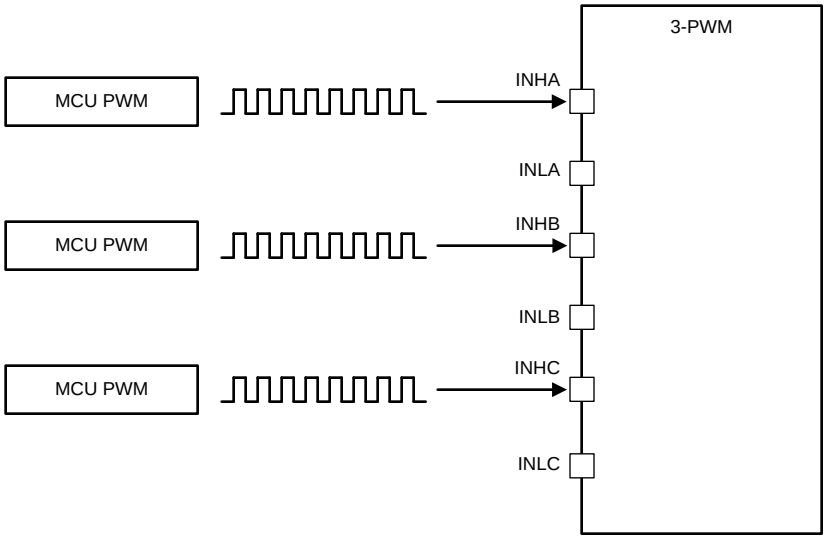


図 9. 3-PWM Mode

9.3.1.1.3 1x PWM Mode (PWM_MODE = 010b or MODE Pin = 75 kΩ to AGND)

In 1x PWM mode, the DRV8343-Q1 device uses 6-step block commutation tables that are stored internally. This feature allows for a three-phase BLDC motor to be controlled using one PWM sourced from a simple controller. The PWM is applied on the INHA pin and determines the output frequency and duty cycle of the half-bridges.

The half-bridge output states are managed by the INLA, INHB, and INLB pins which are used as state logic inputs. The state inputs can be controlled by an external controller or connected directly to the digital outputs of the Hall effect sensor from the motor (INLA = HALL_A, INHB = HALL_B, INLB = HALL_C). The 1x PWM mode usually operates with synchronous rectification (low-side MOSFET recirculation); however, the mode can be configured to use asynchronous rectification (MOSFET body diode freewheeling) on SPI devices. This configuration is set using the 1PWM_COM bit in the SPI registers.

The INHC input controls the direction through the 6-step commutation table which is used to change the direction of the motor when Hall effect sensors are directly controlling the state of the INLA, INHB, and INLB inputs. Tie the INHC pin low if this feature is not required.

The INLC input brakes the motor by turning off all high-side MOSFETs and turning on all low-side MOSFETs when the INLC pin is pulled low. This brake is independent of the state of the other input pins. Tie the INLC pin high if this feature is not required. In the SPI device, the brake and coast mode can also be selected by the 1PWM_BRAKE register (see 表 21).

表 4. Synchronous 1x PWM Mode

LOGIC AND HALL INPUTS							GATE DRIVE OUTPUTS(1)						
STATE	INHC = 0			INHC = 1			PHASE A		PHASE B		PHASE C		DESCRIPTION
	INLA	INHB	INLB	INLA	INHB	INLB	GHA	GLA	GHB	GLB	GHC	GLC	
Stop	0	0	0	0	0	0	L	L	L	L	L	L	Stop
Align	1	1	1	1	1	1	PWM	!PWM	L	H	L	H	Align
1	1	1	0	0	0	1	L	L	PWM	!PWM	L	H	B → C
2	1	0	0	0	1	1	PWM	!PWM	L	L	L	H	A → C
3	1	0	1	0	1	0	PWM	!PWM	L	H	L	L	A → B
4	0	0	1	1	1	0	L	L	L	H	PWM	!PWM	C → B
5	0	1	1	1	0	0	L	H	L	L	PWM	!PWM	C → A
6	0	1	0	1	0	1	L	H	PWM	!PWM	L	L	B → A

(1) *!PWM* is the inverse of the PWM signal.

表 5. Asynchronous 1x PWM Mode 1PWM_COM = 1 (SPI Only)

LOGIC AND HALL INPUTS							GATE DRIVE OUTPUTS						
STATE	INHC = 0			INHC = 1			PHASE A		PHASE B		PHASE C		DESCRIPTION
	INLA	INHB	INLB	INLA	INHB	INLB	GHA	GLA	GHB	GLB	GHC	GLC	
Stop	0	0	0	0	0	0	L	L	L	L	L	L	Stop
Align	1	1	1	1	1	1	PWM	L	L	H	L	H	Align
1	1	1	0	0	0	1	L	L	PWM	L	L	H	B → C
2	1	0	0	0	1	1	PWM	L	L	L	L	H	A → C
3	1	0	1	0	1	0	PWM	L	L	H	L	L	A → B
4	0	0	1	1	1	0	L	L	L	H	PWM	L	C → B
5	0	1	1	1	0	0	L	H	L	L	PWM	L	C → A
6	0	1	0	1	0	1	L	H	PWM	L	L	L	B → A

図 10 and 図 11 show the different possible configurations in 1x PWM mode.

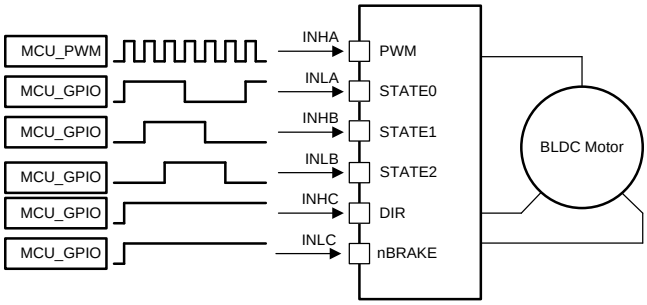


図 10. 1x PWM—Simple Controller

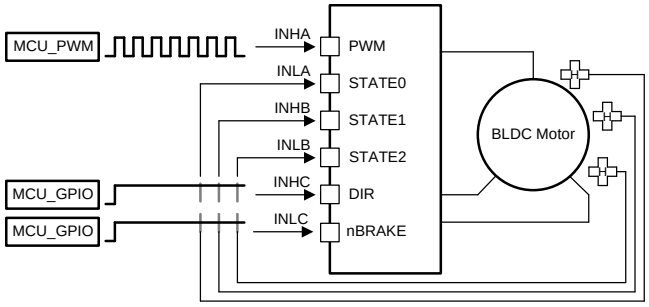


図 11. 1x PWM—Hall Effect Sensor

9.3.1.1.4 Independent Half-Bridge PWM Mode (PWM_MODE = 011b or MODE Pin is > 1.5 MΩ to AGND or Hi-Z)

In independent half-bridge PWM mode, the INHx pin controls each half-bridge independently and supports two output states: low or high. The corresponding INHx and INLx signals control the output state as listed in 表 6. The INLx pin is used to change the half-bridge to high impedance. If the high-impedance (Hi-Z) state is not required, tie all INLx pins logic high.

表 6. Independent Half-Bridge Mode Truth Table

INLx	INHx	GLx	GHx
0	X	L	L
1	0	H	L
1	1	L	H

9.3.1.1.5 Phases A and B are Independent Half-Bridges, Phase C is Independent FET (MODE = 100b)

In this mode, phases A and B are independent half-bridge control, with independent fault handling and dead time enforcement by the device. Phase C is independent FET mode where the dead time inserted by the device is bypassed and both MOSFETs can be turned-on at the same time. This mode is not available in the H/W version.

9.3.1.1.6 Phases B and C are Independent Half-Bridges, Phase A is Independent FET (MODE = 101b or MODE Pin is 75 kΩ to DVDD)

In this mode, phases B and C are independent half-bridge control, with independent fault handling and dead time enforcement by the device. Phase A is independent FET mode where the dead time inserted by the device is bypassed and both MOSFETs can be turned-on at the same time.

9.3.1.1.7 Phases A is Independent Half-Bridge, Phases B and C are Independent FET (MODE = 110b or MODE Pin is 18 kΩ to DVDD)

In this mode, phase A is independent half-bridge control, with dead time enforcement by the device. Phases B and C are independent FET mode where the dead time is bypassed and both MOSFETs in a given phase can be turned-on at the same time. Fault handling is also done independently for each FET in phases B and C.

9.3.1.1.8 Independent MOSFET Drive Mode (PWM_MODE = 111b or MODE Pin = 0.47 kΩ to DVDD)

In independent MOSFET drive mode, the INHx and INLx pins control the outputs, GHx and GLx, respectively. This control mode lets the DRV8343-Q1 device drive separate high-side and low-side loads with each half-bridge. These types of loads include unidirectional brushed DC motors, solenoids, and low-side and high-side switches. In this mode, turning on both the high-side and low-side MOSFETs at the same time in a given half-bridge gate driver is possible to use the device as a high-side or low-side driver. The dead time (t_{DEAD}) is bypassed in the mode and must be inserted by the external MCU.

表 7. Independent PWM Mode Truth Table

INLx	INHx	GLx	GHx
0	0	L	L
0	1	L	H
1	0	H	L
1	1	H	H

図 12 shows how the DRV8343-Q1 device can be used to connect a high-side load and a low-side load at the same time with one half-bridge and drive the loads independently. In this mode, the VDS monitors are active for both the MOSFETs to protect from an overcurrent condition.

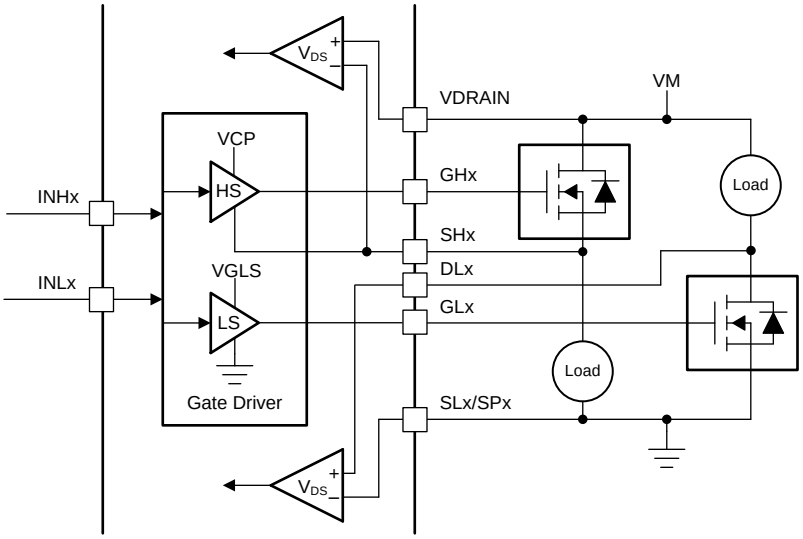


図 12. Independent PWM High-Side and Low-Side Drivers

If the half-bridge is used to implement only a high-side or low-side driver, using the VDS monitors to help protect from an overcurrent condition is possible as shown in 図 13 or 図 14. The unused gate driver can stay disconnected.

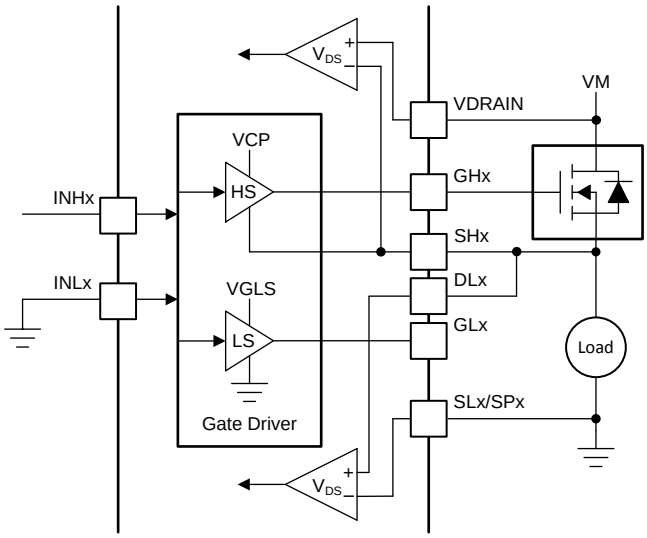


図 13. One High-Side Driver

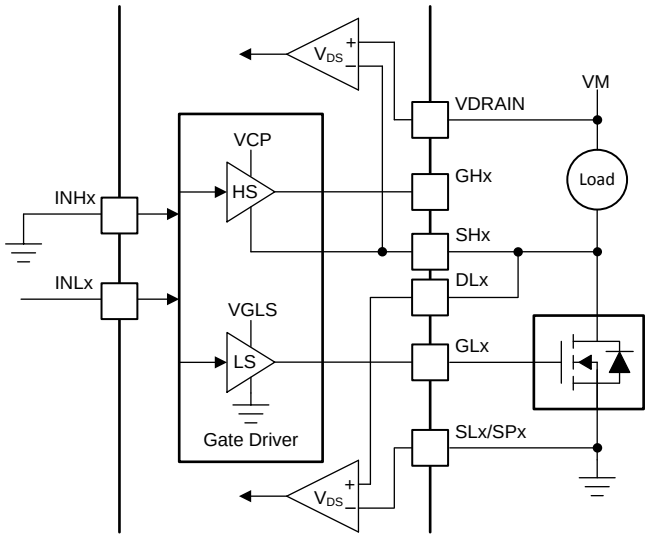


図 14. One Low-Side Driver

図 15 shows how the DRV8343-Q1 device can be used to connect a solenoid load where both the high-side and low-side MOSFETs can be turned on at the same time to drive the load without causing shoot-through. TI recommends having the external diodes for current recirculation. If a half-bridge is not used, the gate pins (GHx and GLx) can stay unconnected and the sense pins (SHx and DLx) can be tied directly or with a resistor to GND.

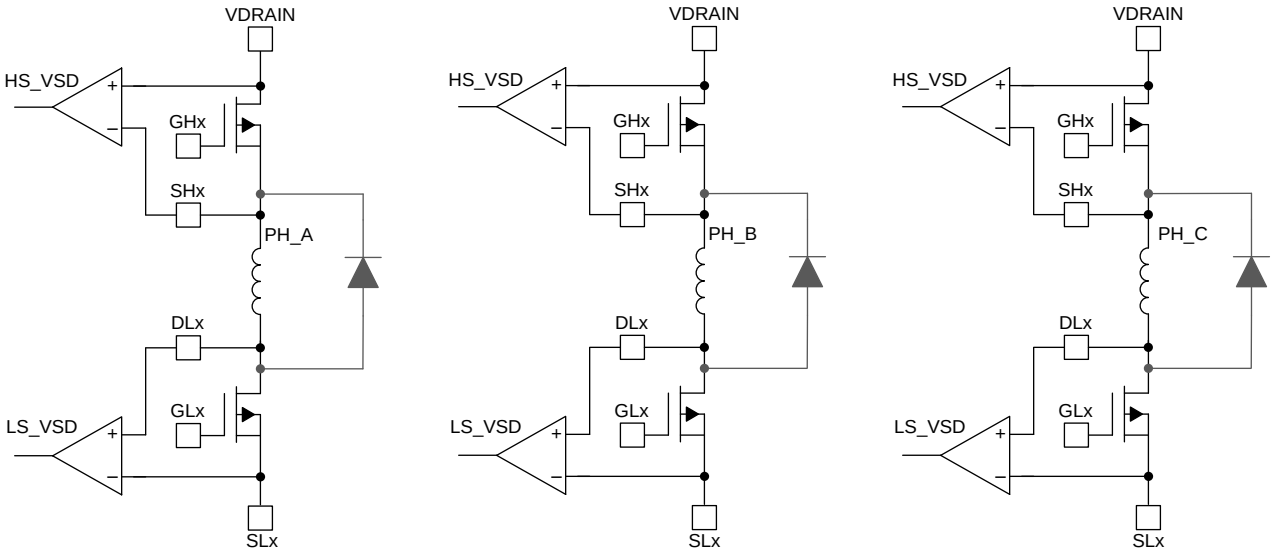


図 15. Solenoid Drive Configuration

9.3.1.2 Device Interface Modes

The DRV8343-Q1 device supports two different interface modes (SPI and hardware) to let the end application design for either flexibility or simplicity. The two interface modes share the same four pins, allowing the different versions to be pin-to-pin compatible. This compatibility lets application designers evaluate with one interface version and potentially switch to another with minimal modifications to their circuit design and layout.

9.3.1.2.1 Serial Peripheral Interface (SPI)

The SPI devices support a serial communication bus that lets an external controller send and receive data with the DRV8343-Q1 device. This support lets the external controller configure device settings and read detailed fault information. The interface is a four wire interface using the SCLK, SDI, SDO, and nSCS pins which are described as follows:

- The SCLK pin is an input that accepts a clock signal to determine when data is captured and propagated on the SDI and SDO pins.
- The SDI pin is the data input.
- The SDO pin is the data output. The SDO pin has a push-pull output structure.
- The nSCS pin is the chip select input. A logic low signal on this pin enables SPI communication with the DRV8343-Q1 device.

For more information on the SPI, see the *SPI Communication* section.

9.3.1.2.2 Hardware Interface

Hardware interface devices convert the four SPI pins into four resistor-configurable inputs which are GAIN, IDRIVE, MODE, and VDS. This conversion lets the application designer configure the most common device settings by tying the pin logic high or logic low, or with a simple pullup or pulldown resistor. This removes the requirement for an SPI bus from the external controller. General fault information can still be obtained through the nFAULT pin.

- The GAIN pin configures the gain of the current sense amplifier.
- The IDRIVE pin configures the gate drive current strength.
- The MODE pin configures the PWM control mode.
- The VDS pin configures the voltage threshold of the V_{DS} overcurrent monitors.

For more information on the hardware interface, see the *Pin Diagrams* section.

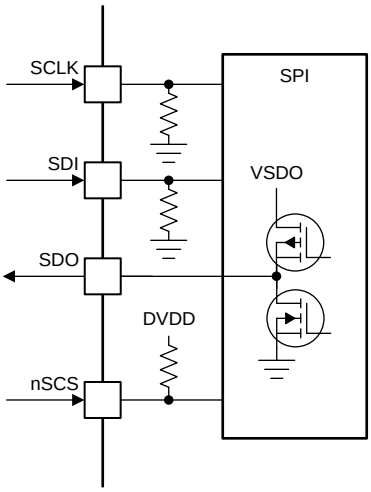


図 16. SPI

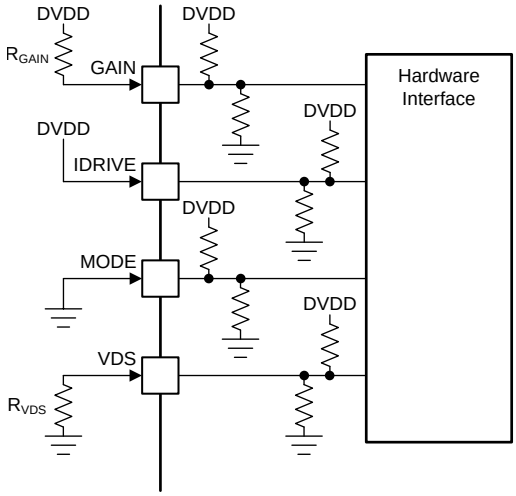


図 17. Hardware Interface

9.3.1.3 Gate Driver Voltage Supplies

The voltage supply for the high-side gate driver is created using a doubler charge pump that operates from the VM voltage supply input. The charge pump lets the gate driver correctly bias the high-side MOSFET gate with respect to the source across a wide input supply voltage range. The charge pump is regulated to keep a fixed output voltage V_{VCP} and supports an average output current I_{GATE_HS}. The charge pump is continuously monitored for undervoltage events to prevent under-driven MOSFET conditions. The charge pump requires a ceramic capacitor between the VM and VCP pins to act as the storage capacitor. Additionally, a flying capacitor is required between the CPH and CPL pins.

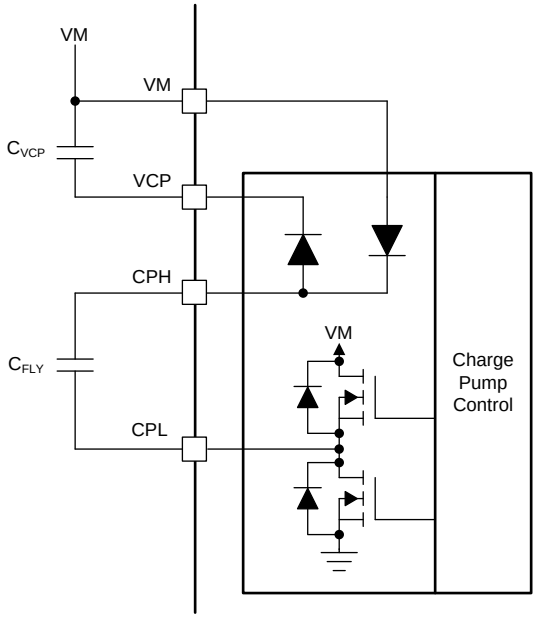


図 18. Charge Pump Architecture

The voltage supply of the low-side gate driver is created using a linear regulator that operates from the VM voltage supply input. The linear regulator lets the gate driver correctly bias the low-side MOSFET gate with respect to ground. The linear regulator output is V_{GSL} and supports an output current I_{GATE_LS}.

9.3.1.4 Smart Gate Drive Architecture

The DRV8343-Q1 gate drivers use an adjustable, complimentary, push-pull topology for both the high-side and low-side drivers. This topology allows for both a strong pullup and pulldown of the external MOSFET gates.

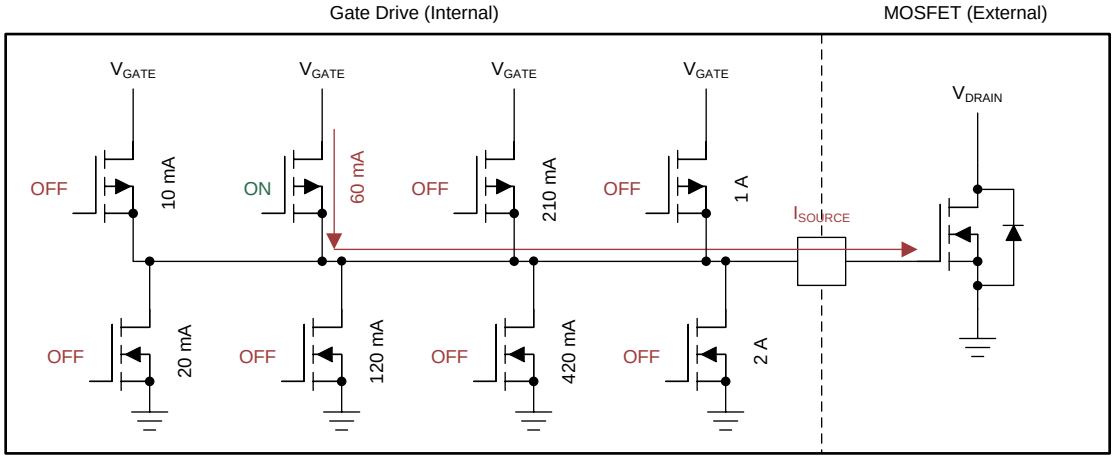


図 19. Charge Pump Architecture

Additionally, the gate drivers use a Smart Gate Drive architecture to provide additional control of the external power MOSFETs, additional steps to protect the MOSFETs, and optimal tradeoffs between efficiency and robustness. This architecture is implemented through two components called IDRIVE and TDRIVE which are described in the *IDRIVE: MOSFET Slew-Rate Control* section and *TDRIVE: MOSFET Gate Drive Control* section. 図 20 shows the high-level functional block diagram of the gate driver.

The IDRIVE gate drive current and TDRIVE gate drive time should be initially selected based on the parameters of the external power MOSFET used in the system and the desired rise and fall times (see the *Application and Implementation* section).

The high-side gate driver also implements a Zener clamp diode to help protect the external MOSFET gate from overvoltage conditions in the case of external short-circuit events on the MOSFET.

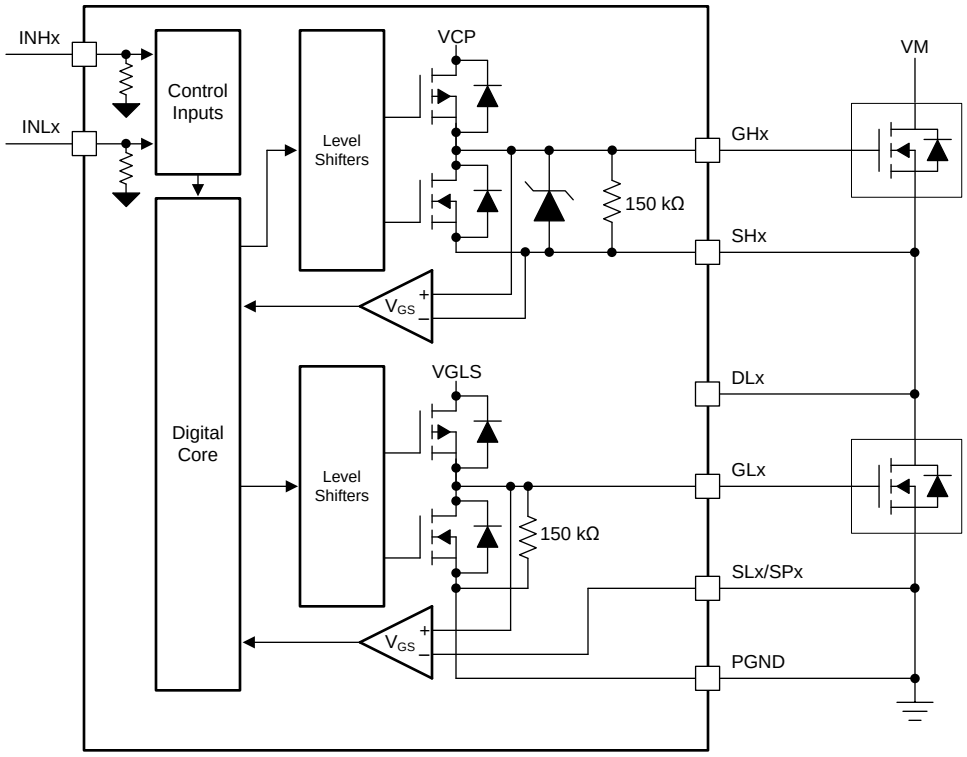


図 20. Gate Driver Block Diagram

9.3.1.4.1 IDRIVE: MOSFET Slew-Rate Control

The IDRIVE component implements adjustable gate drive current to control the MOSFET V_{DS} slew rates. The MOSFET V_{DS} slew rates are a critical factor for optimizing radiated emissions, energy, and duration of diode recovery spikes, dV/dt gate turnon resulting in shoot-through, and switching voltage transients related to parasitics in the external half-bridge. The IDRIVE component operates on the principal that the MOSFET V_{DS} slew rates are predominately determined by the rate of gate charge (or gate current) delivered during the MOSFET Q_{GD} or Miller charging region. By letting the gate driver adjust the gate current, the gate driver can effectively control the slew rate of the external power MOSFETs.

The IDRIVE component lets the DRV8343-Q1 device dynamically switch between gate drive currents either through a register setting on SPI devices or the IDRIVE pin on hardware interface devices. The SPI devices provide 16 I_{DRIVE} settings ranging from 1.5-mA to 1-A source and 3-mA to 2-A sink. Hardware interface devices provide 7 I_{DRIVE} settings within the same ranges. The setting of the gate drive current is delivered to the gate during the turnon and turnoff of the external power MOSFET for the t_{DRIVE} duration. After the MOSFET turnon or turnoff, the gate driver switches to a smaller hold current (I_{HOLD}) to improve the gate driver efficiency. In the event of an overcurrent condition, the IDRIVE component is automatically decreased to help prevent device damage. For additional details on the IDRIVE settings, see the *Register Maps* section for the SPI devices and the *Pin Diagrams* section for the hardware interface devices.

9.3.1.4.2 TDRIVE: MOSFET Gate Drive Control

The TDRIVE component is an integrated gate drive state machine that provides automatic dead time insertion through handshaking between the high-side and low-side gate drivers, parasitic dV/dt gate turnon prevention, and MOSFET gate fault detection.

The first component of the TDRIVE state machine is automatic dead time insertion. Dead time is period of time between the switching of the external high-side and low-side MOSFETs to make sure that they do not cross conduct and cause shoot-through. The DRV8343-Q1 device uses V_{GS} voltage monitors to measure the MOSFET gate-to-source voltage and determine the correct time to switch instead of relying on a fixed time value. This feature lets the dead time of the gate driver adjust for variation in the system such as temperature drift and variation in the MOSFET parameters. An additional digital dead time (t_{DEAD}) can be inserted and is adjustable through the registers on SPI devices.

The second component of the TDRIVE state machine is parasitic dV/dt gate turnon prevention. To implement this component, the TDRIVE state machine enables a strong pulldown current (I_{STRONG}) on the opposite MOSFET gate whenever a MOSFET is switching. The strong pulldown occurs for the TDRIVE duration. This feature helps remove parasitic charge that couples into the MOSFET gate when the voltage half-bridge switch node slews rapidly.

The third component implements a gate-fault detection scheme to detect pin-to-pin solder defects, a MOSFET gate failure, or a MOSFET gate stuck-high or stuck-low voltage condition. This implementation is done with a pair of V_{GS} gate-to-source voltage monitors for each half-bridge gate driver. When the gate driver receives a command to change the state of the half-bridge it starts to monitor the gate voltage of the external MOSFET. If, at the end of the t_{DRIVE} period, the V_{GS} voltage has not increased the correct threshold, the gate driver reports a fault. To make sure that a false gate drive fault (GDF) is not detected, a t_{DRIVE} time should be selected that is longer than the time required to charge or discharge the MOSFET gate. The t_{DRIVE} time does not increase the PWM time and will terminate if another PWM command is received while active. In the SPI device, for IDRIVE bit settings of 0000b, 0001b, 0010b, and 0011b, a longer t_{DRIVE} time of 20-µs is automatically selected by the TDRIVE_MAX bit. If the 20-µs t_{DRVIE} time is not required, write a 0 to the TDRIVE_MAX bit to disable it and set the t_{DRIVE} time by the TDRIVE bits. For all other IDRIVE settings, writing to the TDRIVE_MAX bit is disabled. This option is not available in the H/W device.

For additional details on the TDRIVE settings, see the *Register Maps* section for SPI devices and the *Pin Diagrams* section for hardware interface devices. 図 21 shows an example of the TDRIVE state machine in operation.

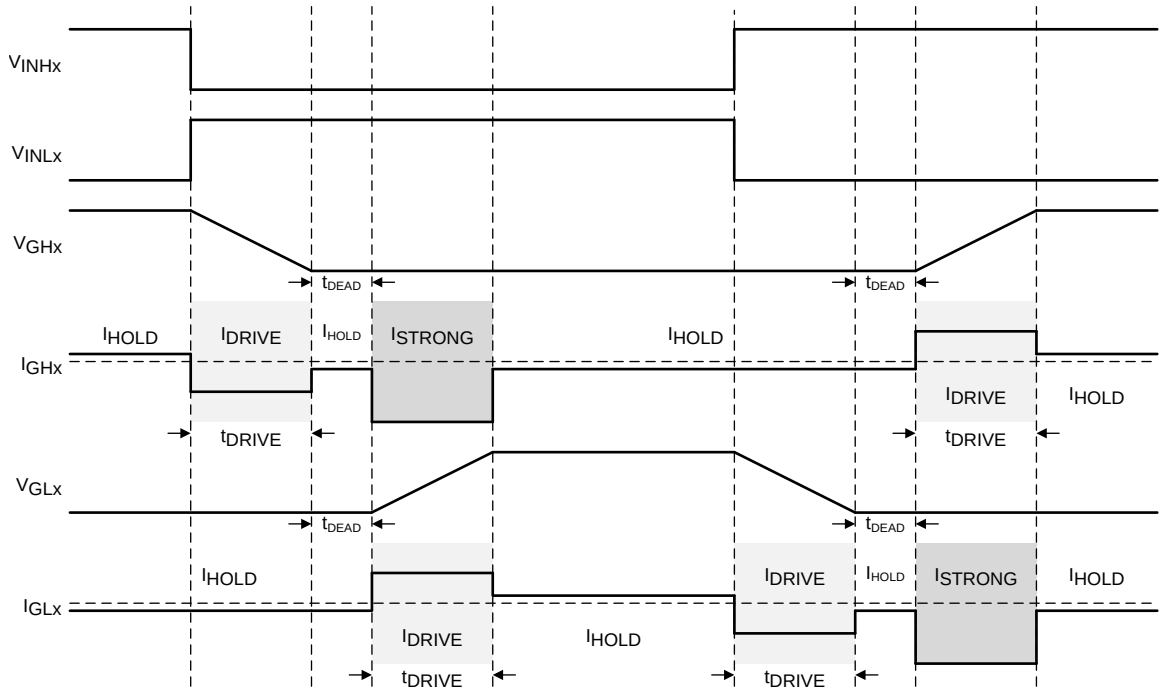


図 21. TDRIVE State Machine

9.3.1.4.3 Propagation Delay

The propagation delay time (t_{pd}) is measured as the time between an input logic edge to a detected output change. This time has three parts consisting of the digital input deglitcher delay, the digital propagation delay, and the delay through the analog gate drivers.

The input deglitcher prevents high-frequency noise on the input pins from affecting the output state of the gate drivers. To support multiple control modes and dead time insertion, a small digital delay is added as the input command propagates through the device. Lastly, the analog gate drivers have a small delay that contributes to the overall propagation delay of the device.

9.3.1.4.4 MOSFET V_{DS} Monitors

The gate drivers implement adjustable V_{DS} voltage monitors to detect overcurrent or short-circuit conditions on the external power MOSFETs. When the monitored voltage is greater than the V_{DS} trip point (V_{VDS_OCP}) for longer than the deglitch time (t_{OCP}), an overcurrent condition is detected and action is taken according to the device V_{DS} fault mode.

The high-side V_{DS} monitors measure the voltage between the VDRAIN and SHx pins.The low-side V_{DS} monitors measure the voltage between the DLx and SLx pins. If the current sense amplifier is unused, tie the SP pins to the common ground point of the external half-bridges.

For the SPI devices, the reference point of the low-side V_{DS} monitor can be changed between the SPx and SNx pins if desired with the LS_REF register setting.

The V_{VDS_OCP} threshold is programmable from 0.06 V to 1.88 V. For additional information on the V_{DS} monitor levels, see the *Register Maps* section for SPI devices and in the *Pin Diagrams* section hardware interface device.

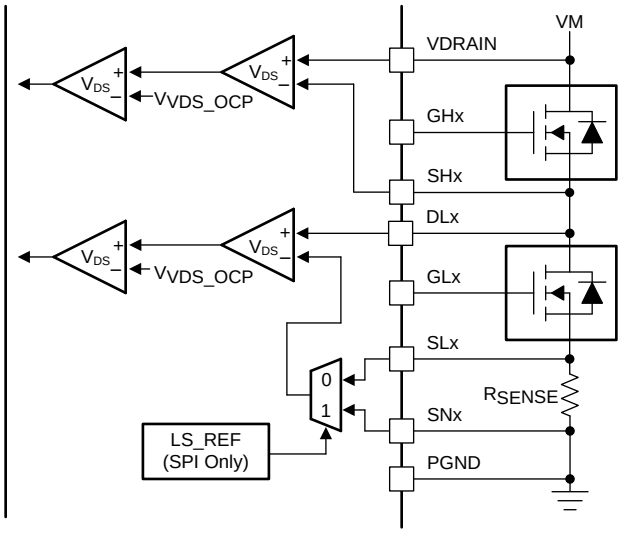


図 22. DRV8343-Q1 V_{DS} Monitors

9.3.1.4.5 VDRAIN Sense Pin

The DRV8343-Q1 device provides a separate sense pin for the common point of the high-side MOSFET drain. This pin is called VDRAIN. This pin lets the sense line for the overcurrent monitors (VDRAIN) and the power supply (VM) stay separate and prevent noise on the VDRAIN sense line. This separation also lets implementation of a small filter on the gate driver supply (VM) or insertion of a boost converter to support lower voltage operation if desired. Care must still be used when designing the filter or separate supply because VM is still the reference point for the VCP charge pump that supplies the high-side gate drive voltage (V_{GSH}). The VM supply must not drift too far from the VDRAIN supply to avoid violating the V_{GS} voltage specification of the external power MOSFETs.

9.3.1.4.6 nFAULT Pin

The nFAULT pin has an open-drain output and should be pulled up to a 5 V or 3.3 V supply. When a fault is detected, the nFAULT line is logic low. For a 3.3-V pullup the nFAULT pin can be tied to the DVDD pin with a resistor (refer to the *Application and Implementation* section). For a 5-V pullup an external 5-V supply must be used.

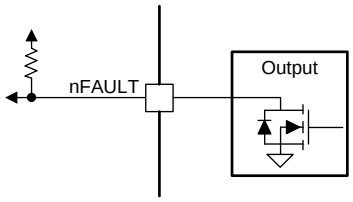


図 23. nFAULT Pin

During the power-up sequence, or when going from sleep mode, the digital core of the device is enabled to a VM voltage of approximately 3.3 V and the device is fully operational after VM exceeds 5.5 V. After the digital core is alive if the VM does not exceed 5.5 V within 100-µs the device will flag a UVLO fault. In the H/W device, the nFAULT pin is driven low. In the SPI device, the FAULT and ULVO bits will be latched high

9.3.2 DVDD Linear Voltage Regulator

A 3.3-V, 30-mA linear regulator is integrated into the DRV8343-Q1 device and is available for use by external circuitry. This regulator can provide the supply voltage for a low-power MCU or other circuitry supporting low current. The output of the DVDD regulator should be bypassed near the DVDD pin with a X5R or X7R, 1-µF, 6.3-V ceramic capacitor routed directly back to the adjacent AGND ground pin.

The DVDD nominal, no-load output voltage is 3.3 V. When the DVDD load current exceeds 30 mA, the regulator functions like a constant-current source. The output voltage drops significantly with a current load greater than 30 mA.

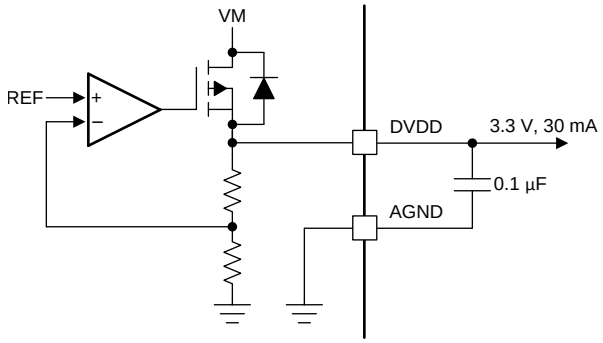


図 24. DVDD Linear Regulator Block Diagram

Use 式 1 to calculate the power dissipated in the device by the DVDD linear regulator.

$$P = \left(V_{VM} - V_{DVDD}\right) \times I_{DVDD} \quad (1)$$

For example, at a V_{VM} of 24 V, drawing 20 mA out of DVDD results in a power dissipation as shown in 式 2.

$$P = \left(24\ V - 3.3\ V\right) \times 20\ mA = 414\ mW \quad (2)$$

9.3.3 Pin Diagrams

図 25 shows the input structure for the logic level pins, INHx, INLx, CAL, ENABLE, nSCS, SCLK, and SDI. The input can be driven with a voltage or external resistor.

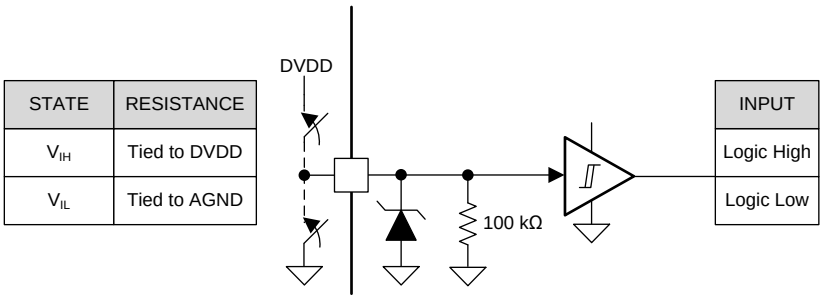


図 25. Logic-Level Input Pin Structure

図 26 shows the structure of the four level input pin, GAIN, on hardware interface devices. The input can be set with an external resistor.

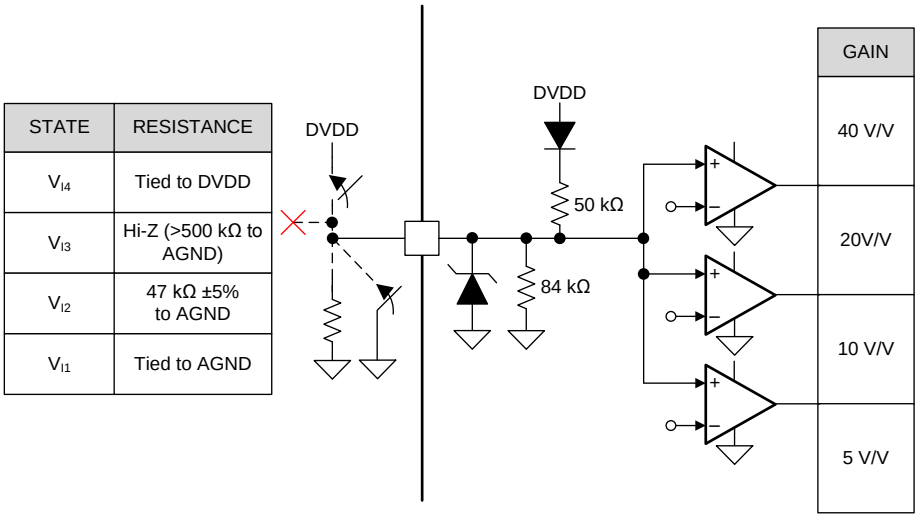
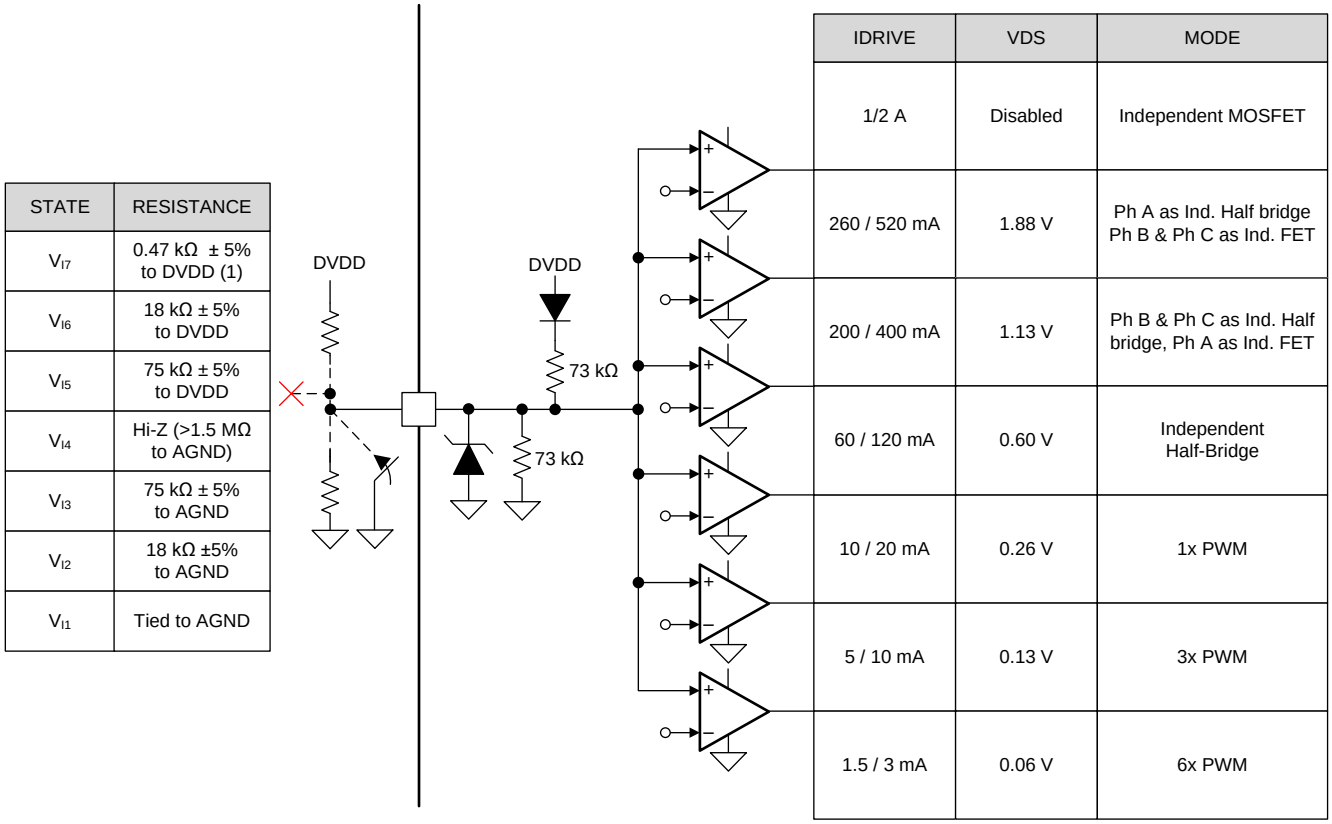


図 26. Four Level Input Pin Structure

図 27 shows the structure of the seven level input pins, MODE, IDRIVE and VDS, on hardware interface devices. The input can be set with an external resistor.

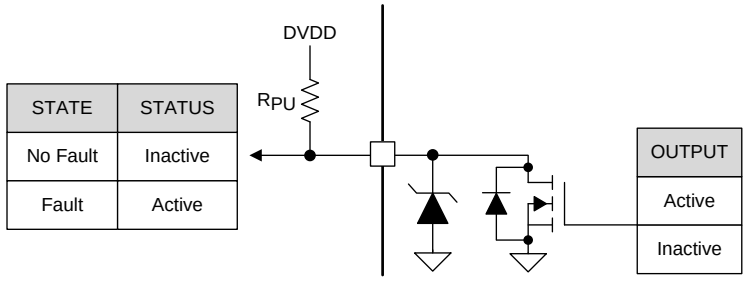


STATE	RESISTANCE
V_{I7}	0.47 kΩ ± 5% to DVDD (1)
V_{I6}	18 kΩ ± 5% to DVDD
V_{I5}	75 kΩ ± 5% to DVDD
V_{I4}	Hi-Z (>1.5 MΩ to AGND)
V_{I3}	75 kΩ ± 5% to AGND
V_{I2}	18 kΩ ±5% to AGND
V_{I1}	Tied to AGND

IDRIVE	VDS	MODE
1/2 A	Disabled	Independent MOSFET
260 / 520 mA	1.88 V	Ph A as Ind. Half bridge Ph B & Ph C as Ind. FET
200 / 400 mA	1.13 V	Ph B & Ph C as Ind. Half bridge, Ph A as Ind. FET
60 / 120 mA	0.60 V	Independent Half-Bridge
10 / 20 mA	0.26 V	1x PWM
5 / 10 mA	0.13 V	3x PWM
1.5 / 3 mA	0.06 V	6x PWM

図 27. Seven Level Input Pin Structure (1)

図 28 shows the structure of the open-drain output pin, nFAULT. The open-drain output requires an external pullup resistor to function correctly.



STATE	STATUS
No Fault	Inactive
Fault	Active

OUTPUT
Active
Inactive

図 28. Open-Drain Output Pin Structure

9.3.4 Low-Side Current Sense Amplifiers

The DRV8343-Q1 integrates three, high-performance low-side current sense amplifiers for current measurements using low-side shunt resistors in the external half-bridges. Low-side current measurements are commonly used to implement overcurrent protection, external torque control, or brushless DC commutation with the external controller. All three amplifiers can be used to sense the current in each of the half-bridge legs or one amplifier can be used to sense the sum of the half-bridge legs. The current sense amplifiers include features such as programmable gain, offset calibration, unidirectional and bidirectional support, and a voltage reference pin (VREF).

(1) V_{I7} requires a 0.47 kΩ resistor to DVDD for MODE input pin. VDS and IDRIVE pins can be directly tied to DVDD.

9.3.4.1 Bidirectional Current Sense Operation

The SOx pin on the DRV8343 outputs an analog voltage equal to the voltage across the SPx and SNx pins multiplied by the gain setting (G_{CSA}). The gain setting is adjustable between four different levels: 5 V/V, 10 V/V, 20 V/V, and 40 V/V. Use 式 3 to calculate the current through the shunt resistor.

$$I = \frac{\frac{V_{VREF}}{2} - V_{SOx}}{G_{CSA} \times R_{SENSE}} \quad (3)$$

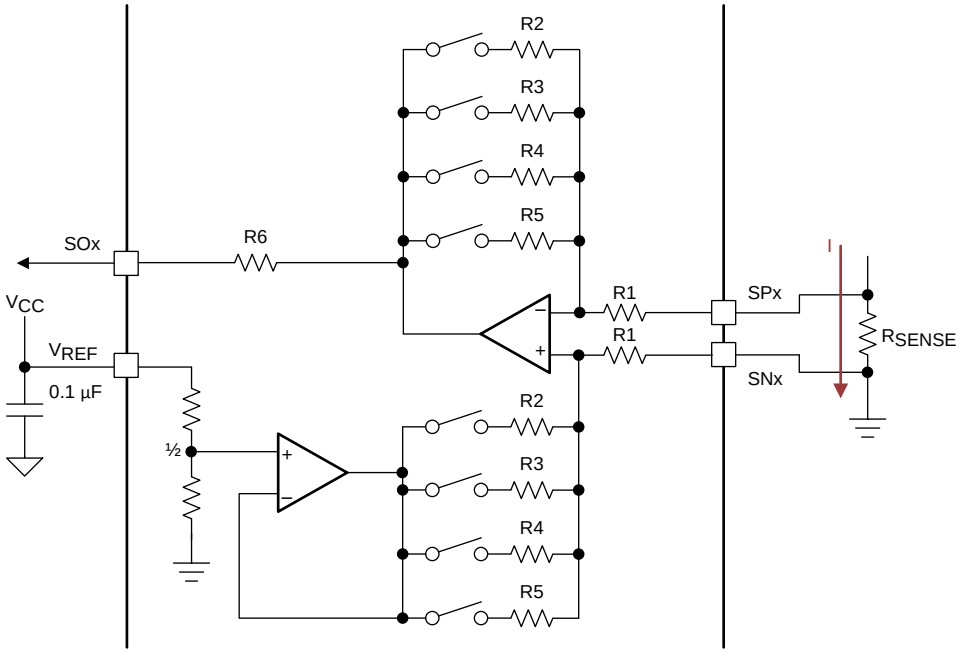


図 29. Bidirectional Current Sense Configuration

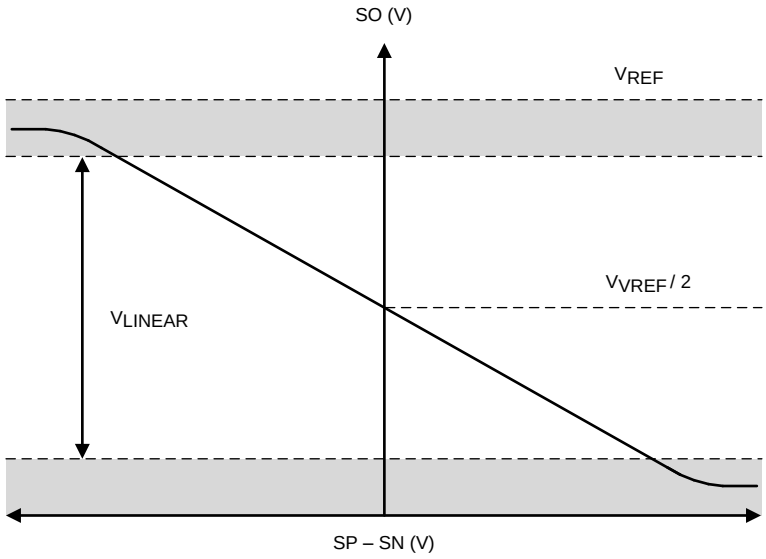


図 30. Bidirectional Current Sense Output

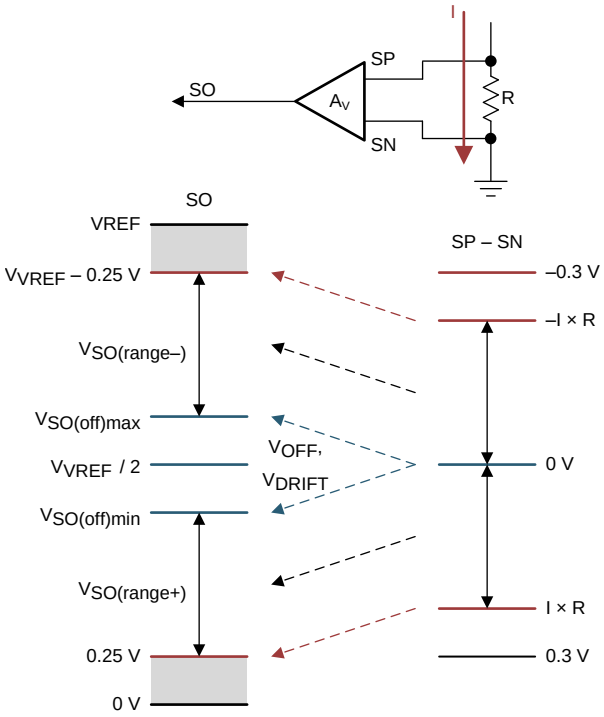


図 31. Bidirectional Current Sense Regions

9.3.4.2 Unidirectional Current Sense Operation (SPI only)

On the DRV8343-Q1 SPI device, use the VREF_DIV bit to remove the VREF divider. In this case the curren sense amplifier operates unidirectionally and the SOx pin outputs an analog voltage equal to the voltage across the SPx and SNx pins multiplied by the gain setting (G_{CSA}). Use 式 4 to calculate the current through the shunt resistor.

$$I = \frac{V_{VREF} - V_{SOx}}{G_{CSA} \times R_{SENSE}} \quad (4)$$

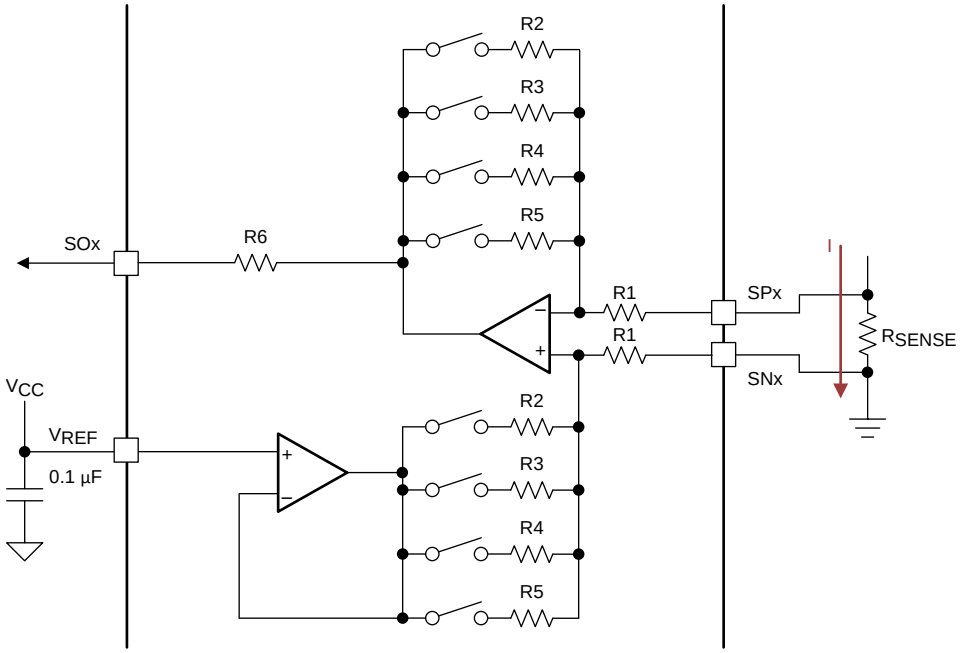


図 32. Unidirectional Current-Sense Configuration

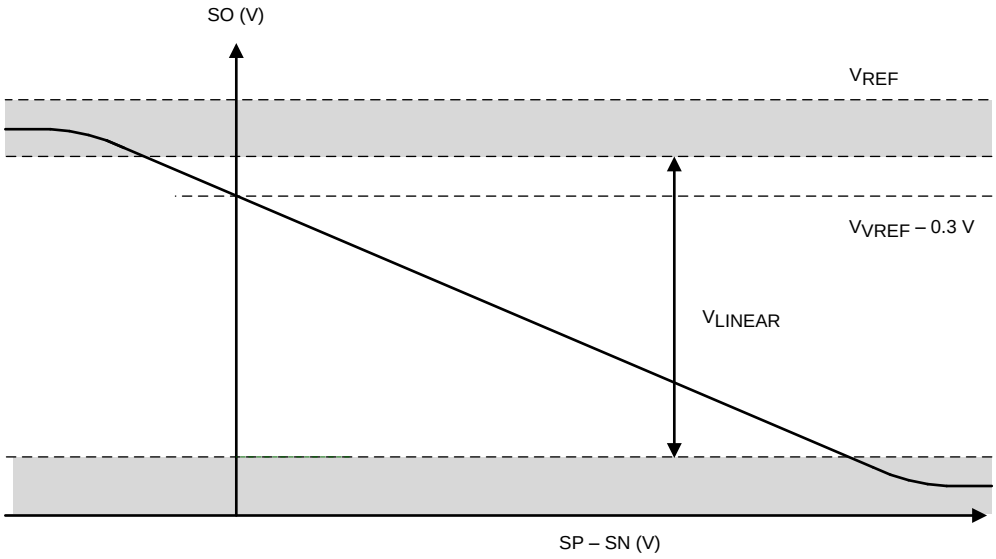


図 33. Unidirectional Current-Sense Output

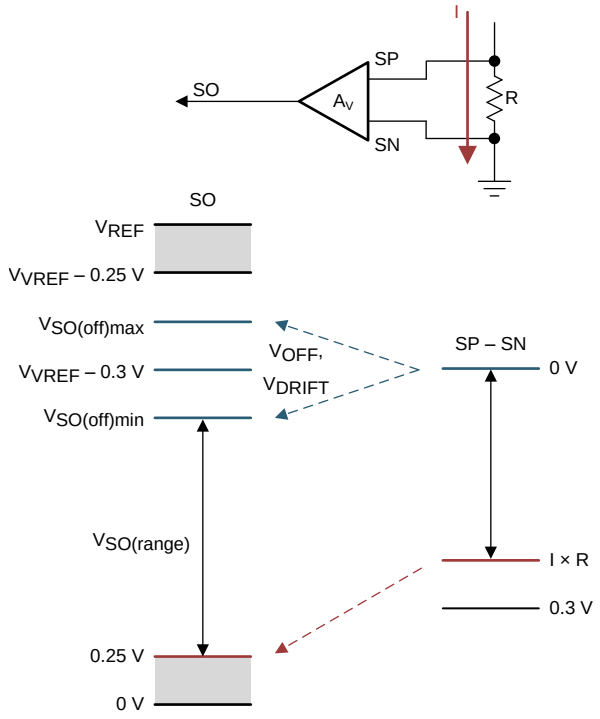


図 34. Unidirectional Current-Sense Regions

9.3.4.3 Amplifier Calibration Modes

To minimize DC offset and drift over temperature, a DC calibration mode is provided and enabled through the SPI register (CSA_CAL_X). This option is not available on the H/W interface device. When the calibration setting is enabled, the inputs to the amplifier are shorted and the shunt resistor is disconnected. DC calibration can be done at any time, even when the half-bridges are operating. For the best results, perform manual calibration during the switching OFF period to decrease the potential noise impact to the amplifier. 図 35 shows a diagram of the calibration mode. When a CSA_CAL_X bit is enabled, the corresponding amplifier goes to the calibration mode.

In both the SPI and H/W device options, the CAL pin can be used to perform DC calibration to all the three amplifiers at the same time. When the CAL pin is pulled high, the inputs of all the three amplifiers are shorted and the shunt resistors are disconnected which lets the host microcontroller perform manual calibration.

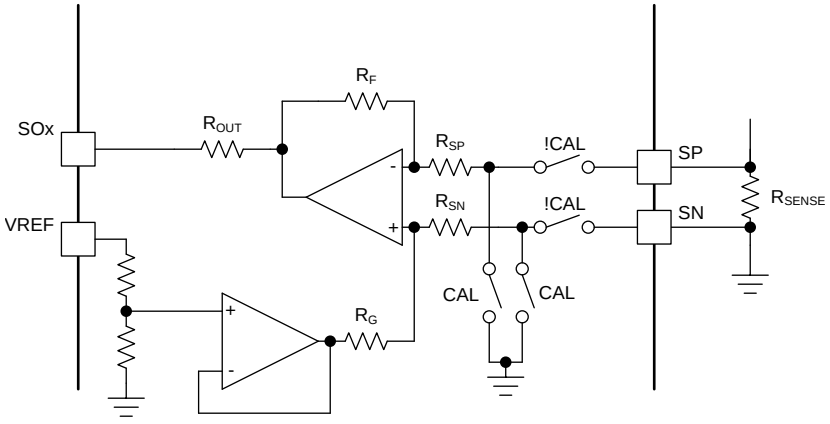


図 35. Amplifier Manual Calibration

In addition to the manual calibration, the DRV8343-Q1 device provides an auto calibration feature on both the SPI and H/W device versions to minimize the amplifier input offset after power up and during run time to account for temperature and device variation. Auto calibration is automatically performed on device power up for both the H/W and SPI device options. The power up auto calibration starts immediately after the VREF pin crosses the minimum operational VREF voltage. Wait 50 µs for the power up auto calibration routine to complete after the VREF pin voltage crosses the minimum VREF operational voltage. The auto calibration functions by performing a trim routine of the amplifier to minimize the amplifier input offset, after which the trim codes are stored in the device and the amplifiers are ready for normal operation. For the SPI device option, auto calibration can also be performed again during run time by enabling the CAL_MODE register setting.

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Auto calibration happens only in the bidirectional mode. If unidirectional mode is selected and auto calibration is commanded, the amplifier will switch to bidirectional mode to perform the auto calibration routine. After auto calibration routine is complete, the amplifier will revert to unidirectional mode.

For the SPI device option, auto calibration can also be performed again during run time by enabling the AUTO_CAL register setting. Auto calibration can then be commanded with the corresponding CSA_CAL_X register setting to rerun the auto calibration routine. During auto calibration all of the amplifiers will be configured for the maximum gain setting in order to improve the accuracy of the calibration routine.

For manual calibration, after writing a 1 to the CAL_CSA_X bits or taking the CAL pin high, the micro-controller needs to wait for 50 µs before performing manual calibration. This 50 µs wait time is for the auto calibration routine to complete. TI recommends that after the 50 µs expires, the micro-controller reads the outputs of the amplifiers to determine the offset and then perform the manual calibration routine.

表 8. CAL and CAL_CSA_X table

	SPI device option		H/W device option
	CAL_MODE = 0b	CAL_MODE = 1b	
CSA_CAL_X = 1b	Manual calibration	Auto calibration	N/A
CAL pin = High	Manual calibration	Auto calibration	Manual Calibration

9.3.4.4 MOSFET V_{DS} Sense Mode (SPI Only)

The current sense amplifiers on the DRV8343-Q1 SPI device can be configured to amplify the voltage across the external low-side MOSFET V_{DS}. This configuration lets the external controller measure the voltage drop across the MOSFET $R_{DS(on)}$ without the shunt resistor and then calculate the half-bridge current level. This setting is not available in the H/W device.

To enable this mode set the CSA_FET bit to 1. The positive input of the amplifier is then internally connected to the DLx pin with an internal clamp to prevent high voltage on the DLx pin from damaging the sense amplifier inputs. During this mode of operation, the SPx pins should stay disconnected. When the CSA_FET bit is set to 1, the negative reference for the low-side V_{DS} monitor is automatically set to the SNx pin, regardless of the state of the state of the LS_REF bit. This setting is implemented to prevent disabling of the low-side V_{DS} monitor.

If the system operates in MOSFET V_{DS} current sense mode, route the DLx and SNx pins with Kelvin connections across the drain and source of the external low-side MOSFETs.

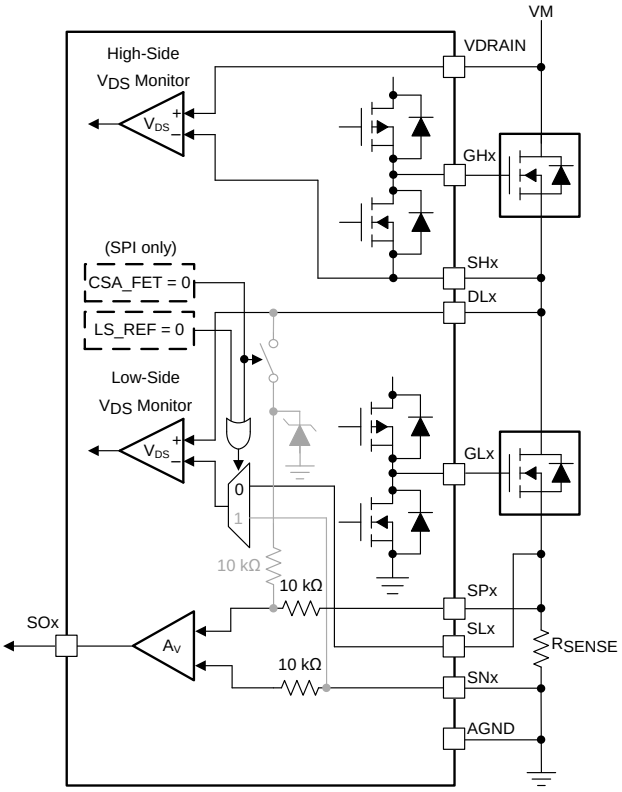

図 36. Resistor Sense Configuration

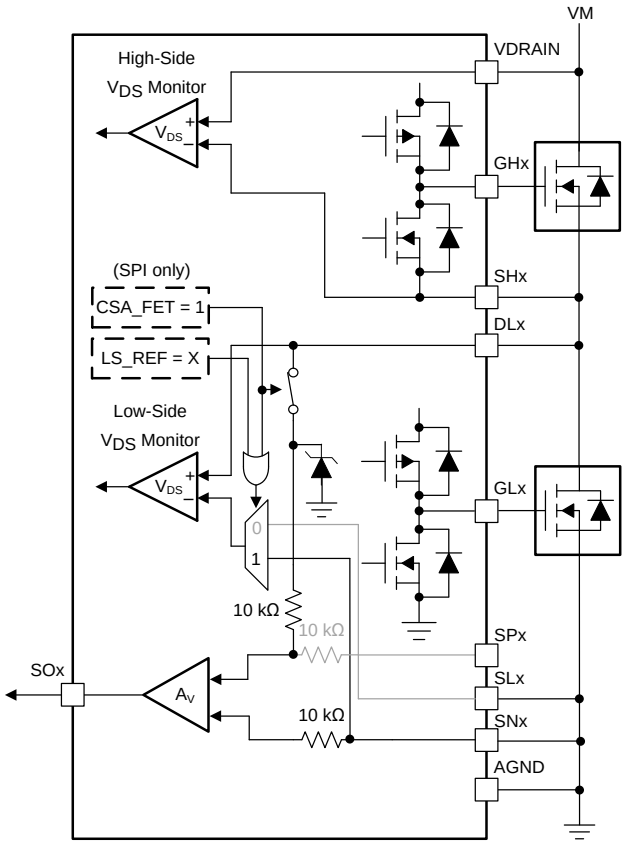

図 37. V_{DS} Current Sense Mode

When operating in MOSFET V_{DS} current sense mode, the amplifier is enabled at the end of the t_{DRIVE} time. At this time, the amplifier input is connected to the DLx pin, and the SOx output is valid. When the low-side MOSFET receives a signal to turn off, the amplifier inputs, SPx and SNx, are shorted together internally.

9.3.5 Gate Driver Protective Circuits

The DRV8343-Q1 device is protected against VM undervoltage, charge pump undervoltage, MOSFET VDS overcurrent, gate driver shorts, and overtemperature events. The DRV8343-Q1 device also provides a detection mechanism for open-load, offline short-to-supply, and offline short-to-ground conditions. When a fault occurs, the individual fault bit is set high along with the global FAULT bit in the FAULT status register for the SPI device. The FAULT bit is OR'ed with all the other individual status bits. In the H/W device, only the nFAULT pin is driven low during a fault condition. Some of the protection and detection features can be disabled through SPI in the SPI device, or the nDIAG pin in the H/W device

表 9. Fault Action and Response

FAULT	CONDITION	CONFIGURATION	REPORT	GATE DRIVER	LOGIC	RECOVERY
VM undervoltage (UVLO)	$V_{VM} < V_{UVLO}$	—	nFAULT	Hi-Z	Disabled	Automatic: $V_{VM} > V_{UVLO}$
Charge pump undervoltage (CPUV)	$V_{VCP} < V_{CPUV}$	DIS_CPUV = 0b	nFAULT	Hi-Z	Active	Automatic: $V_{VCP} > V_{CPUV}$
		DIS_CPUV = 1b	None	Active	Active	
V_{DS} overcurrent (VDS_OCP)	$V_{DS} > V_{VDS\_OCP}$	OCP_MODE = 00b	nFAULT	Hi-Z	Active	Latched: CLR_FLT, ENABLE Pulse
		OCP_MODE = 01b	nFAULT	Hi-Z	Active	Retry: t_{RETRY}
		OCP_MODE = 10b	nFAULT	Active	Active	Report only
		OCP_MODE = 11b	None	Active	Active	No action
V_{SENSE} overcurrent (SEN_OCP)	$V_{SP} > V_{SEN\_OCP}$	OCP_MODE = 00b	nFAULT	Hi-Z	Active	Latched: CLR_FLT, ENABLE Pulse
		OCP_MODE = 01b	nFAULT	Hi-Z	Active	Retry: t_{RETRY}
		OCP_MODE = 10b	nFAULT	Active	Active	Report only
		OCP_MODE = 11b	None	Active	Active	No action
Gate driver fault (GDF)	Gate voltage stuck > t_{DRIVE}	DIS_GDF = 0b	nFAULT	Hi-Z	Active	Latched: CLR_FLT, ENABLE Pulse
		DIS_GDF = 1b	None	Active	Active	No action
Thermal warning (OTW)	$T_J > T_{OTW}$	OTW_REP = 0b	None	Active	Active	No action
		OTW_REP = 1b	nFAULT	Active	Active	Automatic: $T_J < T_{OTW} - T_{HYS}$
Thermal shutdown (OTSD)	$T_J > T_{OTSD}$	OTSD_MODE = 0b	nFAULT	Hi-Z	Active	Latched: CLR_FLT, ENABLE Pulse
		OTSD_MODE = 1b	nFAULT	Hi-Z	Active	Automatic: $T_J < T_{OTSD} - T_{HYS}$
Open load passive (OLP)	No load detected	EN_OLP = 0b	None	Hi-Z	Active	No action
		EN_OLP = 1b	nFAULT	Hi-Z	Active	Report only
Open load active (OLA)	No load detected	EN_OLA_X = 0b	None	Active	Active	No action
		EN_OLA_X = 1b	nFAULT	Active	Active	Report only
Offline short-to-supply (SHT_BAT)	Phase node short-to-supply	EN_SHT_TST = 0b	None	Hi-Z	Active	No action
		EN_SHT_TST = 1b	nFAULT	Hi-Z	Active	Report only
Offline short-to-ground (SHT_GND)	Phase node short-to-ground	EN_SHT_TST = 0b	None	Hi-Z	Active	No action
		EN_SHT_TST = 1b	nFAULT	Hi-Z	Active	Report only
Device internal memory (1)data fault	Memory checksum fault detected	—	nFAULT	Active	Active	No action

(1) The DRV8343-Q1 has a OTP (one time program) memory which stores TI internal data used for analog functional blocks. The memory has a check-sum feature, and nFAULT is pulled low if a fault is detected at power up.

9.3.5.1 VM Supply Undervoltage Lockout (UVLO)

If at any time the input supply voltage on the VM pin falls lower than the V_{UVLO} threshold, all of the external MOSFETs are disabled, the charge pump is disabled, and the nFAULT pin is driven low. The FAULT and VM_UVLO bits are also latched high in the registers on SPI devices. Normal operation starts again (gate driver operation and the nFAULT pin is released) when the VM undervoltage condition clears. The VM_UVLO bit stays set until cleared through the CLR_FLT bit or an ENABLE pin reset pulse (t_{RST}).

9.3.5.2 VCP Charge Pump Undervoltage Lockout (CPUV)

If at any time the voltage on the VCP pin (charge pump) falls lower than the CPUV threshold voltage of the charge pump, all of the external MOSFETs are disabled and the nFAULT pin is driven low. The FAULT and CPUV bits are also latched high in the registers in the SPI device. Normal operation starts again (gate driver operation and the nFAULT pin is released) when the VCP undervoltage condition is removed. The FAULT and CPUV bits stay set until cleared through the CLR_FLT bit or an ENABLE pin reset pulse (t_{RST}). Setting the DIS_CPUV bit high on the SPI devices disables this protection feature. If the DIS_CPUV bit is set high and a charge pump undervoltage condition occurs, the device keeps operating but the CPUV fault bit is set high in the SPI register until cleared through the CLR_FLT bit or an ENABLE pin reset pulse (t_{RST}). CPUV protection cannot be disabled in the H/W device.

9.3.5.3 MOSFET V_{DS} Overcurrent Protection (VDS_OCP)

A MOSFET overcurrent event is sensed by monitoring the VDS voltage drop across the external MOSFET $R_{DS(on)}$. If the voltage across an enabled MOSFET exceeds the V_{VDS_OCP} threshold for longer than the t_{OCP_DEG} deglitch time, a VDS_OCP event is recognized and action is done according to the OCP_MODE. On hardware interface devices, the V_{VDS_OCP} threshold is set with the VDS pin, the t_{OCP_DEG} is fixed at 4 µs, and the OCP_MODE is configured for latched shutdown but can be disabled by tying the VDS pin to DVDD. In the SPI device, the V_{VDS_OCP} threshold is set through the VDS_LVL SPI register, the t_{OCP_DEG} is set through the OCP_DEG bits in the SPI register, and the OCP_MODE bit can operate in four different modes: V_{DS} latched shutdown, V_{DS} automatic retry, V_{DS} report only, and V_{DS} disabled.

9.3.5.3.1 V_{DS} Latched Shutdown (OCP_MODE = 00b)

After a VDS_OCP event in this mode, all external MOSFETs are disabled and the nFAULT pin is driven low. The FAULT, VDS_OCP, and corresponding MOSFET OCP bits are latched high in the SPI registers. Normal operation starts again (gate driver operation and the nFAULT pin is released) when the VDS_OCP condition clears and a clear faults command is issued either through the CLR_FLT bit or an ENABLE reset pulse (t_{RST}). This is the default mode in both the H/W and SPI device options.

9.3.5.3.2 V_{DS} Automatic Retry (OCP_MODE = 01b)

After a VDS_OCP event in this mode, all the external MOSFETs are disabled and the nFAULT pin is driven low. The FAULT, VDS_OCP, and corresponding MOSFET OCP bits are latched high in the SPI registers. Normal operation starts again automatically (gate driver operation and the nFAULT pin is released) after the t_{RETRY} time elapses. The FAULT, VDS_OCP, and MOSFET OCP bits stay latched until the t_{RETRY} period expires.

9.3.5.3.3 V_{DS} Report Only (OCP_MODE = 10b)

No protective action occurs after a VDS_OCP event in this mode. The overcurrent event is reported by driving the nFAULT pin low and latching the FAULT, VDS_OCP, and corresponding MOSFET OCP bits high in the SPI registers. The gate drivers continue to operate as usual. The external controller manages the overcurrent condition by acting appropriately. The reporting clears (nFAULT pin is released) when the VDS_OCP condition clears and a clear faults command is issued either through the CLR_FLT bit or an ENABLE reset pulse (t_{RST}).

9.3.5.3.4 V_{DS} Disabled (OCP_MODE = 11b)

No action occurs after a VDS_OCP event in this mode. The VDS overcurrent monitor is disabled for all three half-bridges at the same time and the DIS_VDS_x bits are locked. In the H/W device, VDS_OCP is disabled for all three half-bridges at the same time through the VDS pin.

9.3.5.4 V_{SENSE} Overcurrent Protection (SEN_OCP)

Half-bridge overcurrent is also monitored by sensing the voltage drop across the external current-sense resistor with the SP pin. If at any time, the voltage on the SP input of the current-sense amplifier exceeds the V_{SEN_OCP} threshold for longer than the t_{OCP_DEG} deglitch time, a SEN_OCP event is recognized and action is done according to the OCP_MODE. On hardware interface devices, the V_{SENSE} threshold is fixed at 1 V, t_{OCP_DEG} is fixed at 4 µs, and the OCP_MODE for V_{SENSE} is fixed for latched shutdown. In the SPI device, the V_{SENSE} threshold is set through the SEN_LVL SPI register, the t_{OCP_DEG} is set through the OCP_DEG SPI register, and the OCP_MODE bit can operate in four different modes: V_{SENSE} latched shutdown, V_{SENSE} automatic retry, V_{SENSE} report only, and V_{SENSE} disabled.

9.3.5.4.1 V_{SENSE} Latched Shutdown (OCP_MODE = 00b)

After a SEN_OCP event in this mode, all the external MOSFETs are disabled and the nFAULT pin is driven low. The FAULT and SEN_OCP bits are latched high in the SPI registers. Normal operation starts again (gate driver operation and the nFAULT pin is released) when the SEN_OCP condition clears and a clear faults command is issued either through the CLR_FLT bit or an ENABLE reset pulse (t_{RST}). This is the default mode in both the H/W and SPI device options.

9.3.5.4.2 V_{SENSE} Automatic Retry (OCP_MODE = 01b)

After a SEN_OCP event in this mode, all the external MOSFETs are disabled and the nFAULT pin is driven low. The FAULT, SEN_OCP, and corresponding sense OCP bits are latched high in the SPI registers. Normal operation starts again automatically (gate driver operation and the nFAULT pin is released) after the t_{RETRY} time elapses. The FAULT, SEN_OCP, and sense OCP bits stay latched until the t_{RETRY} period expires.

9.3.5.4.3 V_{SENSE} Report Only (OCP_MODE = 10b)

No protective action occurs after a SEN_OCP event in this mode. The overcurrent event is reported by driving the nFAULT pin low and latching the FAULT and SEN_OCP bits high in the SPI registers. The gate drivers continue to operate. The external controller manages the overcurrent condition by acting appropriately. The reporting clears (nFAULT released) when the SEN_OCP condition clears and a clear faults command is issued either through the CLR_FLT bit or an ENABLE reset pulse (t_{RST}).

9.3.5.4.4 V_{SENSE} Disabled (OCP_MODE = 11b)

No action occurs after a SEN_OCP event in this mode. The SEN_OCP overcurrent monitor is disabled for all three half-bridges at the same time and the DIS_SEN_x bits are locked. In the H/W device, SEN_OCP is disabled for all three half-bridges at the same time through the VDS pin.

9.3.5.5 Gate Driver Fault (GDF)

The GHx and GLx pins are monitored such that if the voltage on the external MOSFET gate does not increase or decrease after the t_{DRIVE} time, a gate driver fault is detected. This fault may be encountered if the GHx or GLx pins are shorted to the PGND, SHx, SLx, or VM pins. Additionally, a gate driver fault may be encountered if the selected IDRIVE setting is not sufficient to turn on the external MOSFET within the t_{DRIVE} period. After a gate drive fault is detected, all external MOSFETs are disabled and the nFAULT pin driven low. In addition, the FAULT, GDF, and corresponding VGS bits are latched high in the SPI registers. Normal operation starts again (gate driver operation and the nFAULT pin is released) when the gate driver fault condition is removed and a clear faults command is issued either through the CLR_FLT bit or an ENABLE reset pulse (t_{RST}). In the SPI device, setting the DIS_GDF bit high disables this protection feature. If DIS_GDF bit is set high and a gate drive fault occurs, the device keeps operating but the appropriate VGS fault bit is set high in the SPI register until cleared through the CLR_FLT bit or an ENABLE pin reset pulse (t_{RST}). GDF cannot be disabled in the H/W device option.

Gate driver faults can indicate that the selected IDRIVE or t_{DRIVE} settings are too low to slew the external MOSFET in the desired time. Increasing either the IDRIVE or t_{DRIVE} setting can resolve gate driver faults in these cases. Alternatively, if a gate-to-source short occurs on the external MOSFET, a gate driver fault is reported because of the MOSFET gate not turning on. The t_{DRIVE} time also refers to the GDF fault blanking time.

Fault handling is done as follows based on the MODE setting:

- In 6x, 3x, and 1x PWM modes a GDF fault in one of the external MOSFETs turns off all the MOSFETs.
- In independent half-bridge mode (MODE = 011b or MODE pin is Hi-Z) a GDF fault in one half-bridge only

disables both the MOSFETs in that half-bridge. The MOSFETs in the other half-bridges operate as commanded.

- In independent MOSFET mode (MODE = 111b or MODE pin tied to DVDD) a GDF fault in a MOSFET only disables that particular MOSFET. All the other MOSFETs operate as commanded. The same fault handling scheme applies for MODE = 100b, 101b, and 110b.
- A GDF fault in phases set as Independent half-bridge disables both MOSFETs in that particular phase.
- A GDF fault in phases set as Independent FET mode disables the MOSFET where the fault occurred.

9.3.5.6 Thermal Warning (OTW)

If the die temperature exceeds the trip point of the thermal warning (T_{OTW}), the OTW bit is set in the registers of SPI devices. The device performs no additional action and continues to function. When the die temperature falls lower than the hysteresis point of the thermal warning, the OTW bit clears automatically. The OTW bit can also be configured to report on the nFAULT pin by setting the OTW_REP bit to 1 through the SPI registers. OTW is not available in the H/W device.

9.3.5.7 Thermal Shutdown (OTSD)

If the die temperature exceeds the trip point of the thermal shutdown limit (T_{OTSD}), all the external MOSFETs are disabled, the charge pump is shut down, and the nFAULT pin is driven low. In addition, the FAULT and OTSD bits are latched high. This protection feature cannot be disabled. The overtemperature protection can operate in two different modes.

9.3.5.7.1 Latched Shutdown (OTSD_MODE = 0b)

In latched shutdown mode, after a OTSD event, normal operation starts again (motor driver operation and the nFAULT line released) when the OTSD condition is removed and a clear faults command has been issued either through the CLR_FLT bit or an nSLEEP reset pulse. This is the default mode for a OTSD event in the SPI device.

When the DRV8343-Q1 device hits thermal shutdown, the OTSD and FAULT bits are latched in the SPI register. Clearing the fault through the CLR_FLT bit or an nSLEEP reset pulse will clear the OSTD and FAULT bits. When the DRV8343-Q1 device hits thermal shutdown, the device will disable the charge pump without triggering CPUV. The charge pump will be enabled again when the OTSD and FAULT bits are cleared through the CLR_FLT bit or an nSleep reset Pulse.

9.3.5.7.2 Automatic Recovery (OTSD_MODE = 1b)

In automatic recovery mode, after a OTSD event, normal operation starts again (motor driver operation and the nFAULT line released) when the junction temperature falls to less than the overtemperature threshold limit minus the hysteresis ($T_{OTSD} – T_{HYS}$). The OTSD bit stays latched high indicating that a thermal event occurred until a clear faults command is issued either through the CLR_FLT bit or an nSLEEP reset pulse. This is the default mode for a OTSD event in the H/W device.

9.3.5.8 Open Load Detection (OLD)

If the load is disconnected from the device, an open load is detected and the nFAULT pin is latched low. In the DRV8343-Q1 device, The FAULT, OL_SHT, and the corresponding open load (OL_PH_x) bits in the SPI register are latched high. When the open-load condition is removed, and the MCU clears the fault through either the CLR_FLT bit or an ENABLE-pin reset pulse (t_{RST}), the device is ready to drive the motor based on the input commands.

9.3.5.8.1 Open Load Detection in Passive Mode (OLP)

In open load detection in passive mode, open load diagnosis is performed without the motor in motion. If the motor is disconnected from the device an open load is detected and the nFAULT pin will latch low until a clear faults command is issued by the MCU either through the CLR_FLT bit or an ENABLE reset pulse. The fault also clears when the device is power cycled or comes out of sleep mode. OLP is designed for applications having capacitance less than the values listed in 表 10 between motor phase pins to ground.

表 10. Open Load Passive Diagnostic Run-Time

Capacitance (nF)	OLP_SHTS_DLY (ms)
5	0.25
26	1.25
110	5
270	11.5

When the open load test is running, all external MOSFETs are disabled. For the H/W device option, at power-up or after going from sleep mode, the offline short-to-supply (SHT_BAT) and short-to-ground (SHT_GND) diagnostics run first followed by the OLP diagnostic if the nDIAG pin is left as no connect or tied to GND. If the nDIAG pin is tied to DVDD (or an external 3.3 V) the open load test is not performed. If a short condition is detected, the OLP diagnostic is not run (see Offline Shorts Diagnostics). If a short condition and open load occurs on a given phase at device power-up, for example, only the short condition is reported on the nFAULT pin and through the SPI fault register. In the SPI device option the OLP test is performed when commanded through SPI. If both short and OLP diagnostics are enabled simultaneously and a short condition is detection, only the short condition is reported on the nFAULT pin and through the SPI fault register.

The sequence to perform open load diagnostics in passive mode is as follows:

1. Device powered up (ENABLE = 1).
2. Mode is selected by SPI.
3. Hi-Z all three half-bridges by turning-off all the external MOSFETs.
4. Write a 1 to the EN_OLP bit in the SPI register and OLP is performed.
   - If an open load is detected, the nFAULT pin is driven low, and the FAULT bit, the OLD bit, and the respective OL_PH_x bit are latched high. When the open load condition is removed, a clear faults command must be issued by the MCU either through the CLR_FLT bit or an ENABLE reset pulse which resets the OL_PH_x register bit and causes the nFAULT pin to go high.
   - If open load is not detected, the EN_OLP bits return to default setting (0b) after t_{OL} expires.

The EN_OLP register keeps the written command until the diagnostic is complete. The half bridges must stay in Hi-Z state for the entire duration of the test. While open load diagnostic is running, if an input change occurs or the EN_OLP bit is set low, the open load test is aborted to start normal operation again, and no fault is reported. OLP should not be performed if the motor is energized.

The open load detection checks for a high impedance connection on the motor phase pins (SHx or DLx). The diagnostic has two major steps as listed in the *OLP Steps* section. The sequencing of the pullup and pulldown current varies depending on the load connections. 図 38 a simplified H-bridge configuration as an example for open load detection.

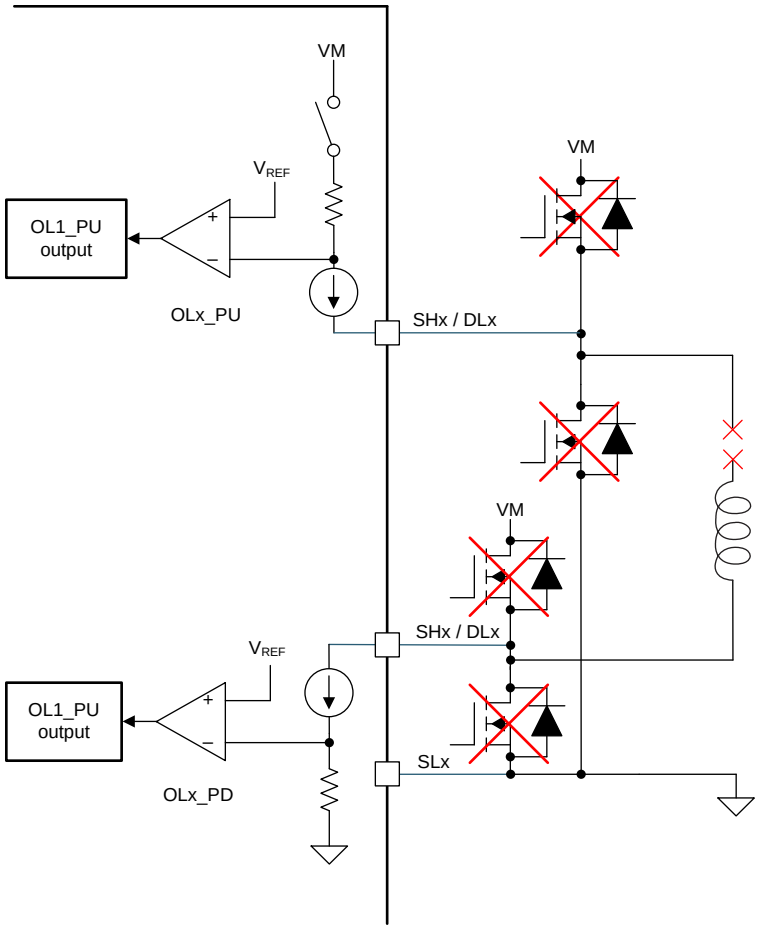

図 38. Circuit for Open Load Detection in Passive Mode

9.3.5.8.1.1 OLP Steps

The OLP algorithm list is as follows:

- The pullup current source is enabled. If a load is connected, current passes through the pullup resistor and the OLx_PU comparator output stays low. If an open load condition occurs, the current through the pullup resistor goes 0 and the OLx_PU comparator trips high.
- The pulldown current source is enabled. In the same way, the OLx_PD comparator output either stays low to indicate load-connected, or trips high to indicate an open load condition.
- If both the OLx_PU and OLx_PD comparators report an open load, the OL_PH_x bit in the SPI register latches high, and the nFAULT line goes low, to indicate an OL fault.

When the OL condition is removed, a clear faults command must be issued by the micro-controller either through the CLR_FLT bit or an ENABLE reset pulse which resets open load register bits. The charge pump stays active during this fault condition. The load connections shown in 図 39 are not supported OLP.

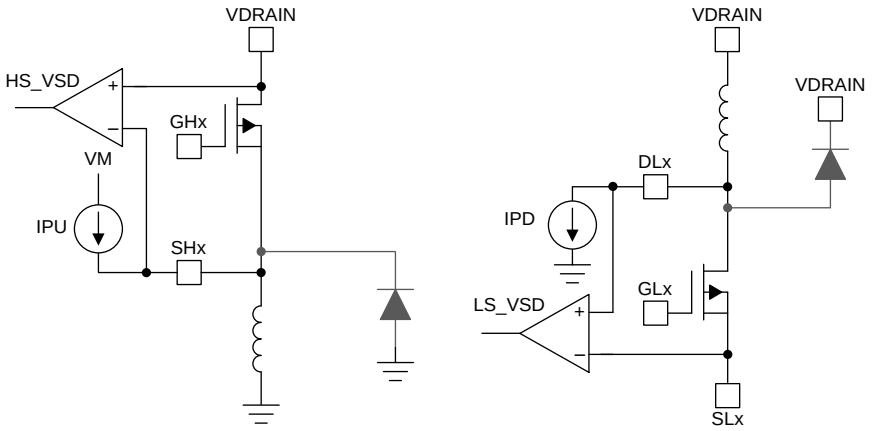

図 39. Load Configurations Not Supported

9.3.5.8.2 Open Load Detection in Active Mode (OLA)

An open load in active mode is disabled by default in the SPI device and can be enabled independently per half-bridge by writing a 1 to the EN_OLA_x bit. In the H/W device, OLA runs if the nDIAG pin is left as unconnected or tied to GND. OLA is detected when the motor gets disconnected from the driver when it is commutating. 図 40 shows a simplified H-bridge configuration for OLA implementation during high-side current recirculation. When the voltage drop across the body diode of the MOSFET does not exhibit overshoot greater than the VOLA over VM between the time the low-side FET is switched off and the high side FET is switched on during an output PWM cycle. An open load is not detected if the energy stored in the inductor is high enough to cause an overshoot greater than the V_{OLA} over VM caused by the fly-back current flowing through the body diode of the high-side FET.

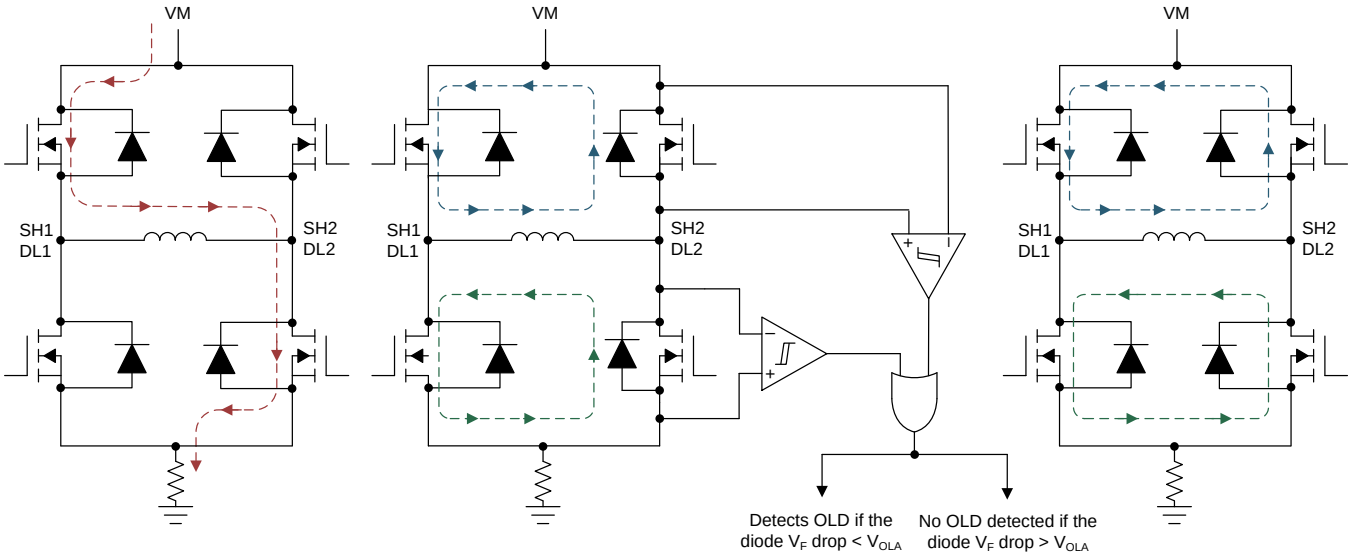

図 40. Circuit for Open Load Detection in Active Mode

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Depending on the operating conditions and on external circuitry, such as the output capacitors, an open load could be reported even though the load is present. This case might occur during a direction change or for small load currents respectively small PWM duty cycles. Therefore, TI recommends evaluating the open load diagnosis only in known suitable operating conditions and to ignore it otherwise.

The device has a failure counter to avoid inadvertent triggering of the open load active diagnosis. Three consecutive occurrences of the internal open load signal must occur, essentially three consecutive PWM pulses without freewheeling detected, before an open load is reported through the nFAULT pin and in the respective SPI register.

In the SPI device, depending on the load configuration and the PWM sequence, OLA on one phase can latch all three OL_PH_x bits high. In that case, the OLP diagnostic can be initiated to determine which phase has the open load condition. The load connections shown in 図 39 are not supported by OLA.

For OLA to function correctly, place capacitors between the motor phase node and GND. This capacitor is required for BLDC, bi-directional BDC and unidirectional BDC motors at the phase node. If a solenoid load is connected, as shown in 図 15, the capacitor is not required. Size the capacitors according 式 5. Make sure that the capacitor (C_{phase}) is placed on the PCB.

$$C_{phase} \geq \frac{V_{TH} \times C_{rss}}{V_{OLA(min)}} - C_{oss} \quad (5)$$

where

- V_{TH} is the threshold voltage of the MOSFET.
- $V_{OLA(min)}$ is 150 mV.

The values of C_{rss} and C_{oss} of the MOSFETs should be used for 0-V V_{DS}. Derating of C_{phase} must be considered when selecting the capacitance.

9.3.5.9 Offline Shorts Diagnostics

The device detects short-to-battery and short-to-ground conditions when the motor is not commutating. These offline diagnostics can be activated in the SPI device by setting the EN_SHT_TST bit high. Both the short-to-battery and short-to-ground diagnostics run when the EN_SHT_TST bit is set high. In the H/W device, these diagnostics run at power-up or when going from the sleep mode if the nDIAG pin is left unconnected or tied to GND. To disable the diagnostics in the H/W device, connect the nDIAG pin to the DVDD supply (or an external 3.3 V or 5 V rail). The short-to-supply diagnostic runs first (see Offline Short-to-Supply Diagnostic (SHT_BAT)) followed by the short-to-ground diagnostic (see Offline Short-to-Ground Diagnostic (SHT_GND)). In the SPI device, the duration for this diagnostics is selected through the OLP_SHTS_DLY register. In the H/W device, the duration is fixed to 2 ms.

9.3.5.9.1 Offline Short-to-Supply Diagnostic (SHT_BAT)

When the EN_SHT_TST bit is set high, all the pulldown current sources on the DLx pins are enabled. The voltage across each pulldown source is individually measured and compared to an internal threshold (V_{TH}). If the voltage across any of the current sources exceeds V_{TH}, the DRV8343-Q1 device flags that as a fault condition. The nFAULT pin is driven low, and in the SPI device the FAULT, OL_SHT, and the corresponding SHT_BAT_x bit is set. 図 41 shows the internal circuit for the short to battery detection.

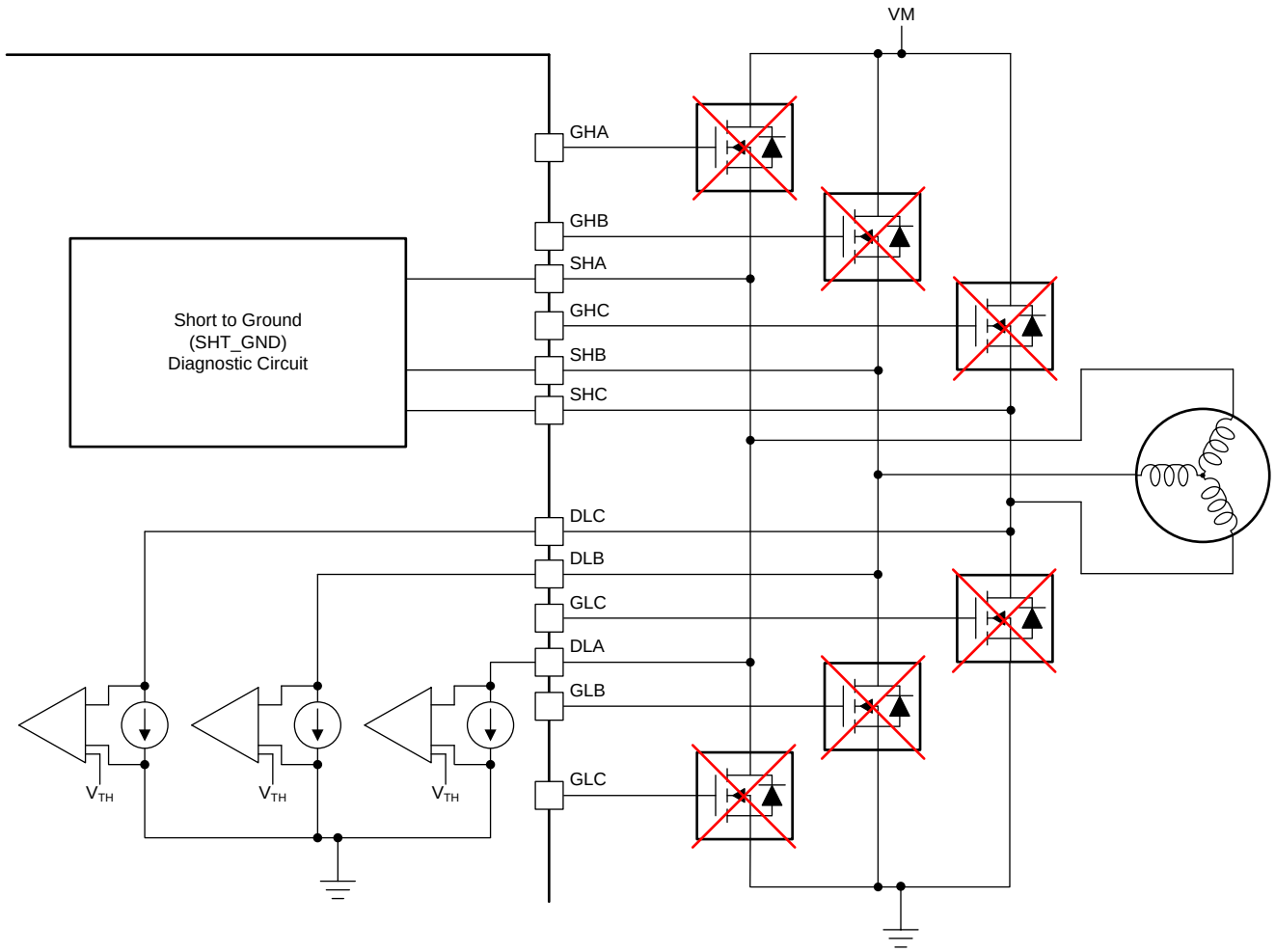

図 41. Offline Short-to-Supply Detection Circuit

In the SPI device, depending on the load configuration, SHT_BAT on one phase can latch all three SHT_BAT_x bits high. To determine which phase has a short-to-supply fault condition, the external MOSFETs can be enabled and the appropriate VDS_Lx fault bit is latched indicating the faulty phase node. SHT_BAT is not supported for load configurations shown in 図 39.

9.3.5.9.2 Offline Short-to-Ground Diagnostic (SHT_GND)

When the EN_SHT_TST bit is set high, all the pullup current sources on the SHx pins are enabled. The voltage across each pullup source is individually measured and compared to an internal threshold (V_{TH}). If the voltage across any of the current sources exceeds V_{TH}, the DRV8343-Q1 device flags that as a fault condition. The nFAULT pin is driven low, and in the SPI device the FAULT, OL_SHT, and the corresponding SHT_GND_x bit is set. 図 42 shows the internal circuit for the short-to-ground detection.

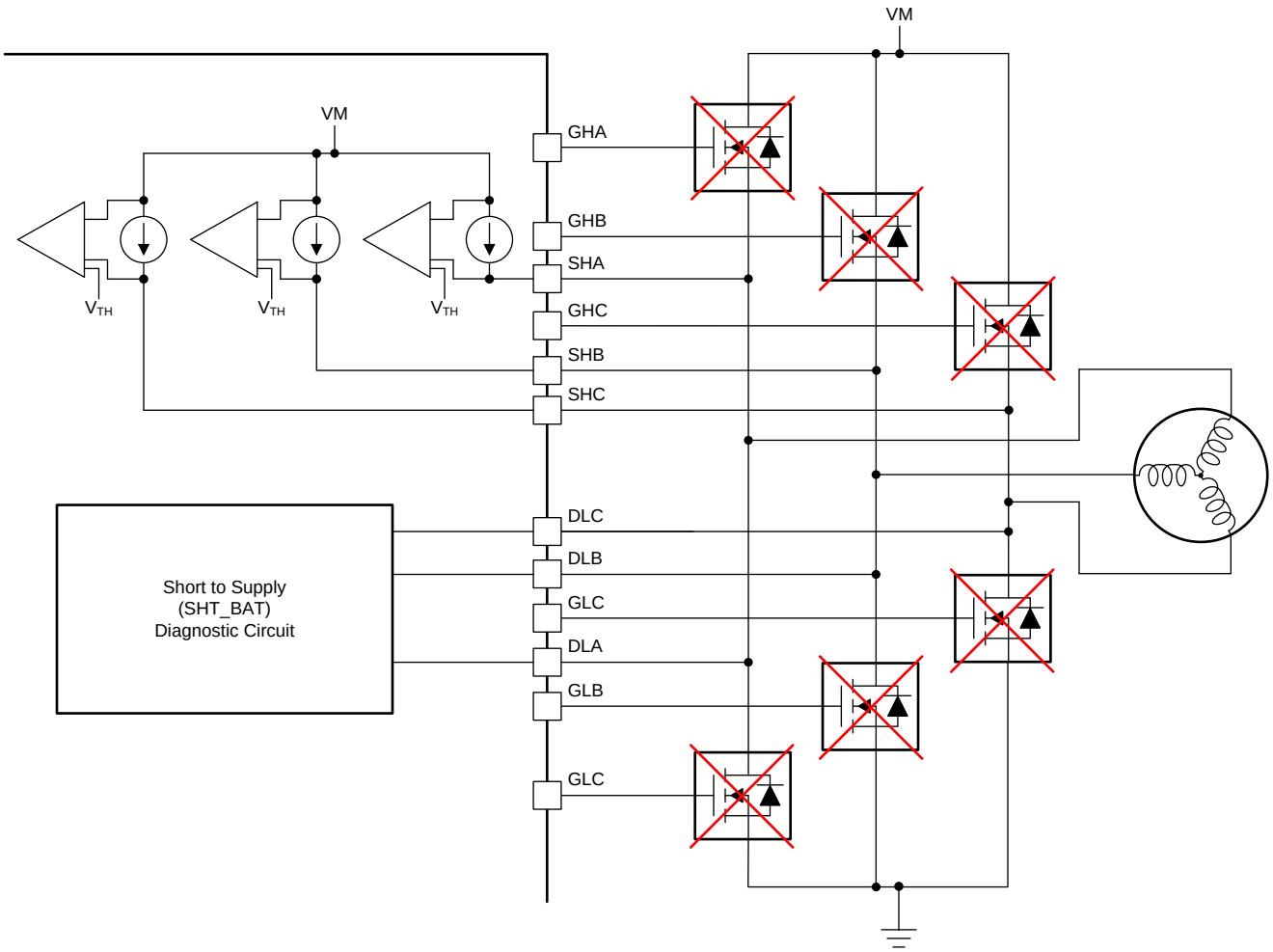

図 42. Offline Short-to-Ground Detection Circuit

In the SPI device, depending on the load configuration, SHT_GND on one phase can latch all three SHT_GND_x bits high. To determine which phase has a short-to-ground fault condition, the external MOSFETs can be enabled and the appropriate VDS_Hx fault bit is latched indicating the faulty phase node. SHT_GND is not supported for load configurations shown in 図 39.

9.3.5.10 Reverse Supply Protection

The circuit in 図 43 can be implemented to help protect the system from reverse supply conditions. This circuit requires the following additional components:

- N-channel MOSFET
- NPN BJT
- Diode
- 10-kΩ and 43-kΩ resistors

The VCP voltage with respect to VM supplies the gate-source voltage of N-channel MOSFET, and the voltage V_{VCP} depends on VM voltage. The characteristics of N-Channel MOSFET (e.g. gate threshold voltage) and the VM voltage range of the system need to be reviewed by the system integrator.

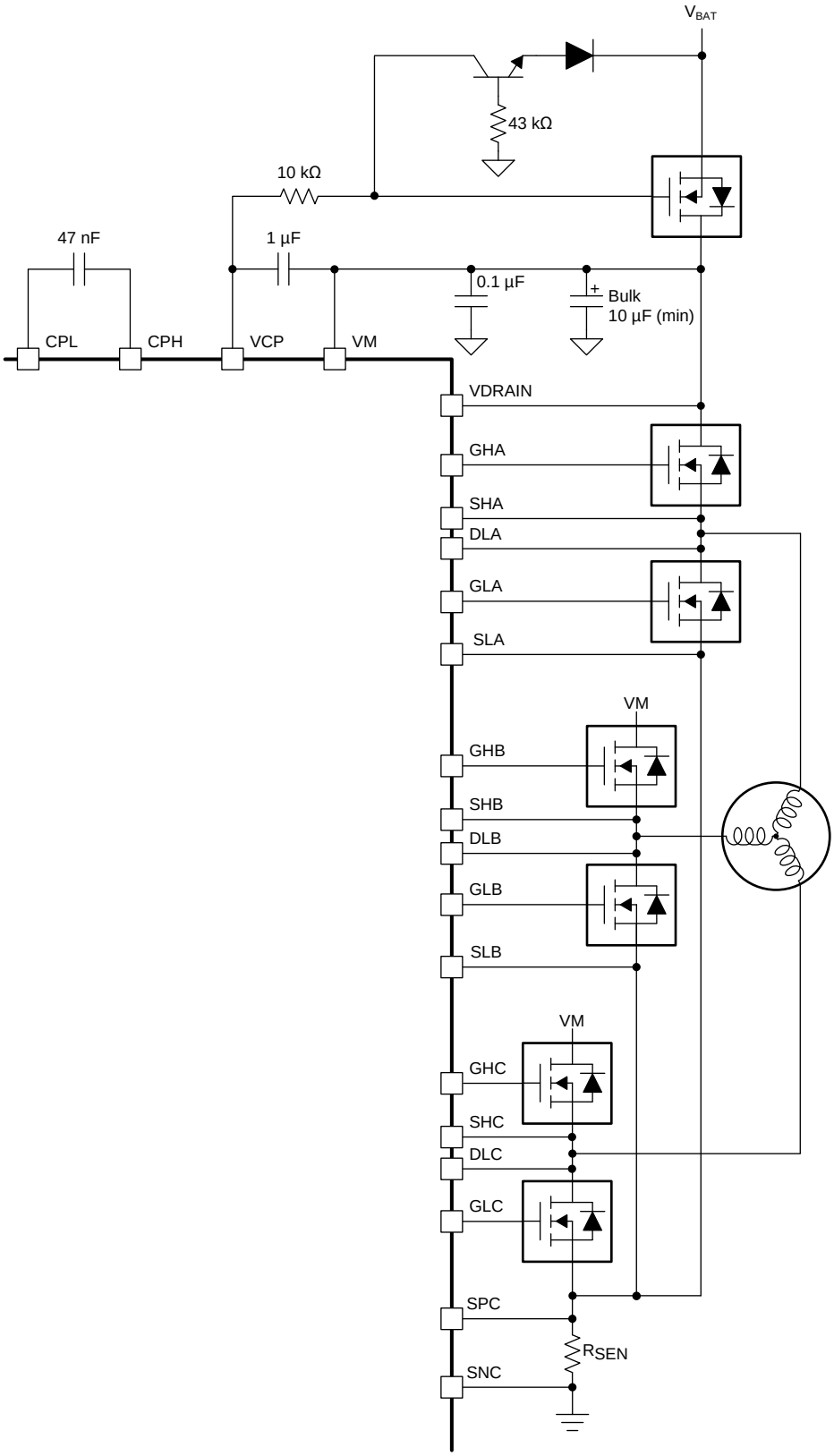

図 43. Reverse Supply Protection

9.4 Device Functional Modes

9.4.1 Gate Driver Functional Modes

9.4.1.1 Sleep Mode

The ENABLE pin manages the state of the DRV8343-Q1 device. When the ENABLE pin is low, the device goes to a low-power sleep mode. In sleep mode, all gate drivers are disabled, all external MOSFETs are disabled, the charge pump is disabled, the DVDD regulator is disabled, and the SPI bus is disabled. The t_{SLEEP} time must elapse after a falling edge on the ENABLE pin before the device goes to sleep mode. The device comes out of sleep mode automatically if the ENABLE pin is pulled high. The t_{WAKE} time must elapse before the device is ready for inputs.

In sleep mode and when $V_{VM} < V_{UVLO}$, all external MOSFETs are disabled. The high-side gate pins, GHx, are pulled to the SHx pin by an internal resistor and the low-side gate pins, GLx, are pulled to the PGND pin by an internal resistor.

9.4.1.2 Operating Mode

When the ENABLE pin is high and the V_{VM} voltage is greater than the V_{UVLO} voltage, the device goes to operating mode. The t_{WAKE} time must elapse before the device is ready for inputs. In this mode the charge pump, low-side gate regulator, DVDD regulator, and SPI bus are active.

9.4.1.3 Fault Reset (CLR_FLT or ENABLE Reset Pulse)

In the case of device latched faults, the DRV8343-Q1 device goes to a partial shutdown state to help protect the external power MOSFETs and system.

When the fault condition clears, the device can go to the operating state again by either setting the CLR_FLT SPI bit on SPI devices or issuing a result pulse to the ENABLE pin on either interface variant. The ENABLE reset pulse (t_{RST}) consists of a high-to-low-to-high transition on the ENABLE pin. The low period of the sequence should fall with the t_{RST} time window or else the device will start the complete shutdown sequence. The reset pulse has no effect on any of the regulators, device settings, or other functional blocks

9.5 Programming

This section applies only to the DRV8343-Q1 SPI devices.

9.5.1 SPI Communication

9.5.1.1 SPI

On DRV8343-Q1 SPI devices, an SPI bus is used to set device configurations, operating parameters, and read out diagnostic information. The SPI operates in slave mode and connects to a master controller. The SPI input data (SDI) word consists of a 16-bit word, with an 8-bit command and 8 bits of data. The SPI output data (SDO) word consists of 8-bit register data. The first 8 bits are don't care bits.

A valid frame must meet the following conditions:

- The SCLK pin should be low when the nSCS pin transitions from high to low and from low to high.
- The nSCS pin should be pulled high for at least 400 ns between words.
- When the nSCS pin is pulled high, any signals at the SCLK and SDI pins are ignored and the SDO pin is placed in the Hi-Z state.
- Data is captured on the falling edge of the SCLK pin and data is propagated on the rising edge of the SCLK pin.
- The most significant bit (MSB) is shifted in and out first.
- A full 16 SCLK cycles must occur for transaction to be valid.
- If the data word sent to the SDI pin is less than or more than 16 bits, a frame error occurs and the data word is ignored.
- For a write command, the existing data in the register being written to is shifted out on the SDO pin following the 8-bit command data.

9.5.1.1.1 SPI Format

The SDI input data word is 16 bits long and consists of the following format:

- 1 read or write bit, W (bit B15)
- 7 address bits, A (bits B14 through B8)
- 8 data bits, D (bits B7 through B0)

The SDO output data word is 16 bits long and the first 5 bits are don't care bits. The data word is the content of the register being accessed.

For a write command (W0 = 0), the response word on the SDO pin is the data currently in the register being written to.

For a read command (W0 = 1), the response word is the data currently in the register being read.

表 11. SDI Input Data Word Format

R/W	ADDRESS							DATA							
B15	B14	B13	B12	B11	B10	B9	B8	B7	B6	B5	B4	B3	B2	B1	B0
W0	0	0	A4	A3	A2	A1	A0	D7	D6	D5	D4	D3	D2	D1	D0

表 12. SDO Output Data Word Format

R/W	DON'T CARE							DATA							
B15	B14	B13	B12	B11	B10	B9	B8	B7	B6	B5	B4	B3	B2	B1	B0
W0	X	X	X	X	X	X	X	D7	D6	D5	D4	D3	D2	D1	D0

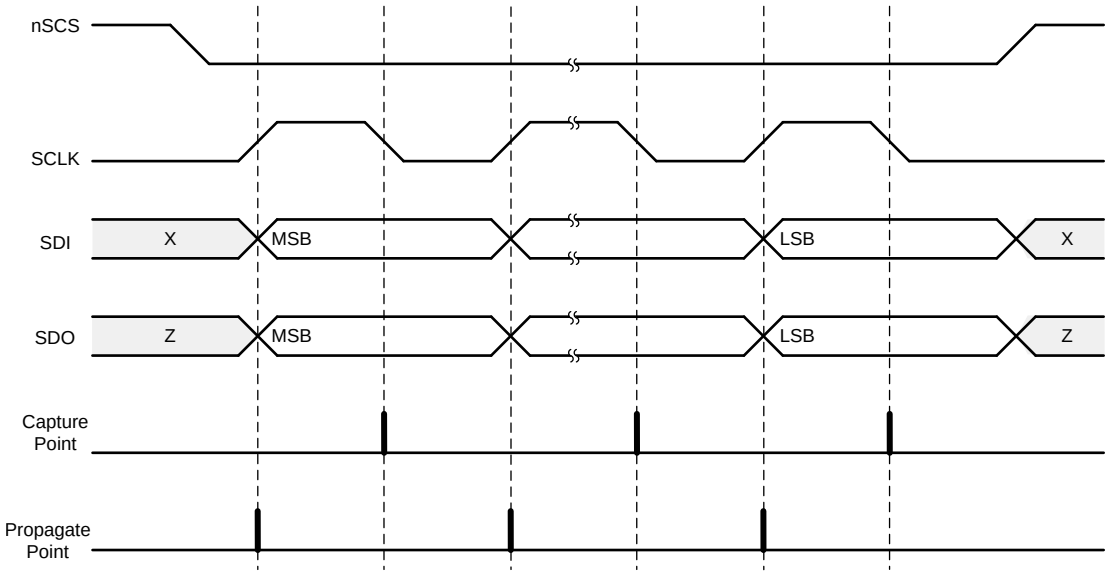

図 44. SPI Slave Timing Diagram

9.6 Register Maps

This section applies only to the DRV8343-Q1 SPI devices.

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Do not modify reserved registers or addresses not listed in the register map (表 13). Writing to these registers may have unintended effects. For all reserved bits, the default value is 0. To help prevent erroneous SPI writes from the master controller, set the LOCK bits to lock the SPI registers.

表 13. DRV8343-Q1 Register Map

Register Name	7	6	5	4	3	2	1	0	Access Type	Address
FAULT Status	FAULT	GDF	CPUV	UVLO	OCP	OTW	OTSD	OL_SHT	R	0x00
DIAG Status A	SA_OC	SHT_GND_A	SHT_BAT_A	OL_PH_A	VGS_LA	VGS_HA	VDS_LA	VDS_HA	R	0x01
DIAG Status B	SB_OC	SHT_GND_B	SHT_BAT_B	OL_PH_B	VGS_LB	VGS_HB	VDS_LB	VDS_HB	R	0x02
DIAG Status C	SC_OC	SHT_GND_C	SHT_BAT_C	OL_PH_C	VGS_LC	VGS_HC	VDS_LC	VDS_HC	R	0x03
IC1 Control	CLR_FLT	PWM_MODE			1PWM_COM	1PWM_DIR	1PWM_BRAKE		RW	0x04
IC2 Control	OTSD_MODE	OLP_SHTS_DLY		EN_SHT_TST	EN_OLP	EN_OLA_C	EN_OLA_B	EN_OLA_A	RW	0x05
IC3 Control	IDRIVEP_LA				IDRIVEP_HA				RW	0x06
IC4 Control	IDRIVEP_LB				IDRIVEP_HB				RW	0x07
IC5 Control	IDRIVEP_LC				IDRIVEP_HC				RW	0x08
IC6 Control	VDS_LVL_LA				VDS_LVL_HA				RW	0x09
IC7 Control	VDS_LVL_LB				VDS_LVL_HB				RW	0x0A
IC8 Control	VDS_LVL_LC				VDS_LVL_HC				RW	0x0B
IC9 Control	COAST	TRETRY		DEAD_TIME		TDRIVE_MAX	TDRIVE		RW	0x0C
IC10 Control	LOCK			DIS_CPUV	DIS_GDF	OCP_DEG			RW	0x0D
IC11 Control	RSVD	OTW_REP	CBC	DIS_VDS_C	DIS_VDS_B	DIS_VDS_A	OCP_MODE		RW	0x0E
IC12 Control	LS_REF	CSA_FET	CSA_GAIN_C		CSA_GAIN_B		CSA_GAIN_A		RW	0x0F
IC13 Control	CAL_MODE	VREF_DIV	SEN_LVL_C		SEV_LVL_B		SEN_LVL_A		RW	0x10
IC14 Control	RSVD		DIS_SEN_C	DIS_SEN_B	DIS_SEN_A	CSA_CAL_C	CSA_CAL_B	CSA_CAL_A	RW	0x11

Complex bit access types are encoded to fit into small table cells. 表 14 shows the codes that are used for access types in this section.

表 14. Status Registers Access Type Codes

Access Type	Code	Description
Read Type		
R	R	Read
Reset or Default Value		
-n		Value after reset or the default value

9.6.1 Status Registers

表 15 lists the memory-mapped registers for the status registers. All register offset addresses not listed in 表 15 should be considered as reserved locations and the register contents should not be modified.

The status registers are used to reporting warning and fault conditions. Status registers are read-only registers.

表 15. Status Registers Summary Table

Address	Register Name	Section
0x00	FAULT Status	Go
0x01	DIAG Status A	Go
0x02	DIAG Status B	Go
0x03	DIAG Status C	Go

9.6.1.1 FAULT Status Register (Address = 0x00) [reset = 0x00]

FAULT Status is shown in 図 45 and described in 表 16.

図 45. FAULT Status Register

7	6	5	4	3	2	1	0
FAULT	GDF	CPUV	UVLO	OCP	OTW	OTSD	OL_SHT
R-0b	R-0b	R-0b	R-0b	R-0b	R-0b	R-0b	R-0b

表 16. FAULT Status Register Field Descriptions

Bit	Field	Type	Default	Description
7	FAULT	R	0b	Logic OR of FAULT status registers
6	GDF	R	0b	Indicates gate drive fault condition
5	CPUV	R	0b	Indicates charge pump undervoltage fault condition
4	UVLO	R	0b	Indicates undervoltage lockout fault condition
3	OCP	R	0b	Indicated overcurrent fault condition either by VDS or SEN_OCP
2	OTW	R	0b	Indicates overtemperature warning
1	OTSD	R	0b	Indicates overtemperature shutdown
0	OL_SHT	R	0b	Indicates open load detection, or offline short-to-supply or GND detection

9.6.1.2 DIAG Status A Register (Address = 0x01) [reset = 0x00]

DIAG Status A is shown in 図 46 and described in 表 17.

図 46. DIAG Status A Register

7	6	5	4	3	2	1	0
SA_OC	SHT_GND_A	SHT_BAT_A	OL_PH_A	VGS_LA	VGS_HA	VDS_LA	VDS_HA
R-0b	R-0b	R-0b	R-0b	R-0b	R-0b	R-0b	R-0b

表 17. DIAG Status A Register Field Descriptions

Bit	Field	Type	Default	Description
7	SA_OC	R	0b	Indicates overcurrent on Phase A sense amplifier
6	SHT_GND_A	R	0b	Indicates offline short-to-ground fault in Phase A
5	SHT_BAT_A	R	0b	Indicates offline short to battery fault in Phase A
4	OL_PH_A	R	0b	Indicates open load fault in Phase A
3	VGS_LA	R	0b	Indicates gate drive fault on the A low-side MOSFET
2	VGS_HA	R	0b	Indicates gate drive fault on the A high-side MOSFET
1	VDS_LA	R	0b	Indicates VDS overcurrent fault on the A low-side MOSFET
0	VDS_HA	R	0b	Indicates VDS overcurrent fault on the A high-side MOSFET

9.6.1.3 DIAG Status B Register (Address = 0x02) [reset = 0x00]

DIAG Status B is shown in 図 47 and described in 表 18.

図 47. DIAG Status B Register

7	6	5	4	3	2	1	0
SB_OC	SHT_GND_B	SHT_BAT_B	OL_PH_B	VGS_LB	VGS_HB	VDS_LB	VDS_HB
R-0b	R-0b	R-0b	R-0b	R-0b	R-0b	R-0b	R-0b

表 18. DIAG Status B Register Field Descriptions

Bit	Field	Type	Default	Description
7	SB_OC	R	0b	Indicates overcurrent on Phase B sense amplifier
6	SHT_GND_B	R	0b	Indicates offline short-to-ground fault in Phase B
5	SHT_BAT_B	R	0b	Indicates offline short to battery fault in Phase B
4	OL_PH_B	R	0b	Indicates open load fault in Phase B
3	VGS_LB	R	0b	Indicates gate drive fault on the B low-side MOSFET
2	VGS_HB	R	0b	Indicates gate drive fault on the B high-side MOSFET
1	VDS_LB	R	0b	Indicates VDS overcurrent fault on the B low-side MOSFET
0	VDS_HB	R	0b	Indicates VDS overcurrent fault on the B high-side MOSFET

9.6.1.4 DIAG Status C Register (address = 0x03) [reset = 0x00]

DIAG Status C iss shown in 図 48 and described in 表 19.

図 48. DIAG Status C Register

7	6	5	4	3	2	1	0
SC_OC	SHT_GND_C	SHT_BAT_C	OL_PH_C	VGS_LC	VGS_HC	VDS_LC	VDS_HC
R-0b	R-0b	R-0b	R-0b	R-0b	R-0b	R-0b	R-0b

表 19. DIAG Status C Register Field Descriptions

Bit	Field	Type	Default	Description
7	SC_OC	R	0b	Indicates overcurrent on Phase C sense amplifier
6	SHT_GND_C	R	0b	Indicates offline short-to-ground fault in Phase C
5	SHT_BAT_C	R	0b	Indicates offline short to battery fault in Phase C
4	OL_PH_C	R	0b	Indicates open load fault in Phase C
3	VGS_LC	R	0b	Indicates gate drive fault on the C low-side MOSFET
2	VGS_HC	R	0b	Indicates gate drive fault on the C high-side MOSFET
1	VDS_LC	R	0b	Indicates VDS overcurrent fault on the C low-side MOSFET
0	VDS_HC	R	0b	Indicates VDS overcurrent fault on the C high-side MOSFET

9.6.2 Control Registers

表 20 lists the memory-mapped registers for the control registers. All register offset addresses not listed in 表 20 should be considered as reserved locations and the register contents should not be modified.

The IC control registers are used to configure the device. Control registers are read and write capable.

表 20. Control Registers Summary Table

Address	Register Name	Section
0x04	IC1 Control	Go
0x05	IC2 Control	Go
0x06	IC3 Control	Go
0x07	IC4 Control	Go
0x08	IC5 Control	Go
0x09	IC6 Control	Go
0x0A	IC7 Control	Go
0x0B	IC8 Control	Go
0x0C	IC9 Control	Go
0x0D	IC10 Control	Go
0x0E	IC11 Control	Go
0x0F	IC12 Control	Go
0x10	IC13 Control	Go
0x11	IC14 Control	Go

9.6.2.1 IC1 Control Register (Address = 0x04) [reset = 0x00]

IC1 Control is shown in 図 49 and described in 表 21.

図 49. IC1 Control Register

7	6	5	4	3	2	1	0
CLR_FLT	PWM_MODE			1PWM_COM	1PWM_DIR	1PWM_BRAKE	
R/W-0b	R/W-000b			R/W-0b	R/W-0b	R/W-00b	

表 21. IC1 Control Field Descriptions

Bit	Field	Type	Default	Description
7	CLR_FLT	R/W	0b	Write a 1 to this bit to clear all latched fault bits. This bit automatically resets after being written
6-4	PWN_MODE	R/W	000b	**000b = 6x PWM mode** 001b = 3x PWM mode 010b = 1x PWM mode 011b = Independent half-bridge (for all phases) 100b = Phases A and B are independent half-bridges, Phase C is independent FET 101b = Phases B and C are independent half-bridges, Phase A is independent FET 110b = Phase A is independent half-bridge, Phases B and C are independent FET 111b =Independent FET (for all phases)
3	1PWM_COM	R/W	0b	**0b = 1x PWM mode uses synchronous rectification** 1b = 1x PWM mode uses asynchronous rectification (diode freewheeling)
2	1PWM_DIR	R/W	0b	In 1x PWM mode this bit is OR'ed with the INHC (DIR) input

表 21. IC1 Control Field Descriptions (continued)

Bit	Field	Type	Default	Description
1-0	1PWM_BRAKE	R/W	00b	**00b = Outputs follow commanded inputs** 01b = Turn on all three low-side MOSFETs 10b = Turn on all three high-side MOSFETs 11b = Turn off all six MOSFETs (coast)

9.6.2.2 IC2 Control Register (address = 0x05) [reset = 0x40]

IC2 Control is shown in 図 50 and described in 表 22.

図 50. IC2 Control Register

7	6	5	4	3	2	1	0
OTSD_MODE	OLP_SHTS_DLY		EN_SHT_TST	EN_OLP	EN_OLA_C	EN_OLA_B	EN_OLA_A
R/W-0b	R/W-10b		R/W-0b	R/W-0b	R/W-0b	R/W-0b	R/W-0b

表 22. IC2 Control Field Descriptions

Bit	Field	Type	Default	Description
7	OTSD_MODE	R/W	0b	**0b = Overtemperature condition will cause a latched fault** 1b = Overtemperature condition will cause an automatic recovery when the fault condition is removed
6-5	OLP_SHTS_DLY	R/W	10b	00b = OLP delay is 0.25 ms and Shorts test delay is 0.1 ms 01b = OLP delay is 1.25 ms and Shorts test delay is 0.5 ms **10b = OLP delay is 5 ms and Shorts test delay is 2 ms** 11b = OLP delay is 11.5 ms and Shorts test delay is 4.4 ms
4	EN_SHT_TST	R/W	0b	Write a 1 to enable offline short to battery and ground diagnoses
3	EN_OLP	R/W	0b	Write a 1 to enable open load diagnostic in standby mode. When open load test is complete EN_OLP returns to the default setting
2	EN_OLA_C	R/W	0b	Write a 1 to enable open load active diagnostic on Phase C
1	EN_OLA_B	R/W	0b	Write a 1 to enable open load active diagnostic on Phase B
0	EN_OLA_A	R/W	0b	Write a 1 to enable open load active diagnostic on Phase A

9.6.2.3 IC3 Control Register (Address = 0x06) [reset = 0xFF]

IC3 Control is shown in 図 51 and described in 表 23.

図 51. IC3 Control Register

7	6	5	4	3	2	1	0
IDRIVEP_LA				IDRIVEP_HA			
R/W-1111b				R/W-1111b			

表 23. IC3 Control Field Descriptions

Bit	Field	Type	Default	Description
7-4	IDRIVEP_LA	R/W	1111b	0000b = 1.5 mA 0001b = 3.5 mA 0010b = 5 mA 0011b = 10 mA 0100b = 15 mA 0101b = 50 mA 0110b = 60 mA 0111b = 65 mA 1000b = 200 mA 1001b = 210 mA 1010b = 260 mA 1011b = 265 mA 1100b = 735 mA 1101b = 800 mA 1110b = 935 mA **1111b = 1000 mA**
3-0	IDRIVEP_HA	R/W	1111b	0000b = 1.5 mA 0001b = 3.5 mA 0010b = 5 mA 0011b = 10 mA 0100b = 15 mA 0101b = 50 mA 0110b = 60 mA 0111b = 65 mA 1000b = 200 mA 1001b = 210 mA 1010b = 260 mA 1011b = 265 mA 1100b = 735 mA 1101b = 800 mA 1110b = 935 mA **1111b = 1000 mA**

9.6.2.4 IC4 Control Register (Address = 0x07) [reset = 0xFF]

IC4 Control is shown in 図 52 and described in 表 24.

図 52. IC4 Control Register

7	6	5	4	3	2	1	0
IDRIVEP_LB				IDRIVEP_HB			
R/W-1111b				R/W-1111b			

表 24. IC4 Control Field Descriptions

Bit	Field	Type	Default	Description
7-4	IDRIVEP_LB	R/W	1111b	0000b = 1.5 mA 0001b = 3.5 mA 0010b = 5 mA 0011b = 10 mA 0100b = 15 mA 0101b = 50 mA 0110b = 60 mA 0111b = 65 mA 1000b = 200 mA 1001b = 210 mA 1010b = 260 mA 1011b = 265 mA 1100b = 735 mA 1101b = 800 mA 1110b = 935 mA **1111b = 1000 mA**
3-0	IDRIVEP_HB	R/W	1111b	0000b = 1.5 mA 0001b = 3.5 mA 0010b = 5 mA 0011b = 10 mA 0100b = 15 mA 0101b = 50 mA 0110b = 60 mA 0111b = 65 mA 1000b = 200 mA 1001b = 210 mA 1010b = 260 mA 1011b = 265 mA 1100b = 735 mA 1101b = 800 mA 1110b = 935 mA **1111b = 1000 mA**

9.6.2.5 IC5 Control Register (Address = 0x08) [reset = 0xFF]

IC5 Control is shown in 図 53 and described in 表 25.

図 53. IC5 Control Register

7	6	5	4	3	2	1	0
IDRIVEP_LC				IDRIVEP_HC			
R/W-1111b				R/W-1111b			

表 25. IC5 Control Field Descriptions

Bit	Field	Type	Default	Description
7-4	IDRIVEP_LC	R/W	1111b	0000b = 1.5 mA 0001b = 3.5 mA 0010b = 5 mA 0011b = 10 mA 0100b = 15 mA 0101b = 50 mA 0110b = 60 mA 0111b = 65 mA 1000b = 200 mA 1001b = 210 mA 1010b = 260 mA 1011b = 265 mA 1100b = 735 mA 1101b = 800 mA 1110b = 935 mA **1111b = 1000 mA**
3-0	IDRIVEP_HC	R/W	1111b	0000b = 1.5 mA 0001b = 3.5 mA 0010b = 5 mA 0011b = 10 mA 0100b = 15 mA 0101b = 50 mA 0110b = 60 mA 0111b = 65 mA 1000b = 200 mA 1001b = 210 mA 1010b = 260 mA 1011b = 265 mA 1100b = 735 mA 1101b = 800 mA 1110b = 935 mA **1111b = 1000 mA**

9.6.2.6 IC6 Control Register (Address = 0x09) [reset = 0x99]

IC6 Control is shown in 図 54 and described in 表 26.

図 54. IC6 Control Register

7	6	5	4	3	2	1	0
VDS_LVL_LA				VDS_LVL_HA			
R/W-1001b				R/W-1001b			

表 26. IC6 Control Field Descriptions

Bit	Field	Type	Default	Description
7-4	VDS_LVL_LA	R/W	1001b	0000b = 0.06 V 0001b = 0.13 V 0010b = 0.2 V 0011b = 0.26 V 0100b = 0.31 V 0101b = 0.45 V 0110b = 0.53 V 0111b = 0.6 V 1000b = 0.68 V **1001b = 0.75 V** 1010b = 0.94 V 1011b = 1.13 V 1100b = 1.3 V 1101b = 1.5 V 1110b = 1.7 V 1111b = 1.88 V
3-0	VDS_LVL_HA	R/W	1001b	0000b = 0.06 V 0001b = 0.13 V 0010b = 0.2 V 0011b = 0.26 V 0100b = 0.31 V 0101b = 0.45 V 0110b = 0.53 V 0111b = 0.6 V 1000b = 0.68 V **1001b = 0.75 V** 1010b = 0.94 V 1011b = 1.13 V 1100b = 1.3 V 1101b = 1.5 V 1110b = 1.7 V 1111b = 1.88 V

9.6.2.7 IC7 Control Register (Address = 0x0A) [reset = 0x99]

IC7 Control is shown in 図 55 and described in 表 27.

図 55. IC7 Control Register

7	6	5	4	3	2	1	0
VDS_LVL_LB				VDS_LVL_HB			
R/W-1001b				R/W-1001b			

表 27. IC7 Control Field Descriptions

Bit	Field	Type	Default	Description
7-4	VDS_LVL_LB	R/W	1001b	0000b = 0.06 V 0001b = 0.13 V 0010b = 0.2 V 0011b = 0.26 V 0100b = 0.31 V 0101b = 0.45 V 0110b = 0.53 V 0111b = 0.6 V 1000b = 0.68 V **1001b = 0.75 V** 1010b = 0.94 V 1011b = 1.13 V 1100b = 1.3 V 1101b = 1.5 V 1110b = 1.7 V 1111b = 1.88 V
3-0	VDS_LVL_HB	R/W	1001b	0000b = 0.06 V 0001b = 0.13 V 0010b = 0.2 V 0011b = 0.26 V 0100b = 0.31 V 0101b = 0.45 V 0110b = 0.53 V 0111b = 0.6 V 1000b = 0.68 V **1001b = 0.75 V** 1010b = 0.94 V 1011b = 1.13 V 1100b = 1.3 V 1101b = 1.5 V 1110b = 1.7 V 1111b = 1.88 V

9.6.2.8 IC8 Control Register (Address = 0x0B) [reset = 0x99]

IC8 control is shown in 図 56 and described in 表 28.

図 56. IC8 Control Register

7	6	5	4	3	2	1	0
VDS_LVL_LC				VDS_LVL_HC			
R/W-1001b				R/W-1001b			

表 28. IC8 Control Field Descriptions

Bit	Field	Type	Default	Description
7-4	VDS_LVL_LC	R/W	1001b	0000b = 0.06 V 0001b = 0.13 V 0010b = 0.2 V 0011b = 0.26 V 0100b = 0.31 V 0101b = 0.45 V 0110b = 0.53 V 0111b = 0.6 V 1000b = 0.68 V **1001b = 0.75 V** 1010b = 0.94 V 1011b = 1.13 V 1100b = 1.3 V 1101b = 1.5 V 1110b = 1.7 V 1111b = 1.88 V
3-0	VDS_LVL_HC	R/W	1001b	0000b = 0.06 V 0001b = 0.13 V 0010b = 0.2 V 0011b = 0.26 V 0100b = 0.31 V 0101b = 0.45 V 0110b = 0.53 V 0111b = 0.6 V 1000b = 0.68 V **1001b = 0.75 V** 1010b = 0.94 V 1011b = 1.13 V 1100b = 1.3 V 1101b = 1.5 V 1110b = 1.7 V 1111b = 1.88 V

9.6.2.9 IC9 Control Register (Address = 0x0C) [reset = 0x2F]

IC9 Control is shown in 図 57 and described in 表 29.

図 57. IC9 Control Register

7	6	5	4	3	2	1	0
COAST	TRETRY		DEAD_TIME		TDRIVE_MAX	TDRIVE	
R/W-0b	R/W-01b		R/W-01b		R/W-1b	R/W-11b	

表 29. IC9 Control Field Descriptions

Bit	Field	Type	Default	Description
7	COAST	R/W	0b	Write a 1 to this bit to put all the MOSFETs in the Hi-Z state
6-5	TRETRY	R/W	01b	00b = 2 ms **01b = 4 ms** 10b = 6 ms 11b = 8 ms
4-3	DEAD_TIME	R/W	01b	00b = 500 ns **01b = 1000 ns** 10b = 2000 ns 11b = 4000 ns
2	TDRIVE_MAX	R/W	1b	Write a 0 to this bit to disable the maximum t_{DRIVE} time of 20 µs. This bit is automatically enabled when IDRIVE = 0000b, 0001b, 0010b, or 0011b is selected
1-0	TDRIVE	R/W	11b	00b = 500 ns peak gate-current drive time 01b = 1000 ns peak gate-current drive time 10b = 2000 ns peak gate-current drive time **11b = 3000 ns peak gate-current drive time**

9.6.2.10 IC10 Control Register (Address = 0x0D) [reset = 0x61]

IC10 Control is shown in 図 58 and described in 表 30.

図 58. IC10 Control Register

7	6	5	4	3	2	1	0
LOCK			DIS_CPUV	DIS_GDF	OCP_DEG		
R/W-011b			R/W-0b	R/W-0b	R/W-001b		

表 30. IC10 Control Field Descriptions

Bit	Field	Type	Default	Description
7-5	LOCK	R/W	011b	Write 110b to lock the settings by ignoring further register writes except to these bits and address 0x04h bit 7 (CLR_FLT). Writing any sequence other than 110b has no effect when unlocked. Write 011b to this register to unlock all registers. Writing any sequence other than 011b has no effect when locked.
4	DIS_CPUV	R/W	0b	**0b = Charge-pump undervoltage lockout fault is enabled** 1b = Charge-pump undervoltage lockout fault is disabled
3	DIS_GDF	R/W	0b	**0b = Gate drive fault is enabled** 1b = Gate drive fault is disabled

表 30. IC10 Control Field Descriptions (continued)

Bit	Field	Type	Default	Description
2-0	OCP_DEG	R/W	001b	000b = 2.5 µs **001b = 4.75 µs** 010b = 6.75 µs 011b = 8.75 µs 100b = 10.25 µs 101b = 11.5 µs 110b = 16.5 µs 111b = 20.5 µs

9.6.2.11 IC11 Control Register (Address = 0x0E) [reset = 0x00]

IC11 Control is shown in 図 59 and described in 表 31.

図 59. IC11 Control Register

7	6	5	4	3	2	1	0
RSVD	OTW_REP	CBC	DIS_VDS_C	DIS_VDS_B	DIS_VDS_A	OCP_MODE	
R/W-0b	R/W-0b	R/W-0b	R/W-0b	R/W-0b	R/W-0b	R/W-00b	

表 31. IC11 Control Field Descriptions

Bit	Field	Type	Default	Description
7	RSVD	R/W	0b	Reserved
6	OTW_REP	R/W	0b	**0b = Overtemperature warning is not reported on nFAULT** 1b = Overtemperature warning is reported on nFAULT
5	CBC	R/W	0b	In retry OCP_MODE, for both VDS_OCP and SEN_OCP, the fault is automatically cleared when a PWM input is given
4	DIS_VDS_C	R/W	0b	Write a 1 to this bit to disable VDS_OCP for MOSFETs in Phase C
3	DIS_VDS_B	R/W	0b	Write a 1 to this bit to disable VDS_OCP for MOSFETs in Phase B
2	DIS_VDS_A	R/W	0b	Write a 1 to this bit to disable VDS_OCP for MOSFETs in Phase A
1-0	OCP_MODE	R/W	00b	**00b = Overcurrent causes a latched fault** 01b = Overcurrent causes an automatic retrying fault 10b = Overcurrent is report only but no action is taken 11b = Overcurrent is not reported and no action is taken

9.6.2.12 IC12 Control Register (Address = 0x0F) [reset = 0x2A]

IC12 Control is shown in 図 60 and described in 表 32.

図 60. IC12 Control Register

7	6	5	4	3	2	1	0
LS_REF	CSA_FET	CSA_GAIN_C		CSA_GAIN_B		CSA_GAIN_A	
R/W-0b	R/W-0b	R/W-10b		R/W-10b		R/W-10b	

表 32. IC12 Control Field Descriptions

Bit	Field	Type	Default	Description
7	LS_REF	R/W	0b	**0b = VDS_OCP for the low-side MOSFET is measured across DLx to SLx** 1b = VDS_OCP for the low-side MOSFET is measured across DLx to AGND (see 図 37)
6	CSA_FET	R/W	0b	**0b = Current sense amplifier positive input is SPx** 1b = Current sense amplifier positive input is DLx (also automatically sets the LS_REF bit to 1b
5-4	CSA_GAIN_C	R/W	10b	00b = 5 V/V current sense amplifier gain 01b = 10 V/V current sense amplifier gain **10b = 20 V/V current sense amplifier gain** 11b = 40 V/V current sense amplifier gain
3-2	CSA_GAIN_B	R/W	10b	00b = 5 V/V current sense amplifier gain 01b = 10 V/V current sense amplifier gain **10b = 20 V/V current sense amplifier gain** 11b = 40 V/V current sense amplifier gain
1-0	CSA_GAIN_A	R/W	10b	00b = 5 V/V current sense amplifier gain 01b = 10 V/V current sense amplifier gain **10b = 20 V/V current sense amplifier gain** 11b = 40 V/V current sense amplifier gain

9.6.2.13 IC13 Control Register (Address = 0x10) [reset = 0x7F]

IC13 Control is shown in 図 61 and described in 表 33.

図 61. IC13 Control Register

7	6	5	4	3	2	1	0
CAL_MODE	VREF_DIV	SEN_LVL_C		SEN_LVL_B		SEN_LVL_B	
R/W-0b	R/W-1b	R/W-11b		R/W-11b		R/W-11b	

表 33. IC13 Control Field Descriptions

Bit	Field	Type	Default	Description
7	CAL_MODE	R/W	0b	**0b = Amplifier calibration operates in manual mode** 1b = Amplifier calibration uses internal auto calibration routine
6	VREF_DIV	R/W	1b	0b = Sense amplifier reference voltage is VREF (unidirectional mode) **1b = Sense amplifier reference voltage is VREF divided by 2**
5-4	SEN_LVL_C	R/W	11b	00b = Sense OCP 0.25 V 01b = Sense OCP 0.5 V 10b = Sense OCP 0.75 V **11b = Sense OCP 1 V**
3-2	SEN_LVL_B	R/W	11b	00b = Sense OCP 0.25 V 01b = Sense OCP 0.5 V 10b = Sense OCP 0.75 V **11b = Sense OCP 1 V**
1-0	SEN_LVL_A	R/W	11b	00b = Sense OCP 0.25 V 01b = Sense OCP 0.5 V 10b = Sense OCP 0.75 V **11b = Sense OCP 1 V**

9.6.2.14 IC14 Control Register (Address = 0x10) [reset = 0x00]

IC14 Control is shown in 図 62 and described in 表 34.

図 62. IC14 Control Register

7	6	5	4	3	2	1	0
RSVD		DIS_SEN_C	DIS_SEN_B	DIS_SEN_A	CSA_CAL_C	CSA_CAL_B	CSA_CAL_A
R/W-00b		R/W-0b	R/W-0b	R/W-0b	R/W-0b	R/W-0b	R/W-0b

表 34. IC14 Control Field Descriptions

Bit	Field	Type	Default	Description
7-6	RSVD	R/W	00b	Reserved
5	DIS_SEN_C	R/W	0b	**0b = Sense overcurrent fault is enabled for Phase C** 1b = Sense overcurrent fault is disabled for Phase C
4	DIS_SEN_B	R/W	0b	**0b = Sense overcurrent fault is enabled for Phase B** 1b = Sense overcurrent fault is disabled for Phase B
3	DIS_SEN_A	R/W	0b	**0b = Sense overcurrent fault is enabled for Phase A** 1b = Sense overcurrent fault is disabled for Phase A
2	CSA_CAL_C	R/W	0b	**0b = Normal current sense amplifier C operation** 1b = Short inputs to current sense amplifier C for offset calibration (manual calibration mode) if CAL_MODE = 0b. Auto calibration mode if CAL_MODE = 1b.
1	CSA_CAL_B	R/W	0b	**0b = Normal current sense amplifier B operation** 1b = Short inputs to current sense amplifier B for offset calibration (manual calibration mode) if CAL_MODE = 0b. Auto calibration mode if CAL_MODE = 1b.
0	CSA_CAL_A	R/W	0b	**0b = Normal current sense amplifier A operation** 1b = Short inputs to current sense amplifier A for offset calibration (manual calibration mode) if CAL_MODE = 0b. Auto calibration mode if CAL_MODE = 1b.

10 Application and Implementation

注

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

10.1 Application Information

The DRV8343-Q1 device is primarily used in applications for three-phase brushless DC motor control. The design procedures in the *Typical Application* section highlight how to use and configure the DRV8343-Q1 device.

10.2 Typical Application

10.2.1 Primary Application

The DRV8343-Q1 SPI device is used in this application example.

Typical Application (continued)

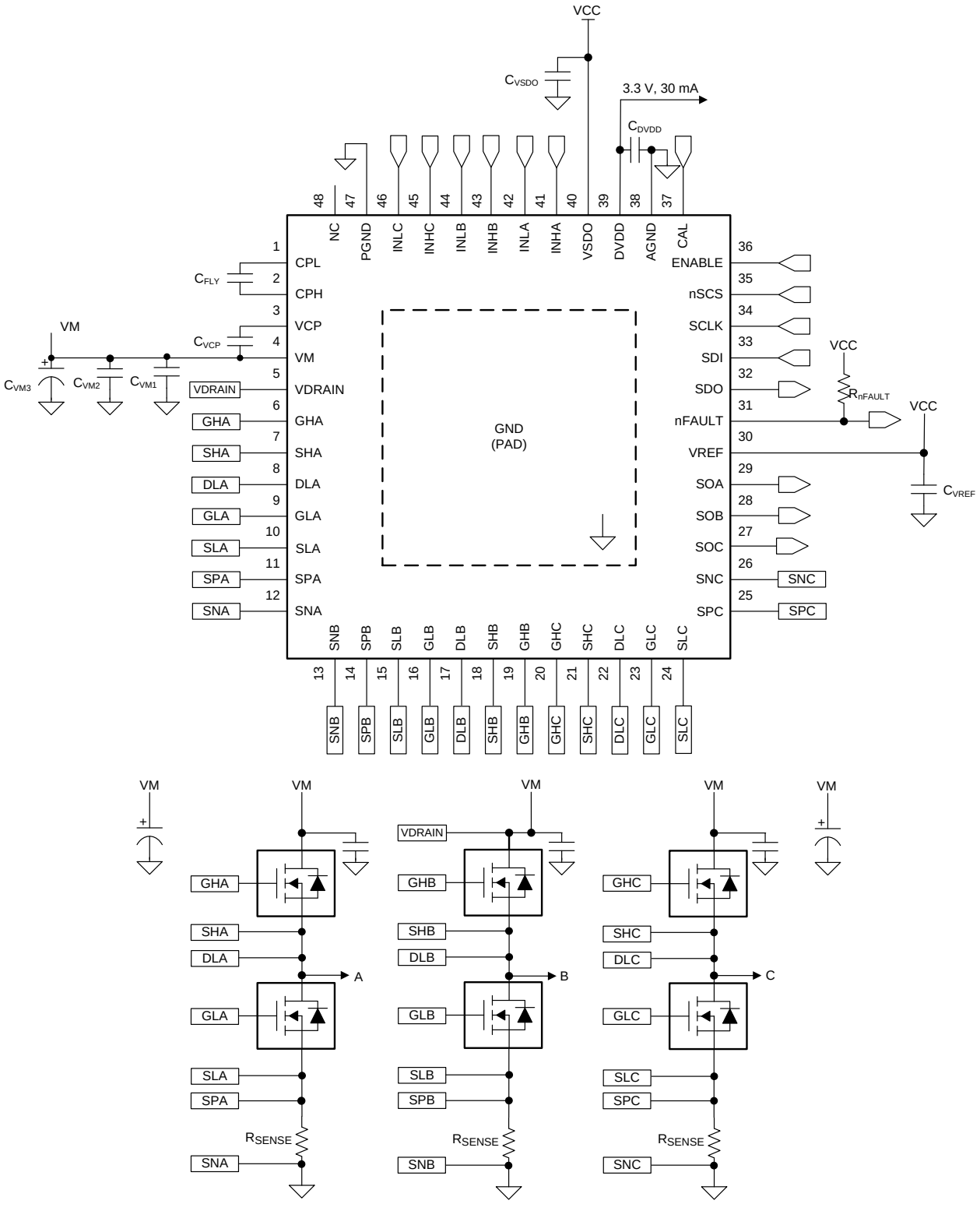


図 63. Primary Application Schematic

Typical Application (continued)

10.2.1.1 Design Requirements

表 35 lists the example input parameters for the system design.

表 35. Design Parameters

EXAMPLE DESIGN PARAMETER	REFERENCE	EXAMPLE VALUE
Nominal supply voltage	V_{VM}	24 V
Supply voltage range		8 V to 45 V
MOSFET part number		CSD18536KCS
MOSFET total gate charge	Q_g	83 nC (typical) at V_{VGS} = 10 V
MOSFET gate to drain charge	Q_{gd}	14 nC (typical)
Target output rise time	t_r	1000 ns
PWM Frequency	f_{PWM}	10 kHz
Maximum motor current	I_{max}	100 A
ADC reference voltage	V_{VREF}	3.3 V
Winding sense current range	I_{SENSE}	–40 A to +40 A
Motor RMS current	I_{RMS}	28.3 A
Sense resistor power rating	P_{SENSE}	2 W
System ambient temperature	T_A	–40°C to 125°C

10.2.1.2 Detailed Design Procedure

10.2.1.2.1 External MOSFET Support

The DRV8343-Q1 MOSFET support is based on the capacity of the charge pump and PWM switching frequency of the output. For a quick calculation of MOSFET driving capacity, use 式 6 and 式 7 for three phase BLDC motor applications.

Trapezoidal 120° Commutation: $I_{VCP} > Q_g \times f_{PWM}$

where

- f_{PWM} is the maximum desired PWM switching frequency.
- I_{VCP} is the charge pump capacity, which depends on the VM pin voltage.
- The multiplier based on the commutation control method, may vary based on implementation. (6)

Sinusoidal 180° Commutation: $I_{VCP} > 3 \times Q_g \times f_{PWM}$ (7)

10.2.1.2.1.1 Example

If a system with a V_{VM} voltage of 8 V (I_{VCP} = 15 mA) uses a maximum PWM switching frequency of 10 kHz, then the charge pump can support MOSFETs using trapezoidal commutation with a Q_g less than 750 nC, and MOSFETs using sinusoidal commutation with a Q_g less than 250 nC.

10.2.1.2.2 IDRIVE Configuration

The strength of the gate drive current, I_{DRIVE}, is selected based on the gate-to-drain charge of the external MOSFETs and the target rise and fall times at the outputs. If I_{DRIVE} is selected to be too low for a given MOSFET, then the MOSFET may not turn on completely within the t_{DRIVE} time and a gate drive fault may be asserted. Additionally, slow rise and fall times result in higher switching power losses. TI recommends adjusting these values in the system with the required external MOSFETs and motor to determine the best possible setting for any application.

The I_{DRIVEP} and I_{DRIVEN} current for both the low-side and high-side MOSFETs are independently adjustable on SPI devices through the SPI registers. On hardware interface devices, both source and sink settings are selected at the same time on the IDRIVE pin.

For MOSFETs with a known gate-to-drain charge Q_{gd}, desired rise time (t_r), and a desired fall time (t_f), use 式 8 and 式 9 to calculate the value of I_{DRIVEP} and I_{DRIVEN} (respectively).

$$I_{DRIVEP} > Q_{gd} \times t_r \quad (8)$$

$$I_{DRIVEN} = 2 \times I_{DRIVEP} \quad (9)$$

10.2.1.2.2.1 Example

Use 式 10 to calculate the value of I_{DRIVEP} for a gate-to-drain charge of 14 nC and a rise time from 100 to 300 ns.

$$I_{DRIVEP} = \frac{12\ nC}{1000\ ns} 14\ mA \quad (10)$$

Select an I_{DRIVEP} value that is close to 14 mA which will set the I_{DRIVEN} value close to 28 mA. For this example, the value of I_{DRIVEP} was selected as 15 mA.

10.2.1.2.3 V_{DS} Overcurrent Monitor Configuration

The V_{DS} monitors are configured based on the worst-case motor current and the $R_{DS(on)}$ of the external MOSFETs as shown in 式 11.

$$V_{DS\_OCP} > I_{max} \times R_{DS(on)max} \quad (11)$$

10.2.1.2.3.1 Example

The goal of this example is to set the V_{DS} monitor to trip at a current greater than 100 A. According to the *CSD18536KCS 60 V N-Channel NexFET™ Power MOSFET* data sheet, the $R_{DS(on)}$ value is 1.8 times higher at 175°C, and the maximum $R_{DS(on)}$ value at a V_{GS} of 10 V is 1.6 mΩ. From these values, the approximate worst-case value of $R_{DS(on)}$ is 1.8 × 1.6 mΩ = 2.88 mΩ.

Using 式 11 with a value of 2.88 mΩ for $R_{DS(on)}$ and a worst-case motor current of 100 A, 式 12 shows the calculated the value of the V_{DS} monitors.

$$V_{DS\_OCP} > 100\ A \times 2.88\ m\Omega$$
$$V_{DS\_OCP} > 0.288\ V \quad (12)$$

For this example, the value of V_{DS_OCP} was selected as 0.31 V.

The SPI devices allow for adjustment of the deglitch time for the V_{DS} overcurrent monitor. The deglitch time can be set to 2 µs, 4 µs, 6 µs, 8 µs, 10 µs, 12 µs, 16 µs, or 20 µs.

10.2.1.2.4 Sense Amplifier Bidirectional Configuration

The sense amplifier gain on the DRV8343-Q1 device and sense resistor value are selected based on the target current range, VREF voltage supply, power rating of the sense resistor, and operating temperature range. In bidirectional operation of the sense amplifier, the dynamic range at the output is approximately calculated as shown in 式 13.

$$V_O = \left(V_{VREF} - 0.25\ V\right) - \frac{V_{VREF}}{2} \quad (13)$$

Use 式 14 to calculate the approximate value of the selected sense resistor with V_O calculated using 式 13.

$$R = \frac{V_O}{A_V \times I} \qquad P_{SENSE} > I_{RMS}^2 \times R \quad (14)$$

From 式 13 and 式 14, select a target gain setting based on the power rating of the target sense resistor.

10.2.1.2.4.1 Example

In this system example, the value of the VREF voltage is 3.3 V with a sense current from –40 to +40 A. The linear range of the SOx output is 0.25 V to V_{VREF} – 0.25 V (from the V_{LINEAR} specification). The differential range of the sense amplifier input is –0.3 to +0.3 V (V_{DIFF}).

$$V_O = \left(3.3\ V - 0.25\ V\right) - \frac{3.3\ V}{2} = 1.4\ V \quad (15)$$

$$R = \frac{1.4\ V}{A_V \times 40\ A} \qquad 2\ W > 28.3^2 \times R \rightarrow R < 2.5\ m\Omega \quad (16)$$

$$2.5\ m\Omega > \frac{1.4\ V}{A_V \times 40\ A} \rightarrow A_V > 14 \quad (17)$$

Therefore, the gain setting must be selected as 20 V/V or 40 V/V and the value of the sense resistor must be less than 2.5 mΩ to meet the power rating for the sense resistor. For this example, the gain setting was selected as 20 V/V. The value of the resistor and worst case current can be verified that R < 2.5 mΩ and I_{max} = 40 A does not violate the differential range specification of the sense amplifier input (V_{SPxD}).

10.2.1.2.5 External Components

表 36lists the recommended external components.

表 36. External Components

COMPONENT	PIN 1	PIN 2	RECOMMENDED
C_{FLY}	CPH	CPL	47-nF ceramic capacitor X5R or X7R rated for VM(1)
C_{VCP}	VCP	VM	1-µF ceramic capacitor X5R or X7R rated for VCP – VM (1)
C_{VM1}	VM	PGND	0.1-µF ceramic capacitor X5R or X7R rated for VM(1)
C_{VM2}	VM	PGND	4.7-µF ceramic capacitor X5R or X7R rated for VM(1)
C_{VM3}	VM	PGND	> 10-µF electrolytic capacitor rated for VM(1)
C_{VREF}	VREF	AGND	0.1-µF ceramic capacitor X5R or X7R rated for VREF(1)
C_{DVDD}	DVDD	AGND	1-µF ceramic capacitor X5R or X7R rated for DVDD(1)
C_{VSDO}	VSDO	AGND	0.1-µF ceramic capacitor X5R or X7R rated for VSDO(1). DRV8343S only
R_{nFAULT}	nFAULT	VCC(2)	2.5 – 10 kΩ pulled up the MCU I/O (VCC) power supply
R_{SENSE}	SPx	SNx	2.5 mΩ shunt resistor for current sense amplifier

(1) The effective capacitance of ceramic capacitors varies with DC operating voltage and temperature. As a rule of thumb, expect the effective capacitance to decrease by as much as 50% at the extremes of the operating voltage. The system designer must review the capacitor characteristics and select the component accordingly.
(2) The VCC pin is not a pin on the DRV8343-Q1 device, but a VCC supply voltage pullup is required for the open-drain output, nFAULT. These pins can also be pulled up to DVDD.

10.2.1.3 Application Curves

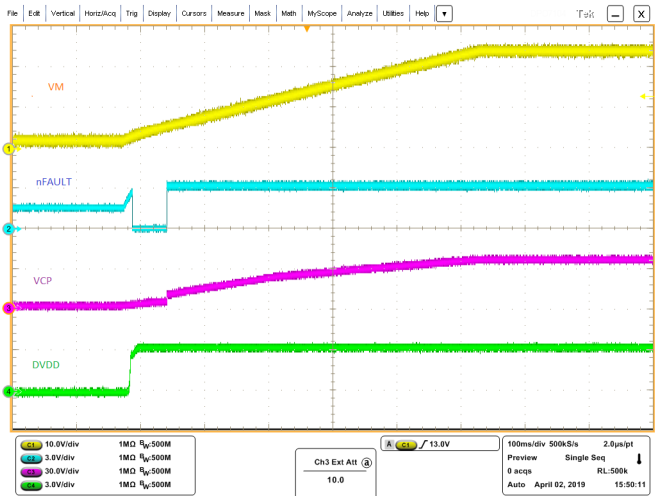


図 64. Device Power Up Sequence Waveform

図 65. BLDC Motor Commutation and Current Sense

10.2.2 Application With One Sense Amplifier

In this application, one sense amplifier is used in unidirectional mode for a summing current sense scheme often used in trapezoidal or hall-based BLDC commutation control.

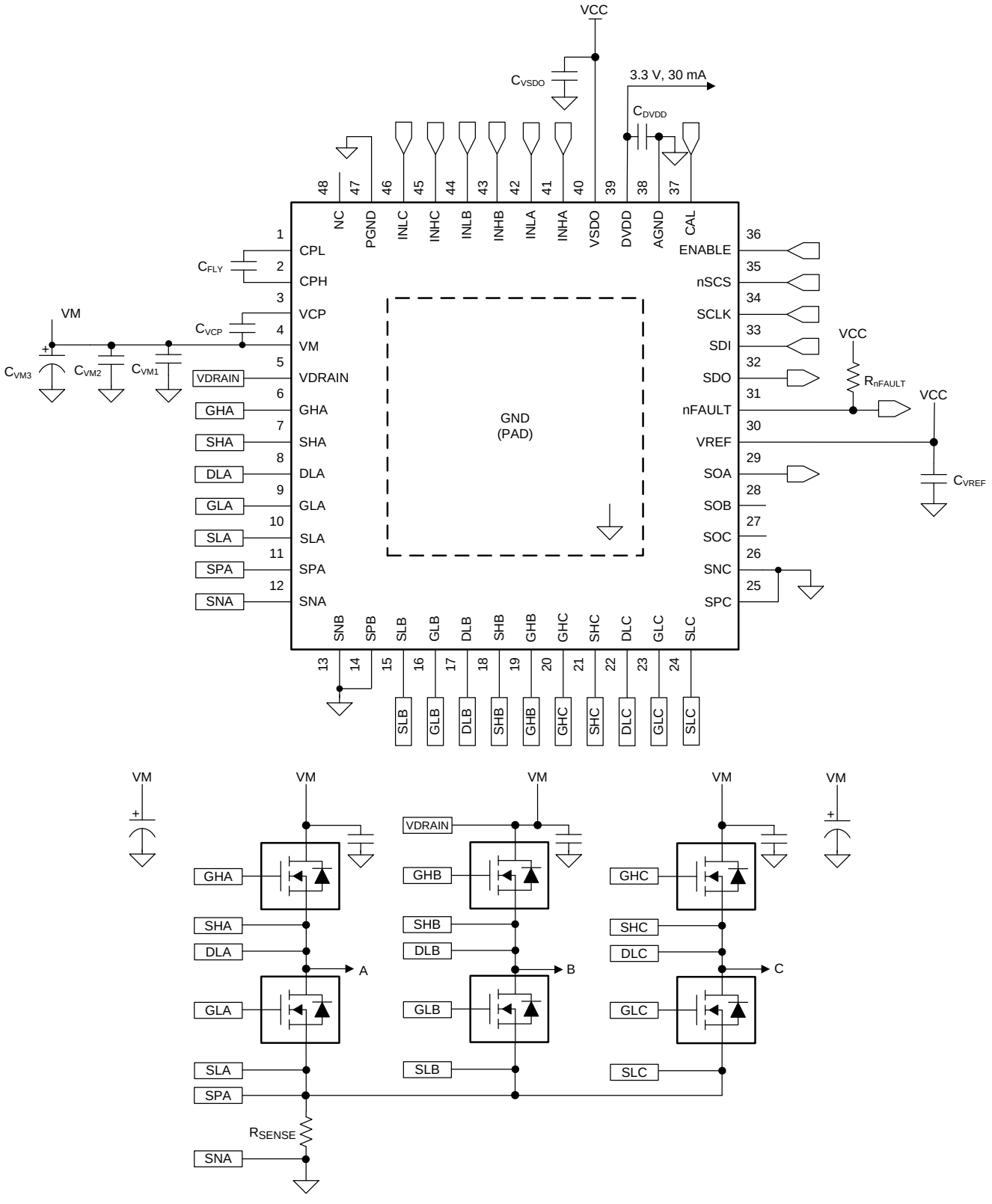


図 66. Alternative Application Schematic

10.2.2.1 Design Requirements

表 37 lists the example design input parameters for system design.

表 37. Design Parameters

EXAMPLE DESIGN PARAMETER	REFERENCE	EXAMPLE VALUE
ADC reference voltage	V_{VREF}	3.3 V
Sensed current	I_{SENSE}	0 to 40 A
Motor RMS current	I_{RMS}	28.3 A
Sense-resistor power rating	P_{SENSE}	3 W
System ambient temperature	T_A	–40°C to 125°C

10.2.2.2 Detailed Design Procedure

10.2.2.2.1 Sense Amplifier Unidirectional Configuration

The sense amplifiers are configured to be unidirectional through the registers on SPI devices by writing a 0 to the VREF_DIV bit.

The sense amplifier gain and sense resistor values are selected based on the target current range, VREF, power rating of the sense resistor, and operating temperature range. In unidirectional operation of the sense amplifier, use 式 18 to calculate the approximate value of the dynamic range at the output.

$$V_O = (V_{VREF} - 0.25\ V) - 0.25\ V = V_{VREF} - 0.5\ V \quad (18)$$

Use 式 19 to calculate the approximate value of the selected sense resistor.

$$R = \frac{V_O}{A_V \times I} \qquad P_{SENSE} > I_{RMS}{}^2 \times R$$

where

- $V_O = V_{VREF} - 0.5\ V$ (19)

From 式 18 and 式 19, select a target gain setting based on the power rating of a target sense resistor.

10.2.2.2.1.1 Example

In this system example, the value of the VREF voltage is 3.3 V with a sense current from 0 to 40 A. The linear range of the SOx output for the device is 0.25 V to V_{VREF} – 0.25 V (from the V_{LINEAR} specification). The differential range of the sense-amplifier input is –0.3 to +0.3 V (V_{DIFF}).

$$V_O = 3.3\ V - 0.5\ V = 2.8\ V \quad (20)$$

$$R = \frac{2.8\ V}{A_V \times 40\ A} \qquad 3\ W > 28.3^2 \times R \rightarrow R < 3.75\ m\Omega \quad (21)$$

$$3.75\ m\Omega > \frac{2.8\ V}{A_V \times 40\ A} \rightarrow A_V > 18.7 \quad (22)$$

Therefore, the gain setting must be selected as 20 V/V or 40 V/V and the value of the sense resistor must be less than 3.75 mΩ to meet the power rating for the sense resistor. For this example, the gain setting was selected as 20 V/V. The value of the resistor and worst-case current can be verified that R < 3.75 mΩ and I_{max} = 40 A does not violate the differential range specification of the sense amplifier input (V_{SPxD}).

10.2.2.2.1.2 Unused pins

One sense amplifier, channel A, is used in the figure 図 66, and channel B and C are not used. The connections of the channel B and C sense amplifier signals are recommended as below;

- Connect SPB, SNB, SPC and SNC pins to AGND
- Leave SOB and SOC pins open

10.2.2.2.2 External Components

Refer to 表 36 for the recommended external components.

11 Power Supply Recommendations

The DRV8343-Q1 device is designed to operate from an input voltage supply (VM) range from 6 V to 60 V.

11.1 Power Supply Consideration in Generator Mode

When the motor shaft of BLDC or PMSM motor is turned by an external force, the motor windings will generate a voltage on the motor inputs. This condition is known as generator mode or motor back-drive. In the generator mode, a positive voltage can be observed on SHx pins of the device. If there is a switch between VDRAIN and VM (SW_{VDRAIN} in 図 67) and the following conditions exist in the system, the absolute max voltage of VCP with respect to VM needs to be reviewed;

- Generator mode
- SW_{VDRAIN} is off
- VM and VCP are low voltage (e.g. VM = 0V)

If SHx voltage (V_{SHx}) exceeds VCP voltage, the VCP voltage starts following V_{SHx} because of the device internal diodes D1 and D2 (or D3). If VCP - VM voltage exceeds the absolute max voltage of DRV8343-Q1, the ESD diode D4 starts conducting and results in a big current from SHx to VM through the diodes D2, D1 and D4. To avoid this condition, it is recommended to add an external diode D_{VDRAIN_VM} between VDRAIN and VM.

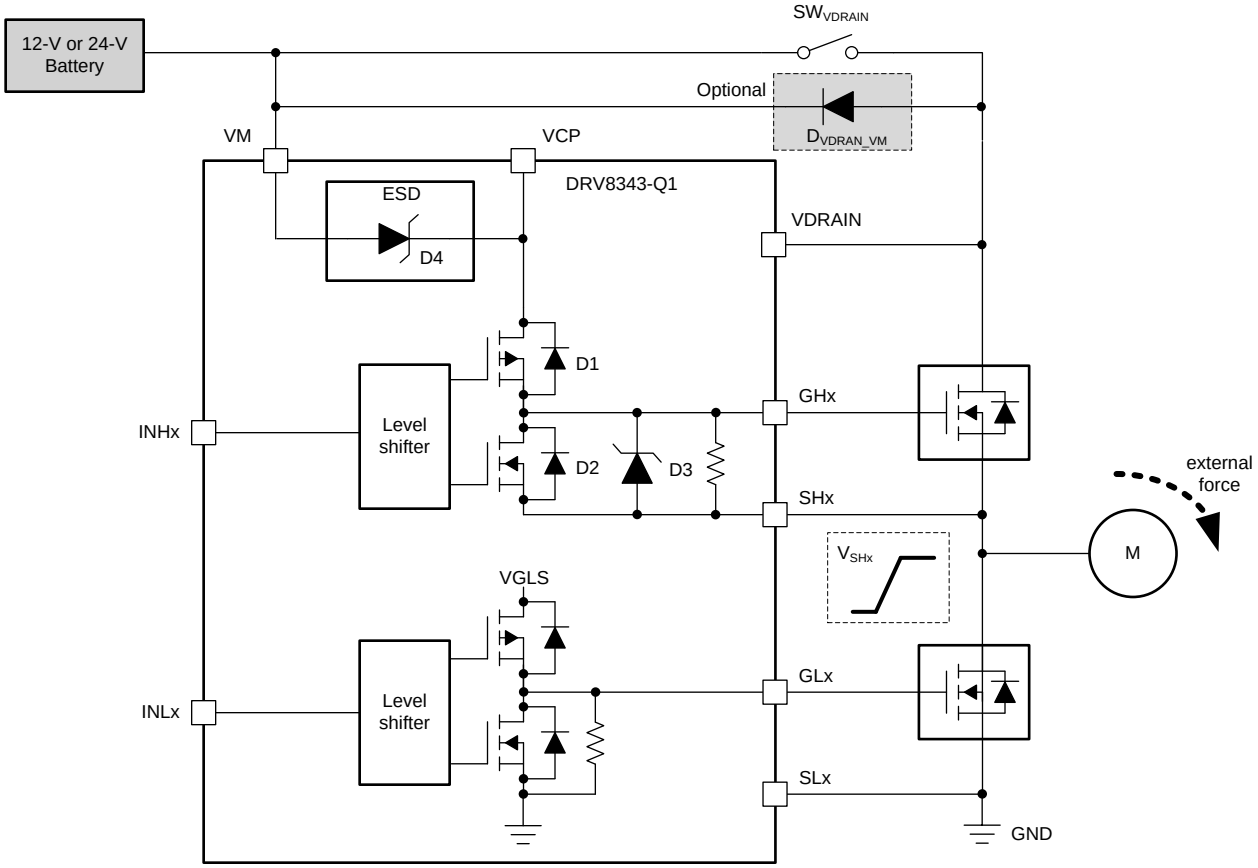


図 67. Power Supply Consideration in Generator mode

11.2 Bulk Capacitance Sizing

Having appropriate local bulk capacitance is an important factor in motor drive system design. It is generally beneficial to have more bulk capacitance, while the disadvantages are increased cost and physical size. The amount of local capacitance depends on a variety of factors including:

- The highest current required by the motor system
- The power supply's type, capacitance, and ability to source current

Bulk Capacitance Sizing (continued)

- The amount of parasitic inductance between the power supply and motor system
- The acceptable supply voltage ripple
- Type of motor (brushed DC, brushless DC, stepper)
- The motor startup and braking methods

The inductance between the power supply and motor drive system will limit the rate current can change from the power supply. If the local bulk capacitance is too small, the system will respond to excessive current demands or dumps from the motor with a change in voltage. When adequate bulk capacitance is used, the motor voltage stays stable and high current can be quickly supplied.

The data sheet provides a recommended minimum value, but system level testing is required to determine the appropriate sized bulk capacitor.

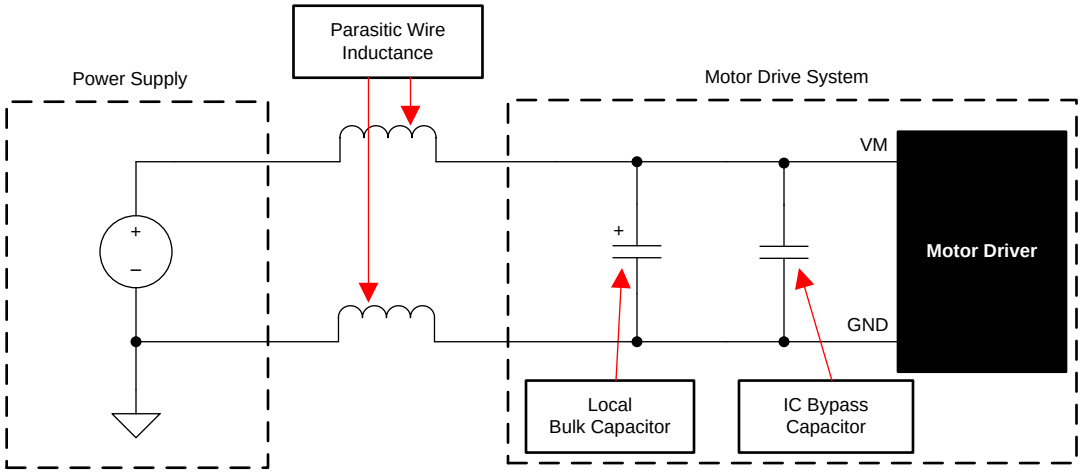


図 68. Motor Drive Supply Parasitics Example

12 Layout

12.1 Layout Guidelines

Bypass the VM pin to the PGND pin using a low-ESR ceramic bypass capacitor C_{VM1}. Place this capacitor as close to the VM pin as possible with a thick trace or ground plane connected to the PGND pin. Additionally, bypass the VM pin using a bulk capacitor rated for VM. This component can be electrolytic. This capacitance must be at least 10 µF.

Additional bulk capacitance is required to bypass the high current path on the external MOSFETs. This bulk capacitance should be placed such that it minimizes the length of any high current paths through the external MOSFETs. The connecting metal traces should be as wide as possible, with numerous vias connecting PCB layers. These practices minimize inductance and let the bulk capacitor deliver high current.

Place a low-ESR ceramic capacitor C_{FLY} between the CPL and CPH pins. Additionally, place a low-ESR ceramic capacitor C_{VCP} between the VCP and VM pins.

Bypass the DVDD pin to the AGND pin with C_{DVDD}. Place this capacitor as close to the pin as possible and minimize the path from the capacitor to the AGND pin.

The VDRAIN pin can be shorted directly to the VM pin. However, if a significant distance is between the device and the external MOSFETs, use a dedicated trace to connect to the common point of the drains of the high-side external MOSFETs. Do not connect the SLx pins directly to PGND. Instead, use dedicated traces to connect these pins to the sources of the low-side external MOSFETs. These recommendations offer more accurate V_{DS} sensing of the external MOSFETs for overcurrent detection.

Minimize the loop length for the high-side and low-side gate drivers. The high-side loop is from the GHx pin of the device to the high-side power MOSFET gate, then follows the high-side MOSFET source back to the SHx pin. The low-side loop is from the GLx pin of the device to the low-side power MOSFET gate, then follows the low-side MOSFET source back to the PGND pin.

12.2 Layout Example

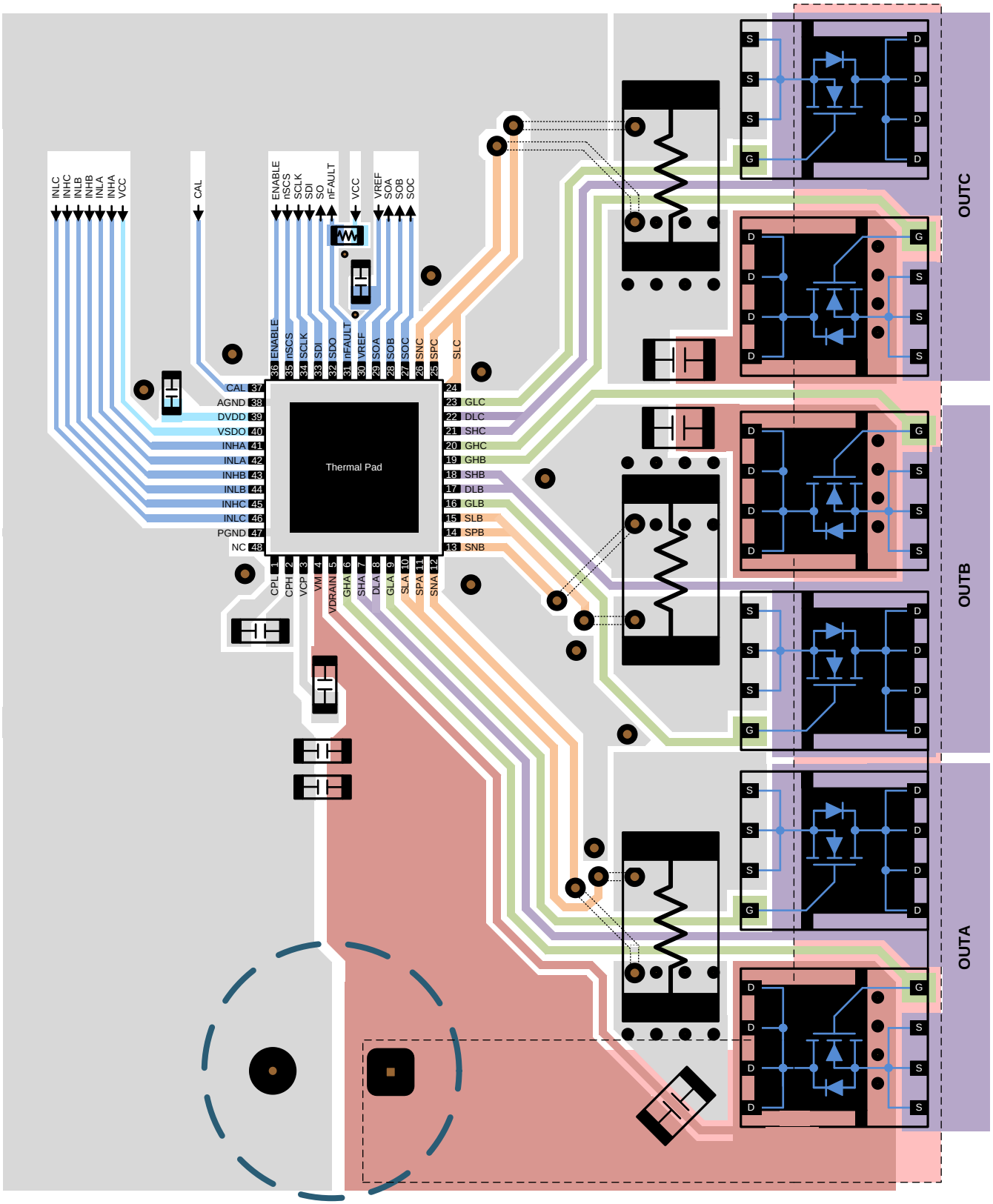


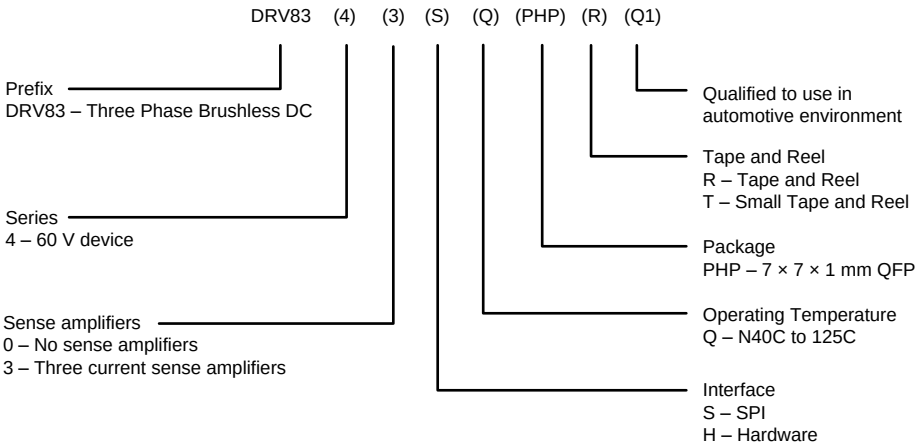
図 69. Layout Example

13 デバイスおよびドキュメントのサポート

13.1 デバイス・サポート

13.1.1 デバイスの項目表記

次の図は、完全なデバイス名を解釈するための凡例を示したものです。



13.2 ドキュメントのサポート

13.2.1 関連資料

- テキサス・インスツルメンツ、*『AN-1149 スイッチング電源のレイアウトのガイドライン』*アプリケーション・レポート
- テキサス・インスツルメンツ、*『DRV834x-Q1の強化されたフォルト診断』* TI TechNote
- テキサス・インスツルメンツ、*『BLDCモーターを使用する電動自転車のハードウェア設計の考慮事項』*
- テキサス・インスツルメンツ、*『スイッチング電源のレイアウトのガイドライン』*
- テキサス・インスツルメンツ、*『MSP430™を使用するセンサ付き3相BLDCモーター制御』*アプリケーション・レポート
- テキサス・インスツルメンツ、*『TI製モーター・ゲート・ドライバでのIDRIVEおよびTDRIVEについて』*アプリケーション・レポート

13.3 ドキュメントの更新通知を受け取る方法

ドキュメントの更新についての通知を受け取るには、ti.comのデバイス製品フォルダを開いてください。右上の「アラートを受け取る」をクリックして登録すると、変更されたすべての製品情報に関するダイジェストを毎週受け取れます。変更の詳細については、修正されたドキュメントに含まれている改訂履歴をご覧ください。

13.4 コミュニティ・リソース

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

TI E2E™ Online Community ***TI's Engineer-to-Engineer (E2E) Community.*** Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support ***TI's Design Support*** Quickly find helpful E2E forums along with design support tools and contact information for technical support.

13.5 商標

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13.6 静電気放電に関する注意事項

すべての集積回路は、適切なESD保護方法を用いて、取扱いと保存を行うようにして下さい。

静電気放電はわずかな性能の低下から完全なデバイスの故障に至るまで、様々な損傷を与えます。高精度の集積回路は、損傷に対して敏感であり、極めてわずかなパラメータの変化により、デバイスに規定された仕様に適合しなくなる場合があります。

13.7 Glossary

SLYZ022 — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

14 メカニカル、パッケージ、および注文情報

以降のページには、メカニカル、パッケージ、および注文に関する情報が記載されています。この情報は、そのデバイスについて利用可能な最新のデータです。このデータは予告なく変更されることがあり、ドキュメントが改訂される場合もあります。本データシートのブラウザ版を使用されている場合は、画面左側の説明をご覧ください。

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package | Pins	Package qty | Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
DRV8343HPHPRQ1	Active	Production	HTQFP (PHP) | 48	1000 | LARGE T&R	Yes	NIPDAU	Level-3-260C-168 HR	-40 to 125	DRV8343H
DRV8343HPHPRQ1.A	Active	Production	HTQFP (PHP) | 48	1000 | LARGE T&R	Yes	NIPDAU	Level-3-260C-168 HR	-40 to 125	DRV8343H
DRV8343SPHPRQ1	Active	Production	HTQFP (PHP) | 48	1000 | LARGE T&R	Yes	NIPDAU	Level-3-260C-168 HR	-40 to 125	DRV8343S
DRV8343SPHPRQ1.A	Active	Production	HTQFP (PHP) | 48	1000 | LARGE T&R	Yes	NIPDAU	Level-3-260C-168 HR	-40 to 125	DRV8343S

(1) **Status:** For more details on status, see our product life cycle.

(2) **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

(3) **RoHS values:** Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

(4) **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

(5) **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

(6) **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

GENERIC PACKAGE VIEW

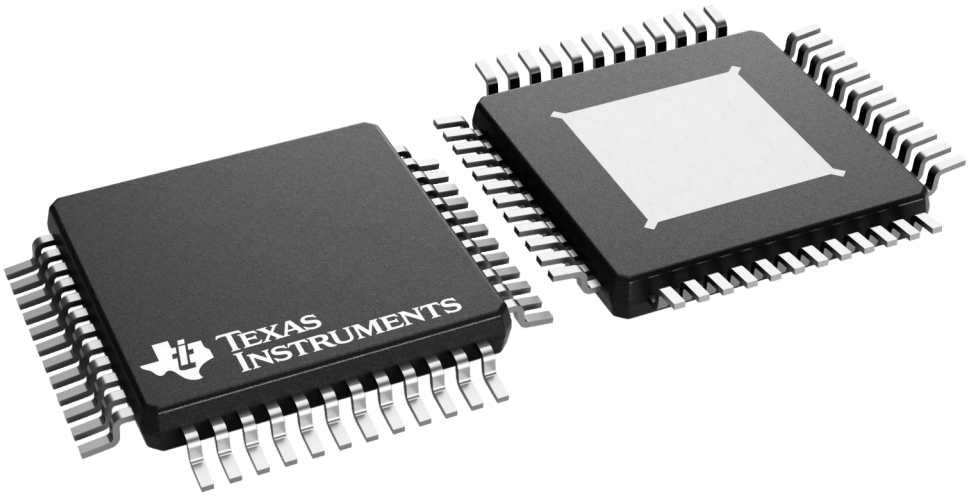
PHP 48

TQFP - 1.2 mm max height

7 x 7, 0.5 mm pitch

QUAD FLATPACK

This image is a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.



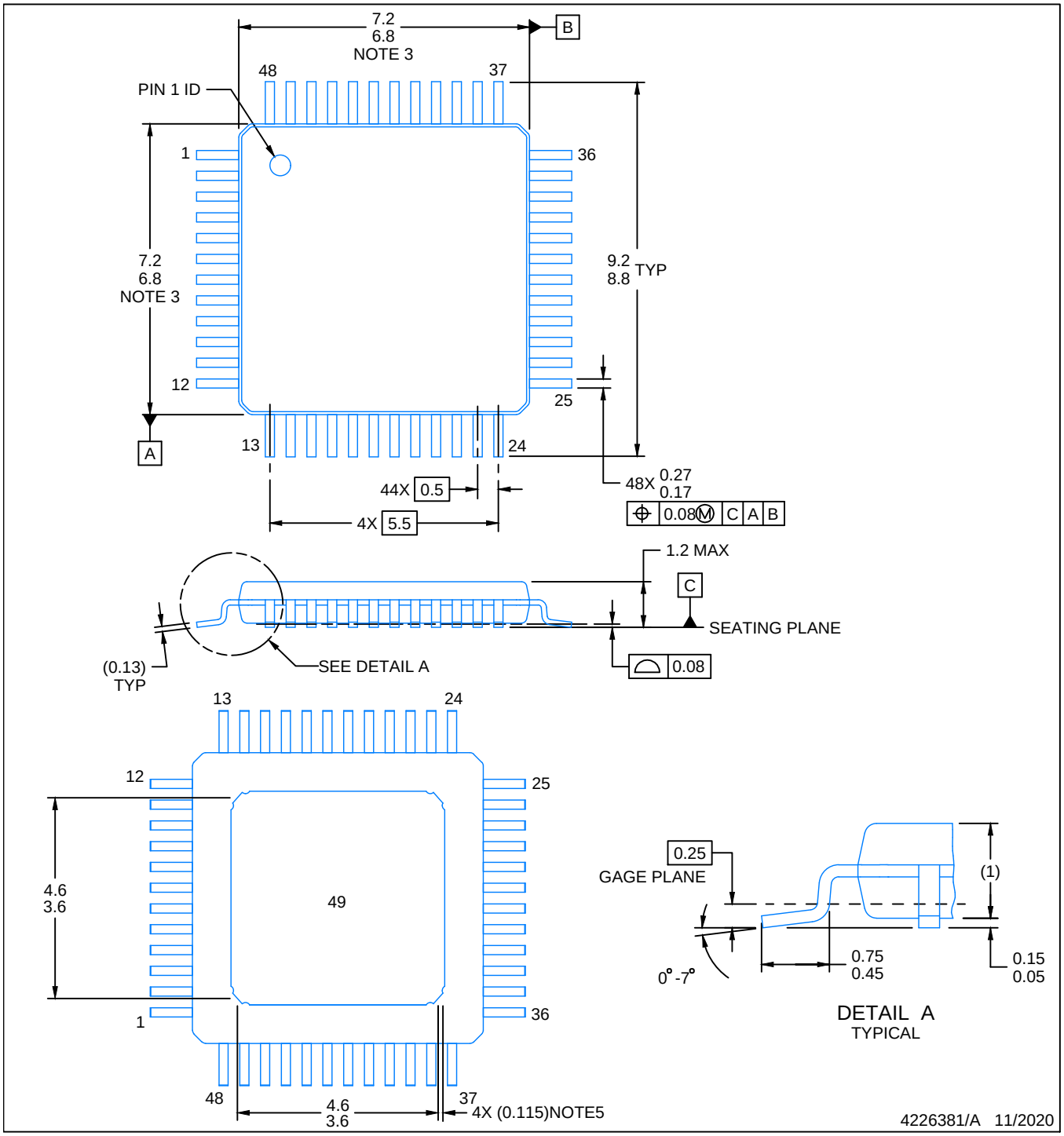
4226443/A

PACKAGE OUTLINE

PHP0048C

PowerPAD™ TQFP - 1.2 mm max height

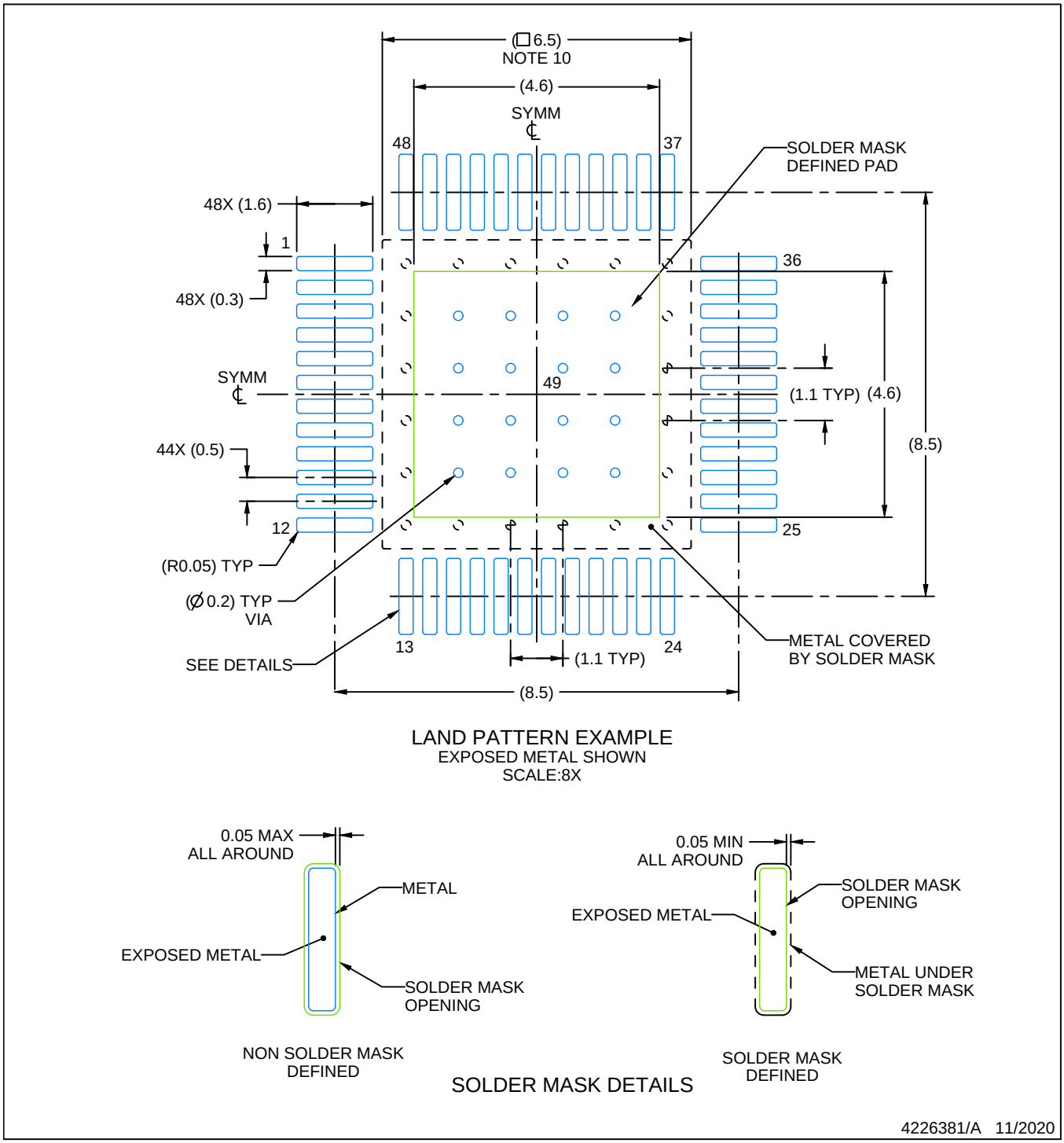
PLASTIC QUAD FLATPACK



PowerPAD is a trademark of Texas Instruments.

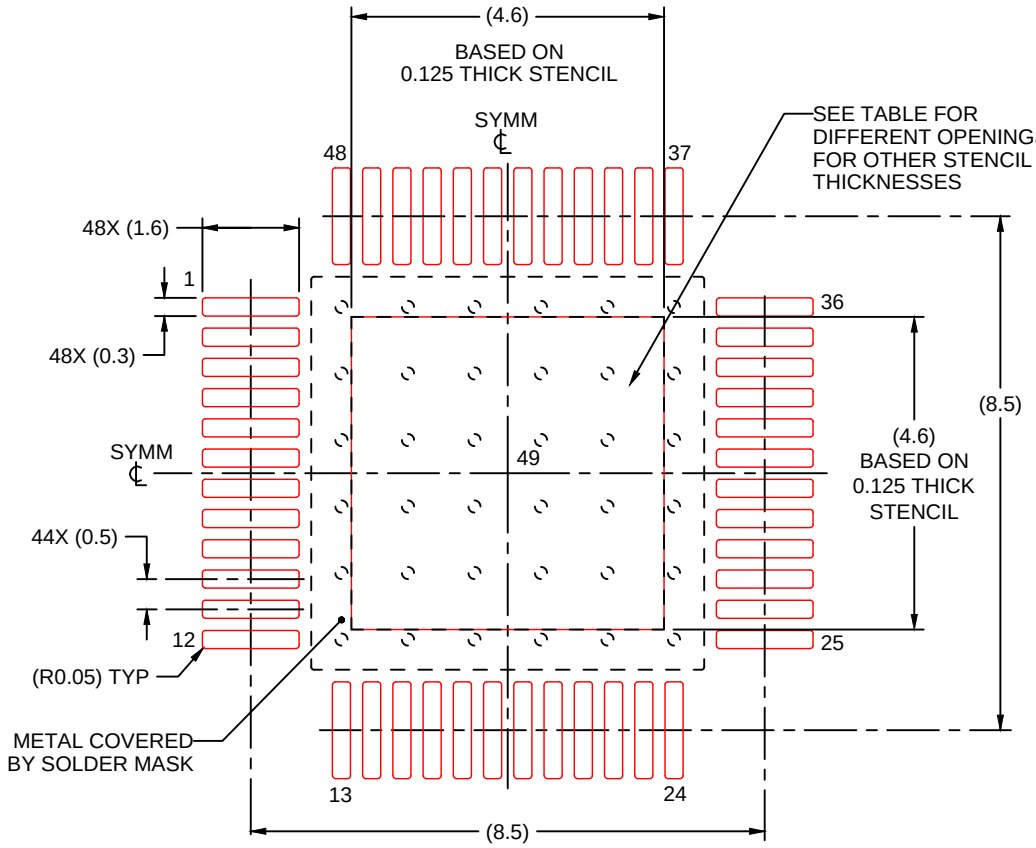
NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. Reference JEDEC registration MS-026.
5. Feature may not be present.



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.
8. This package is designed to be soldered to a thermal pad on the board. See technical brief, Powerpad thermally enhanced package, Texas Instruments Literature No. SLMA002 (www.ti.com/lit/slma002) and SLMA004 (www.ti.com/lit/slma004).
9. Vias are optional depending on application, refer to device data sheet. It is recommended that vias under paste be filled, plugged or tented.
10. Size of metal pad may vary due to creepage requirement.



SOLDER PASTE EXAMPLE
EXPOSED PAD
100% PRINTED SOLDER COVERAGE BY AREA
SCALE:8X

STENCIL THICKNESS	SOLDER STENCIL OPENING
0.1	5.14 X 5.14
0.125	4.6 X 4.6 (SHOWN)
0.150	4.2 X 4.2
0.175	3.89 X 3.89

4226381/A 11/2020

NOTES: (continued)

11. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
12. Board assembly site may have different recommendations for stencil design.

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